



FM25W04I3

4M-BIT SERIAL FLASH MEMORY

Datasheet

Sep. 2023



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1. Description

The FM25W04I3 is a 4M-bit (512K-byte) Serial Flash memory, with advanced write protection mechanisms. The FM25W04I3 supports the standard Serial Peripheral Interface (SPI), Dual/Quad I/O as well as 2-clock instruction cycle Quad Peripheral Interface (QPI). They are ideal for code shadowing to RAM, executing code directly from Dual/Quad SPI (XIP) and storing voice, text and data.

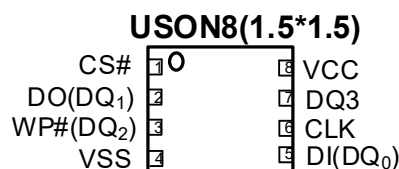
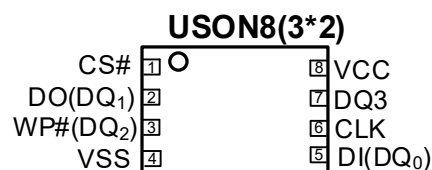
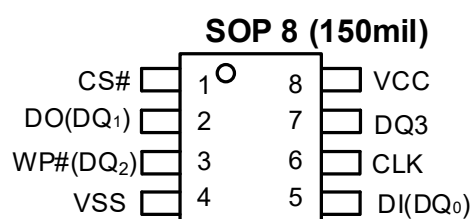
The FM25W04I3 can be programmed 1 to 256 bytes at a time, using the Page Program instruction. It is designed to allow either single Sector/Block at a time or full chip erase operation. The FM25W04I3 can be configured to protect part of the memory as the software protected mode. The device can sustain a minimum of 100K program/erase cycles on each sector or block.

2. Features

- **4Mbit of Flash memory**
 - 128 uniform sectors with 4K-byte each
 - 8 uniform blocks with 64K-byte each or
 - 16 uniform blocks with 32K-byte each
 - 256 bytes per programmable page
- **Wide Operation Range**
 - 1.65V~3.6V single voltage supply
 - Industrial temperature range
- **Serial Interface**
 - Standard SPI: CLK, CS#, DI, DO, WP#
 - Dual SPI: CLK, CS#, DQ₀, DQ₁, WP#
 - Quad SPI: CLK, CS#, DQ₀, DQ₁, DQ₂, DQ₃
 - QPI: CLK, CS#, DQ₀, DQ₁, DQ₂, DQ₃
 - Continuous READ mode support
 - Allow true XIP(execute in place) operation
- **High Performance**
 - Max FAST_READ clock frequency: 100MHz
 - Max READ clock frequency: 50MHz
 - Typical page program time: 0.5ms
 - Typical sector erase time: 80ms
 - Typical block erase time: 250/400ms
 - Typical chip erase time: 3s
- **Low Power Consumption**
 - Typical Deep Power Down current: <1μA
- **Security**
 - Software and hardware write protection
 - Lockable4X256-Byte OTP security Pages
 - 64-Bit Unique ID for each device
 - Discoverable parameters(SFDP) register

- **High Reliability**
 - Endurance: 100,000 program/erase cycles
 - Data retention: 20 years
- **Green Package**
 - 8-pin SOP (150mil)
 - 8-pin USON (3*2mm,0.45mm thickness)
 - 8-pin USON (1.5*1.5mm, 0.45mm thickness)
 - Thin 8-ball TWLCSP
 - All Packages are RoHS Compliant and Halogen-free

3. Packaging Type



4. Pin Configurations

PIN NO.	PIN NAME	I/O	FUNCTION
1	CS#	I	Chip Select Input
2	DO (DQ ₁)	I/O	Data Output (Data Input Output 1) ⁽¹⁾
3	WP# (DQ ₂)	I/O	Write Protect Input (Data Input Output 2) ⁽²⁾
4	VSS		Ground
5	DI (DQ ₀)	I/O	Data Input (Data Input Output 0) ⁽¹⁾
6	CLK	I	Serial Clock Input
7	DQ ₃	I/O	Data Input Output 3 ⁽²⁾
8	VCC		Power Supply

Note:

- 1 DQ₀ and DQ₁ are used for Dual SPI instructions.
- 2 DQ₀ – DQ₃ are used for Quad SPI and QPI instructions.

5. Block Diagram

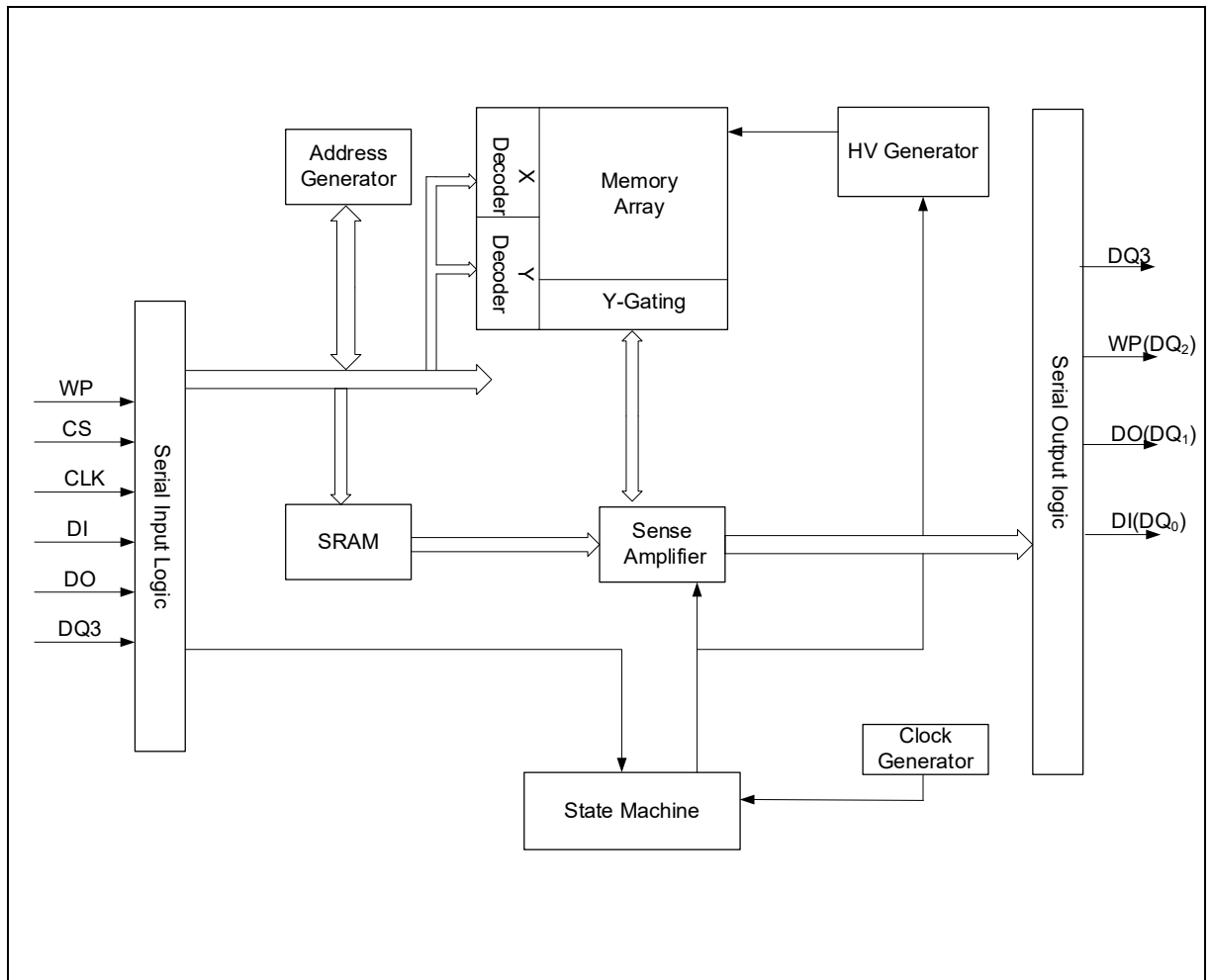


Figure 1 FM25W04I3 Serial Flash Memory Block Diagram

6. Pin Descriptions

Serial Clock (CLK): The SPI Serial Clock Input (CLK) pin provides the timing for serial input and output operations.

Serial Data Input, Output and I/Os (DI, DO and DQ₀, DQ₁, DQ₂, DQ₃): The FM25W04I3 supports standard SPI, Dual SPI, Quad SPI and QPI operation. Standard SPI instructions use the unidirectional DI (input) pin to serially write instructions, addresses or data to the device on the rising edge of the Serial Clock (CLK) input pin. Standard SPI also uses the unidirectional DO (output) to read data or status from the device on the falling edge of CLK.

Dual/Quad SPI and QPI instructions use the bidirectional DQ pins to serially write instructions, addresses or data to the device on the rising edge of CLK and read data or status from the device on the falling edge of CLK.

Chip Select (CS#): The SPI Chip Select (CS#) pin enables and disables device operation. When CS# is high, the device is deselected and the Serial Data Output (DO, or DQ₀, DQ₁, DQ₂, DQ₃) pins are at high impedance. When deselected, the devices power consumption will be at standby levels unless an internal erase, program or write status register cycle is in progress. When CS# is brought low, the device will be selected, power consumption will increase to active levels and instructions can be written to and data read from the device. After power-up, CS# must transition from high to low before a new instruction will be accepted. The CS# input must track the VCC supply level at power-up (see “Write Protection” and Figure 61). If needed a pull-up resistor on CS# can be used to accomplish this.

Write Protect (WP#): The Write Protect (WP#) pin can be used to prevent the Status Registers from being written. Used in conjunction with the Status Register’s Block Protect (SEC, TB, BP₂, BP₁ and BP₀) bits and Status Register Protect (SRP) bits, a portion as small as a 4KB sector or the entire memory array can be hardware protected. The WP# pin is active low.

7. Memory Organization

The FM25W0413 array is organized into 2,048 programmable pages of 256-bytes each. Up to 256 bytes can be programmed (bits are programmed from 1 to 0) at a time. Pages can be erased in groups of 16 (4KB sector erase), groups of 128 (32KB block erase), groups of 256 (64KB block erase) or the entire chip (chip erase). The FM25W0413 has 128 erasable sectors, 16 erasable 32-k byte blocks and 8 erasable 64-k byte blocks respectively. The small 4KB sectors allow for greater flexibility in applications that require data and parameter storage.

Table 1 Memory Organization

Block (64KB)	Block (32KB)	Sector (4KB)	Address Range	
7	15	127	07F000h	07FFFFh
	
	14	112	070000h	070FFFh
6	13	111	06F000h	06FFFFh
	
	12	96	060000h	060FFFh
5	11	95	05F000h	05FFFFh
	
	10	80	050000h	050FFFh
.				
.				
.				
2	5	47	02F000h	02FFFFh
	
	4	32	020000h	020FFFh
1	3	31	01F000h	01FFFFh
	
	2	16	010000h	010FFFh
0	1 0	15	00F000h	00FFFFh
	
		2	002000h	002FFFh
		1	001000h	001FFFh
		0	000000h	000FFFh

8. Device Operations

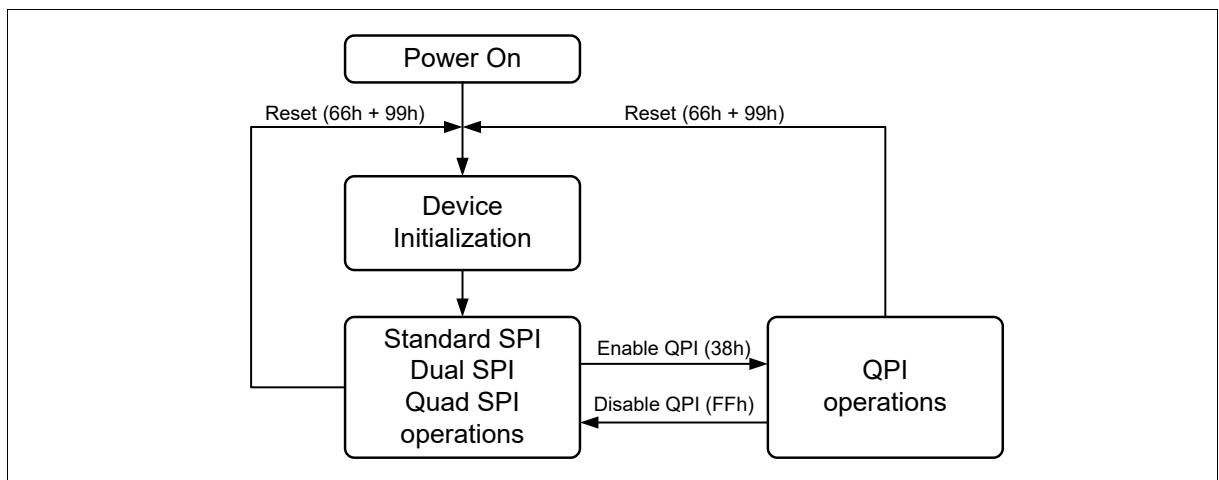


Figure 2 FM25W04I3 Serial Flash Memory Operation Diagram

8.1. Standard SPI

The FM25W04I3 is accessed through an SPI compatible bus consisting of four signals: Serial Clock (CLK), Chip Select (CS#), Serial Data Input (DI) and Serial Data Output (DO). Standard SPI instructions use the DI input pin to serially write instructions, addresses or data to the device on the rising edge of CLK. The DO output pin is used to read data or status from the device on the falling edge of CLK.

SPI bus operation Mode 0 (0,0) and 3 (1,1) are supported. The primary difference between Mode 0 and Mode 3 concerns the normal state of the CLK signal when the SPI bus master is in standby and data is not being transferred to the Serial Flash. For Mode 0, the CLK signal is normally low on the falling and rising edges of CS#. For Mode 3, the CLK signal is normally high on the falling and rising edges of CS#.

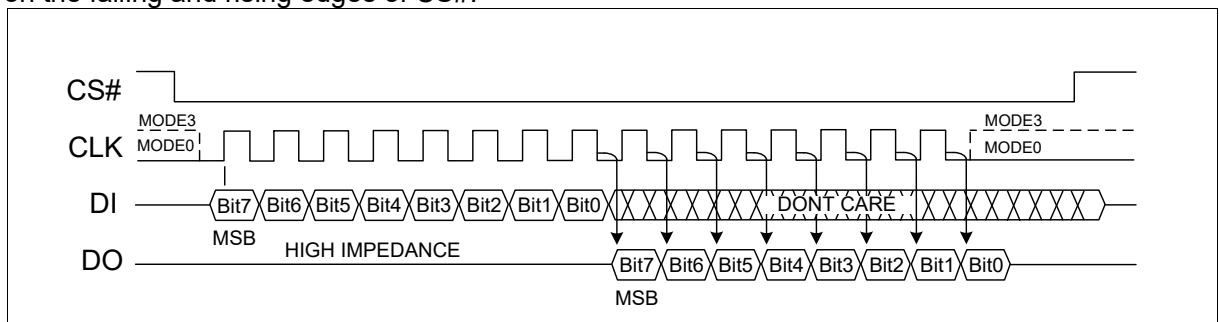


Figure 3 The difference between Mode 0 and Mode 3

8.2. Dual SPI

The FM25W04I3 supports Dual SPI operation when using instructions such as “Fast Read Dual Output (3Bh)” and “Fast Read Dual I/O (BBh)”. These instructions allow data to be transferred to or from the device at two to three times the rate of ordinary Serial Flash devices. The Dual SPI Read instructions are ideal for quickly downloading code to RAM upon power-up (code-shadowing) or for executing non-speed-critical code directly from the SPI bus (XIP). When using Dual SPI instructions, the DI and DO pins become bidirectional I/O pins: DQ₀ and DQ₁.

8.3. Quad SPI

The FM25W04I3 supports Quad SPI operation when using instructions such as “Fast Read Quad Output (6Bh)”, “Fast Read Quad I/O (EBh)”, “Word Read Quad I/O (E7h)” and “Octal Word Read Quad I/O (E3h)”. These instructions allow data to be transferred to or from the device four to six times the rate of ordinary Serial Flash. The Quad Read instructions offer a significant improvement in continuous and random access transfer rates allowing fast code-shadowing to RAM or execution directly from the SPI bus (XIP).

8.4. QPI

The FM25W04I3 supports Quad Peripheral Interface (QPI) operations only when the device is switched from Standard/Dual/Quad SPI mode to QPI mode using the “Enable QPI (38h)” instruction. The typical SPI protocol requires that the byte-long instruction code being shifted into the device only via DI pin in eight serial clocks. The QPI mode utilizes all four DQ pins to input the instruction code, thus only two serial clocks are required. This can significantly reduce the SPI instruction overhead and improve system performance in an XIP environment. Standard/Dual/Quad SPI mode and QPI mode are exclusive. Only one mode can be active at any given time. “Enable QPI (38h)” and “Disable QPI (FFh)” instructions are used to switch between these two modes. Upon power-up or after a software reset using “Reset (99h)” instruction, the default state of the device is Standard/Dual/Quad SPI mode. See Figure 2 for the device operation modes.

9. Write Protection

Applications that use non-volatile memory must take into consideration the possibility of noise and other adverse system conditions that may compromise data integrity. To address this concern, the FM25W04I3 provides several means to protect the data from inadvertent writes.

Write Protect Features

- Device resets when VCC is below threshold
- Time delay write disable after Power-up
- Write enable/disable instructions and automatic write disable after erase or program
- Software and Hardware (WP# pin) write protection using Status Register
- Write Protection using Power-down instruction
- Lock Down write protection for Status Register until the next power-up
- One Time Program (OTP) write protection for array and Security Sectors using Status Register.

Upon power-up or at power-down, the FM25W04I3 will maintain a reset condition while VCC is below the threshold value of VWI, (See “12.3Power-up Timing” and Figure 61). While reset, all operations are disabled and no instructions are recognized. During power-up and after the VCC voltage exceeds VWI, all program and erase related instructions are further disabled for a time delay of t_{PUW} . This includes the Write Enable, Page Program, Sector Erase, Block Erase, Chip Erase and the Write Status Register instructions. Note that the chip select pin (CS#) must track the VCC supply level at power-up until the VCC-min level and t_{VSL} time delay is reached. If needed a pull-up resistor on CS# can be used to accomplish this.

After power-up the device is automatically placed in a write-disabled state with the Status Register Write Enable Latch (WEL) set to a 0. A Write Enable instruction must be issued before a Page Program, Sector Erase, Block Erase, Chip Erase or Write Status Register instruction will be accepted. After completing a program, erase or write instruction the Write Enable Latch (WEL) is automatically cleared to a write-disabled state of 0.

Software controlled write protection is facilitated using the Write Status Register instruction and setting the Status Register Protect (SRP) and Block Protect (SEC, TB, BP2, BP1 and BP0) bits. These settings allow a portion as small as a 4KB sector or the entire memory array to be configured as read only. Used in conjunction with the Write Protect (WP#) pin, changes to the Status Register can be enabled or disabled under hardware control. See Status Register section for further information. Additionally, the Power-down instruction offers an extra level of write protection as all instructions are ignored except for the Release Power-down instruction.

10. Status Register

The Read Status Register instructions can be used to provide status on the availability of the Flash memory array, if the device is write enabled or disabled, the state of write protection, Quad SPI setting, Security Sector lock status. The Write Status Register instruction can be used to configure the device write protection features, Quad SPI setting and Security Sector OTP lock. Write access to the Status Register is controlled by the state of the non-volatile Status Register Protect bit (SRP), the Write Enable instruction, and during Standard/Dual SPI operations, the WP# pin.

Factory default for all Status Register bits are 0.

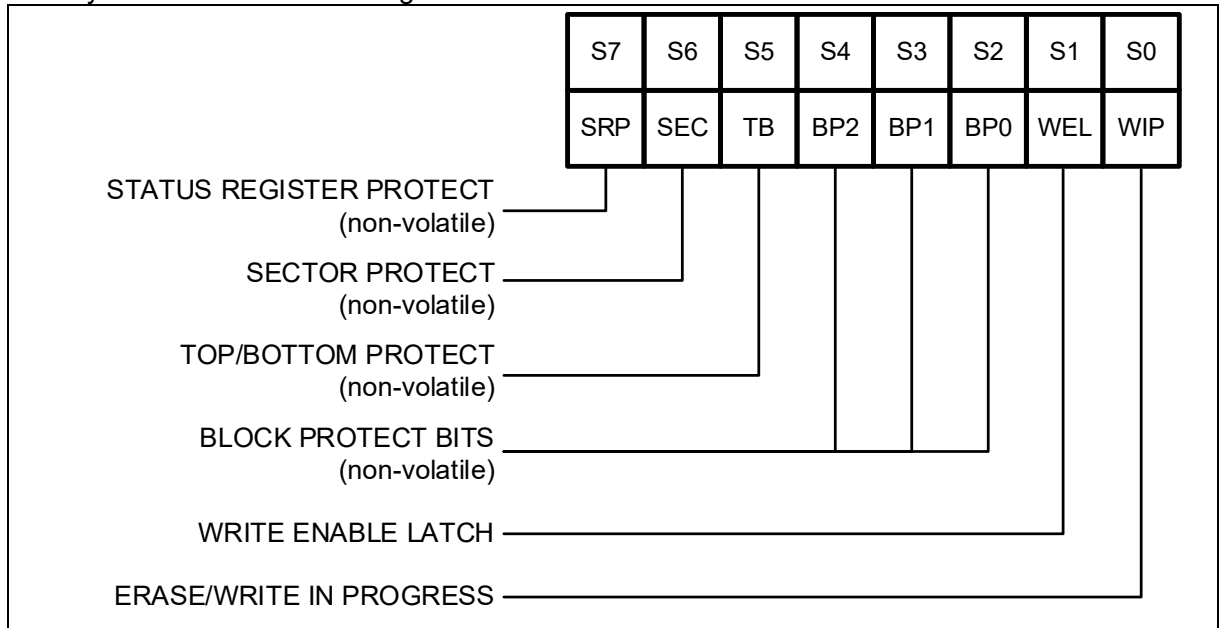


Figure 4 Status Register 1

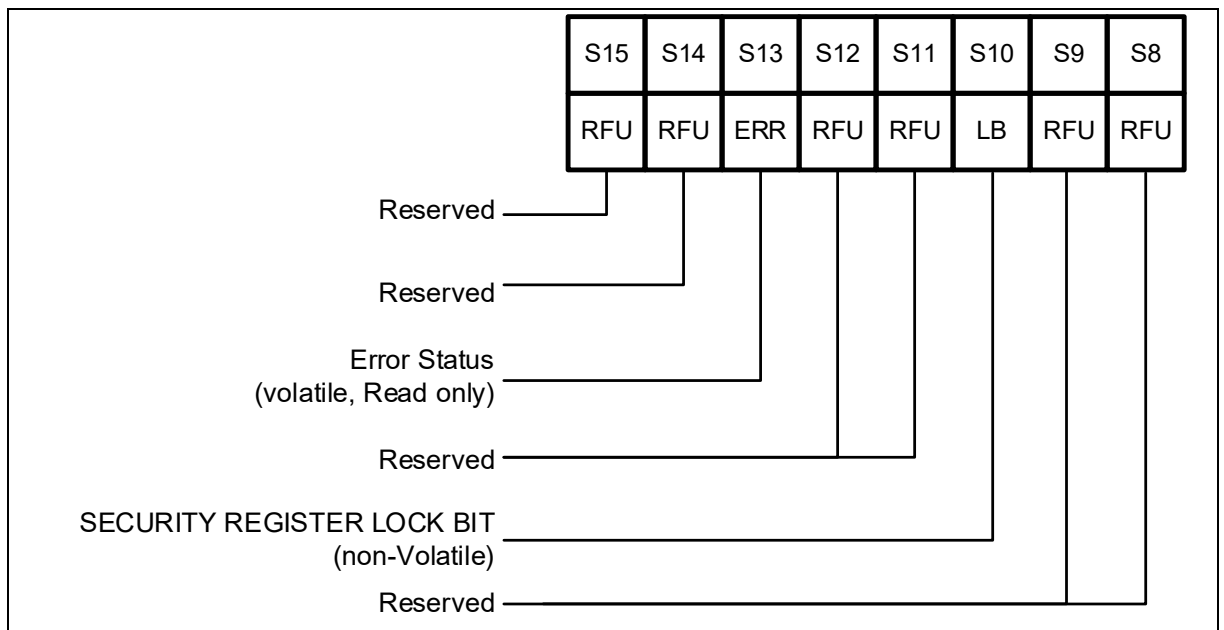


Figure 5 Status Register 2

10.1. WIP Bit

WIP is a read only bit in the status register (S0) that is set to a 1 state when the device is executing a Page Program, Quad Page Program, Sector Erase, Block Erase, Chip Erase, Write Status Register or Erase/Program Security Sector instruction. During this time the device will ignore further instructions except for the Read Status Register instruction (see t_W , t_{PP} , t_{SE} , t_{BE} , and t_{CE} in “12.6AC Electrical Characteristics”). When the program, erase or write status register (or security sector) instruction has completed, the WIP bit will be cleared to a 0 state indicating the device is ready for further instructions.

10.2. Write Enable Latch (WEL)

Write Enable Latch (WEL) is a read only bit in the status register (S1) that is set to 1 after executing a Write Enable Instruction. The WEL status bit is cleared to 0 when the device is write disabled. A write disable state occurs upon power-up or after any of the following instructions: Write Disable, Page Program, Quad Page Program, Sector Erase, Block Erase, Chip Erase, Write Status Register, Erase Security Sector and Program Security Sector.

10.3. Block Protect Bits (BP2, BP1, BP0)

The Block Protect Bits (BP2-0) are non-volatile read/write bits in the status register (S4-2) that provide Write Protection control and status. Block Protect bits can be set using the Write Status Register Instruction (see t_W in “12.6AC Electrical Characteristics”). All, none or a portion of the memory array can be protected from Program and Erase instructions (see Table 3 Status Register Memory Protection). The factory default setting for the Block Protection Bits is 0, none of the array protected.

10.4. Top/Bottom Block Protect (TB)

The non-volatile Top/Bottom bit (TB) controls if the Block Protect Bits (BP2-0) protect from the Top (TB=0) or the Bottom (TB=1) of the array as shown in Table 3 Status Register Memory Protection table. The factory default setting is TB=0. The TB bit can be set with the Write Status Register Instruction depending on the state of the SRP0, SRP1 and WEL bits.

10.5. Sector/Block Protect (SEC)

The non-volatile Sector/Block Protect bit (SEC) controls if the Block Protect Bits (BP2-0) protect either 4KB Sectors (SEC=1) or 64KB Blocks (SEC=0) in the Top (TB=0) or the Bottom (TB=1) of the array as shown in Table 3 Status Register Memory Protection table. The default setting is SEC=0.

10.6. Status Register Protect (SRP)

The Status Register Protect bit (SRP) is non-volatile read/write bit in the status register (S7). The SRP bit controls the method of write protection: software protection and hardware protection.

Table 2 Status Register Protect bit

SRP	WP#	Status Register	Description
0	X	Software Protection	WP# pin has no control. The Status register can be written to after a Write Enable instruction, WEL=1. (Factory Default)
1	0	Hardware Protected	When WP# pin is low the Status Register locked and can not be written to.
1	1	Hardware Unprotected	When WP# pin is high the Status register is unlocked and can be written to after a Write Enable instruction, WEL=1.

10.7. Error Bit (ERR)

The Error bit is a status flag, which shows the status of last Program/Erase operation. It will be set to "1", if the Program/Erase operation fails. If the Program/Erase region is protected, Error bit will not be set to "1". It will be clear to "0" after power-up, or software Reset/Write Enable instruction.

10.8. Security Sector Lock Bit (LB)

The Security Register Lock Bit (LB) is non-volatile One Time Program (OTP) bit in Status Register (S10) that provides the write protect control and status to the Security Registers. The default state of LB is 0, Security Registers are unlocked. LB can be set to 1 using the Write Status Register instruction. LB bit is One Time Programmable (OTP), once it's set to 1, the Security Registers will become read-only permanently.

10.9. Status Register Memory Protection

Table 3 Status Register Memory Protection

STATUS REGISTER					FM25W04I3 (4M-BIT) MEMORY PROTECTION			
SEC	TB	BP2	BP1	BP0	PROTECTED BLOCK(S)	PROTECTED ADDRESSES	PROTECTED DENSITY	PROTECTED PORTION
X	X	0	0	0	NONE	NONE	NONE	NONE
0	0	0	0	1	7	070000h – 07FFFFh	64KB	Upper 1/8
0	0	0	1	0	6 and 7	060000h – 07FFFFh	128KB	Upper 1/4
0	0	0	1	1	4 thru 7	040000h – 07FFFFh	256KB	Upper 1/2
0	1	0	0	1	0	000000h – 00FFFFh	64KB	Lower 1/8
0	1	0	1	0	0 and 1	000000h – 01FFFFh	128KB	Lower 1/4
0	1	0	1	1	0 thru 3	000000h – 03FFFFh	256KB	Lower 1/2
0	X	1	X	X	0 thru 7	000000h – 07FFFFh	512KB	ALL

STATUS REGISTER					FM25W04I3 (4M-BIT) MEMORY PROTECTION			
SEC	TB	BP2	BP1	BP0	PROTECTED BLOCK(S)	PROTECTED ADDRESSES	PROTECTED DENSITY	PROTECTED PORTION
1	0	0	0	1	7	07F000h – 07FFFFh	4KB	U - 1/128
1	0	0	1	0	7	07E000h – 07FFFFh	8KB	U - 1/64
1	0	0	1	1	7	07C000h – 07FFFFh	16KB	U - 1/32
1	0	1	0	X	7	078000h – 07FFFFh	32KB	U - 1/16
1	0	1	1	0	7	078000h – 07FFFFh	32KB	U - 1/16
1	1	0	0	1	0	000000h – 000FFFh	4KB	L - 1/128
1	1	0	1	0	0	000000h – 001FFFh	8KB	L - 1/64
1	1	0	1	1	0	000000h – 003FFFh	16KB	L - 1/32
1	1	1	0	x	0	000000h – 007FFFh	32KB	L - 1/16
1	1	1	1	0	0	000000h – 007FFFh	32KB	L - 1/16
1	X	1	1	1	0 thru 7	000000h – 07FFFFh	512KB	ALL

Notes:

1. X= don't care
2. If and Erase or Program command specifies a memory region that contains protected data portion, this command will be ignored.

11. Instructions

The Standard/Dual/Quad SPI instruction set of the FM25W04I3 consists of 34 basic instructions that are fully controlled through the SPI bus (see Table 6 ~ Table 8). Instructions are initiated with the falling edge of Chip Select (CS#). The first byte of data clocked into the DI input provides the instruction code. Data on the DI input is sampled on the rising edge of clock with most significant bit (MSB) first.

The QPI instruction set of the FM25W04I3 consists of 23 basic instructions that are fully controlled through the SPI bus (see Table 8 QPI Instructions Set 9 Instruction Set). Instructions are initiated with the falling edge of Chip Select (CS#). The first byte of data clocked through DQ[3:0] pins provides the instruction code. Data on all four DQ pins are sampled on the rising edge of clock with most significant bit (MSB) first. All QPI instructions, addresses, data and dummy bytes are using all four DQ pins to transfer every byte of data with every two serial clocks (CLK).

Instructions vary in length from a single byte to several bytes and may be followed by address bytes, data bytes, dummy bytes (don't care), and in some cases, a combination. Instructions are completed with the rising edge of edge CS#. Clock relative timing diagrams for each instruction are included in Figure 6 through Figure 60. All read instructions can be completed after any clocked bit. However, all instructions that Write, Program or Erase must complete on a byte boundary (CS# driven high after a full 8-bits have been clocked) otherwise the instruction will be ignored. This feature further protects the device from inadvertent writes. Additionally, while the memory is being programmed or erased, or when the Status Register is being written, all instructions except for Read Status Register will be ignored until the program or erase cycle has completed.

11.1. Manufacturer and Device Identification

Table 4 Manufacturer and Device Identification

OP Code	MF7-MF0	ID15-ID0	ID7-ID0
ABh			12h
90h,92h,94h	A1h		12h
9Fh	A1h	2813h	

11.2. Standard SPI Instructions Set

Table 5 Standard SPI Instructions Set ⁽¹⁾

INSTRUCTION NAME	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
CLOCK NUMBER	(0-7)	(8-15)	(16-23)	(24-31)	(32-39)	(40-47)
Write Enable	06h					
Volatile SR Write Enable	50h					
Write Disable	04h					
Read Status Register-1	05h	(S7-S0) ⁽²⁾				
Write Status Register-1	01h	S7-S0				
Read Status Register-2	35h	(S15-S8) ⁽²⁾				
Write Status Register-2	31h	S15-S8				
Page Program	02h	A23-A16	A15-A8	A7-A0	D7-D0	D7-D0 ⁽³⁾
Sector Erase (4KB)	20h	A23-A16	A15-A8	A7-A0		
Block Erase (32KB)	52h	A23-A16	A15-A8	A7-A0		
Block Erase (64KB)	D8h	A23-A16	A15-A8	A7-A0		
Chip Erase	C7h/60h					
Power-down	B9h					
Read Data	03h	A23-A16	A15-A8	A7-A0	(D7-D0)	
Fast Read	0Bh	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Release Powerdown / ID ⁽⁴⁾	ABh	dummy	dummy	dummy	(ID7-ID0) ⁽²⁾	
Manufacturer/Device ID ⁽⁴⁾	90h	dummy	dummy	00h	(MF7-MF0)	(ID7-ID0)
JEDEC ID ⁽⁴⁾	9Fh	(MF7-MF0) Manufacture	(ID15-ID8) Memory Type	(ID7-ID0) Capacity		
Read SFDP Register	5Ah	00h	00h	A7-A0	dummy	(D7-D0)
Read Unique ID ⁽⁵⁾	4Bh	dummy	dummy	dummy	dummy	(UID63-UID0)
Erase Security Sectors ⁽⁶⁾	44h	A23-A16	A15-A8	A7-A0		
Program Security Sectors ⁽⁶⁾	42h	A23-A16	A15-A8	A7-A0	D7-D0	D7-D0 ⁽³⁾
Read Security Sectors ⁽⁶⁾	48h	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Enable QPI	38h					
Enable Reset	66h					
Reset	99h					

11.3. Dual SPI Instructions Set

Table 6 Dual SPI Instructions Set

INSTRUCTION NAME	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
<i>CLOCK NUMBER</i>	(0-7)	(8-15)	(16-23)	(24-31)	(32-39)	(40-47)
Fast Read Dual Output	3Bh	A23-A16	A15-A8	A7-A0	dummy	(D7-D0, ...) ⁽⁸⁾
Fast Read Dual I/O	BBh	A23-A8 ⁽⁷⁾	A7-A0, M7-M0 ⁽⁷⁾	(D7-D0, ...) ⁽⁸⁾		
Manufacturer/Device ID by Dual I/O ⁽⁴⁾	92h	A23-A8 ⁽⁷⁾	A7-A0, M7-M0 ⁽⁷⁾	(MF7-MF0, ID7-ID0)		

11.4. Quad SPI Instructions Set

Table 7 Quad SPI Instructions Set

INSTRUCTION NAME	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
<i>CLOCK NUMBER</i>	(0-7)	(8-15)	(16-23)	(24-31)	(32-39)	(40-47)
Quad Page Program	32h	A23-A16	A15-A8	A7-A0	D7-D0, ... ⁽¹⁰⁾	D7-D0, ... ⁽³⁾
Fast Read Quad Output	6Bh	A23-A16	A15-A8	A7-A0	dummy	(D7-D0, ...) ⁽¹⁰⁾
Fast Read Quad I/O	EBh	A23-A0, M7-M0 ⁽⁹⁾	(xxxx, D7-D0) ⁽¹¹⁾	(D7-D0, ...) ⁽¹⁰⁾		
Word Read Quad I/O ⁽¹³⁾	E7h	A23-A0, M7-M0 ⁽⁹⁾	(xx, D7-D0) ⁽¹²⁾	(D7-D0, ...) ⁽¹⁰⁾		
Octal Word Read Quad I/O ⁽¹⁴⁾	E3h	A23-A0, M7-M0 ⁽⁹⁾	(D7-D0, ...) ⁽¹⁰⁾			
Set Burst with Wrap	77h	xxxxxx, W6-W4 ⁽⁹⁾				
Manufacture/Device ID by Quad I/O ⁽⁴⁾	94h	A23-A0, M7-M0 ⁽⁹⁾	xxxx, (MF7-MF0, ID7-ID0)	(MF7-MF0, ID7-ID0, ...)		

11.5. QPI Instructions Set

Table 8 QPI Instructions Set⁽¹⁵⁾

INSTRUCTION NAME	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
<i>CLOCK NUMBER</i>	(0,1)	(2,3)	(4,5)	(6,7)	(8,9)	(10,11)
Write Enable	06h					
Write Disable	04h					
Read Status Register-1	05h	(S7-S0) ⁽²⁾				
Read Status Register-2	35h	(S15-S8) ⁽²⁾				
Page Program	02h	A23-A16	A15-A8	A7-A0	D7-D0 ⁽¹⁰⁾	D7-D0 ⁽³⁾
Sector Erase (4KB)	20h	A23-A16	A15-A8	A7-A0		
Block Erase (32KB)	52h	A23-A16	A15-A8	A7-A0		
Block Erase (64KB)	D8h	A23-A16	A15-A8	A7-A0		
Chip Erase	C7h/60h					

INSTRUCTION NAME	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
Power-down	B9h					
Set Read Parameters	C0h	P7-P0				
Fast Read	0Bh	A23-A16	A15-A8	A7-A0	dummy ⁽¹⁶⁾	(D7-D0)
Burst Read with Wrap ⁽¹⁷⁾	0Ch	A23-A16	A15-A8	A7-A0	dummy ⁽¹⁶⁾	(D7-D0)
Fast Read Quad I/O	EBh	A23-A16	A15-A8	A7-A0	M7-M0 ⁽¹⁶⁾	(D7-D0)
Release Powerdown / ID ⁽⁴⁾	ABh	dummy	dummy	dummy	(ID7-ID0) ⁽²⁾	
Manufacturer/Device ID ⁽⁴⁾	90h	dummy	dummy	00h	(MF7-MF0)	(ID7-ID0)
JEDEC ID ⁽⁴⁾	9Fh	(MF7-MF0) Manufacturer	(ID15-ID8) Memory Type	(ID7-ID0) Capacity		
Disable QPI	FFh					
Enable Reset	66h					
Reset	99h					

Notes:

- Data bytes are shifted with Most Significant Bit first. Byte fields with data in parenthesis “ () ” indicate data output from the device on either 1 or 2 or 4 DQ pins.
- The Status Register contents and Device ID will repeat continuously until CS# terminates the instruction.
- At least one byte of data input is required for Page Program, Quad Page Program and Program Security Sectors, up to 256 bytes of data input. If more than 256 bytes of data are sent to the device, the addressing will wrap to the beginning of the page and overwrite previously sent data.
- See Table 4 Manufacturer and Device Identification table for device ID information.
- Please contact Shanghai Fudan Microelectronics Group Co., Ltd for details.
- Security Sector Address:
Security Sector: A23-A10 = 000h; A9-A8=00~11; A7-A0 = byte address
- Dual SPI address input format:
DQ₀ = A22, A20, A18, A16, A14, A12, A10, A8, A6, A4, A2, A0, M6, M4, M2, M0
DQ₁ = A23, A21, A19, A17, A15, A13, A11, A9, A7, A5, A3, A1, M7, M5, M3, M1
- Dual SPI data output format:
DQ₀ = (D6, D4, D2, D0)
DQ₁ = (D7, D5, D3, D1)
- Quad SPI address input format:

DQ ₀ = A20, A16, A12, A8, A4, A0, M4, M0 DQ ₁ = A21, A17, A13, A9, A5, A1, M5, M1 DQ ₂ = A22, A18, A14, A10, A6, A2, M6, M2 DQ ₃ = A23, A19, A15, A11, A7, A3, M7, M3	Set Burst with Wrap input format: DQ ₀ = x, x, x, x, x, x, W4, x DQ ₁ = x, x, x, x, x, x, W5, x DQ ₂ = x, x, x, x, x, x, W6, x DQ ₃ = x, x, x, x, x, x, x, x
--	--
- Quad SPI data input/output format:
DQ₀ = (D4, D0...)
DQ₁ = (D5, D1...)
DQ₂ = (D6, D2...)
DQ₃ = (D7, D3...)
- Fast Read Quad I/O data output format:
DQ₀ = (x, x, x, x, D4, D0, D4, D0)
DQ₁ = (x, x, x, x, D5, D1, D5, D1)
DQ₂ = (x, x, x, x, D6, D2, D6, D2)
DQ₃ = (x, x, x, x, D7, D3, D7, D3)
- Word Read Quad I/O data output format:
DQ₀ = (x, x, D4, D0, D4, D0, D4, D0)
DQ₁ = (x, x, D5, D1, D5, D1, D5, D1)
DQ₂ = (x, x, D6, D2, D6, D2, D6, D2)

$DQ_3 = (x, x, D7, D3, D7, D3, D7, D3)$

13. For Word Read Quad I/O, the lowest address bit must be 0. ($A_0 = 0$)
14. For Octal Word Read Quad I/O, the lowest four address bits must be 0. ($A_3, A_2, A_1, A_0 = 0$)
15. QPI Command Address, Data input/output format:

CLK#	0	1	2	3	4	5	6	7	8	9	10	11
DQ_0	C4	C0	A20	A16	A12	A8	A4	A0	D4	D0	D4	D0
DQ_1	C5	C1	A21	A17	A13	A9	A5	A1	D5	D1	D5	D1
DQ_2	C6	C2	A22	A18	A14	A10	A6	A2	D6	D2	D6	D2
DQ_3	C7	C3	A23	A19	A15	A11	A7	A3	D7	D3	D7	D3

16. The number of dummy clocks for QPI Fast Read, QPI Fast Read Quad I/O & QPI Burst Read with Wrap is controlled by read parameter P7 ~ P4.
17. The wrap around length for QPI Burst Read with Wrap is controlled by read parameter P3 ~ P0.

11.6. Write Enable (WREN) (06h)

The Write Enable (WREN) instruction (Figure 6) sets the Write Enable Latch (WEL) bit in the Status Register to a1. The WEL bit must be set prior to every Page Program, Quad Page Program, Sector Erase, Block Erase, Chip Erase, Write Status Register and Erase/Program Security Sectors instruction. The Write Enable (WREN) instruction is entered by driving CS# low, shifting the instruction code “06h” into the Data Input (DI) pin on the rising edge of CLK, and then driving CS# high.

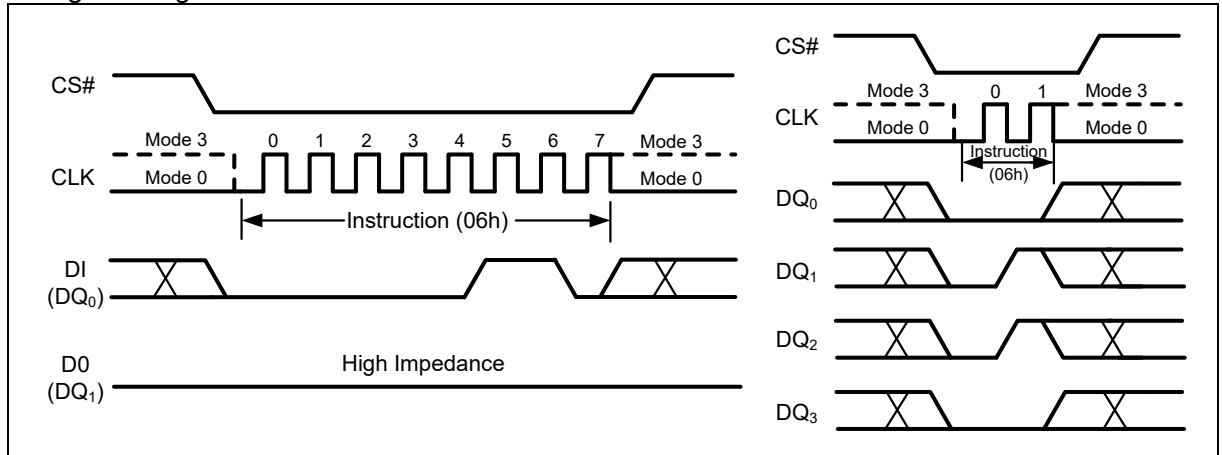


Figure 6 Write Enable Instruction for SPI Mode (left) or QPI Mode (right)

11.7. Write Enable for Volatile Status Register (50h)

The non-volatile Status Register bits described in section 10.1 can also be written to as volatile bits. This gives more flexibility to change the system configuration and memory protection schemes quickly without waiting for the typical non-volatile bit write cycles or affecting the endurance of the Status Register non-volatile bits. To write the volatile values into the Status Register bits, the Write Enable for Volatile Status Register (50h) instruction must be issued prior to a Write Status Register (01h/31h) instruction. Write Enable for Volatile Status Register instruction (Figure 7) will not set the Write Enable Latch (WEL) bit, it is only valid for the Write Status Register instruction to change the volatile Status Register bit values.

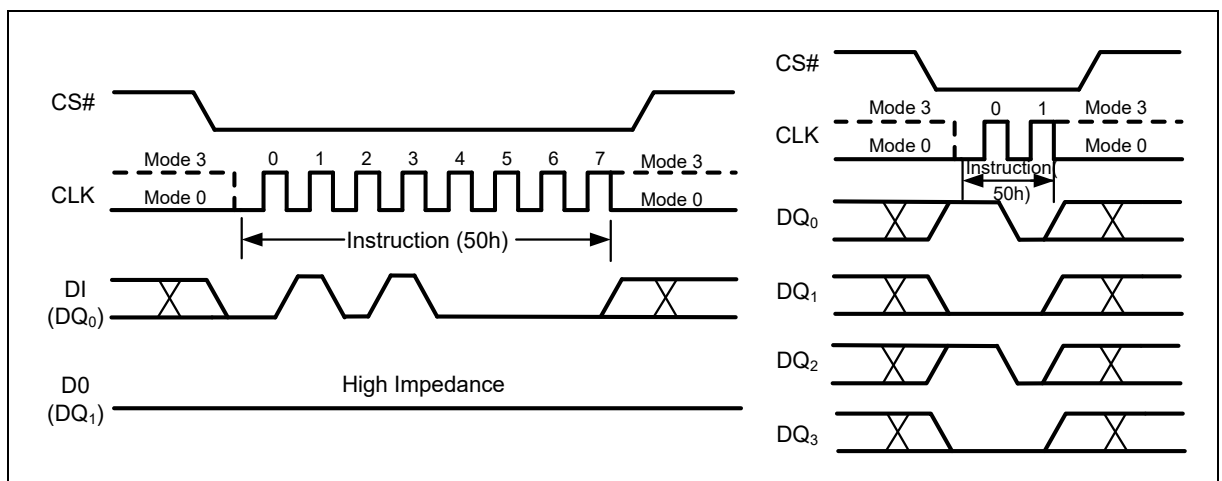


Figure 7 Write Enable for Volatile Status Register Instruction for SPI Mode (left) or QPI Mode (right)

11.8. Write Disable(WRDI) (04h)

The Write Disable (WRDI) instruction (Figure 8) resets the Write Enable Latch (WEL) bit in the Status Register to a 0. The Write Disable(WRDI) instruction is entered by driving CS# low, shifting the instruction code “04h” into the DI pin and then driving CS# high. Note that the WEL bit is automatically reset after Power-up and upon completion of the Write Status Register, Erase/Program Security Sectors, Page Program, Quad Page Program, Sector Erase, Block Erase, Chip Erase and Reset instructions.

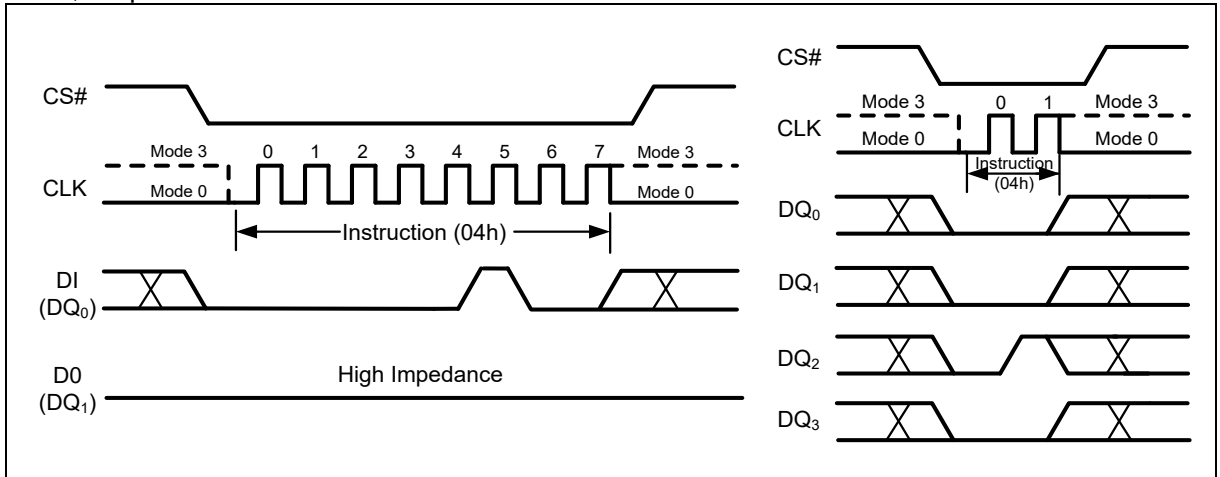


Figure 8 Write Disable Instruction for SPI Mode (left) or QPI Mode (right)

11.9. Read Status Register-1(RDSR1) (05h) , Status Register-2 (RDSR2)(35h)

The Read Status Register instructions allow the 8-bit Status Registers to be read. The instruction is entered by driving CS# low and shifting the instruction code “05h”for Status Register-1 or “35h” for Status Register-2 into the DI pin on the rising edge of CLK. The status register bits are then shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) first as shown in Figure 9 and Figure 10. The Status Register bits are shown in Figure 4 and Figure 5.

The Read Status Register instruction may be used at any time, even while a Program, Erase or Write Status Register cycle is in progress. This allows the WIP status bit to be checked to determine when the cycle is complete and if the device can accept another instruction. The Status Register can be read continuously, as shown in Figure 9 and Figure 10. The instruction is completed by driving CS# high.

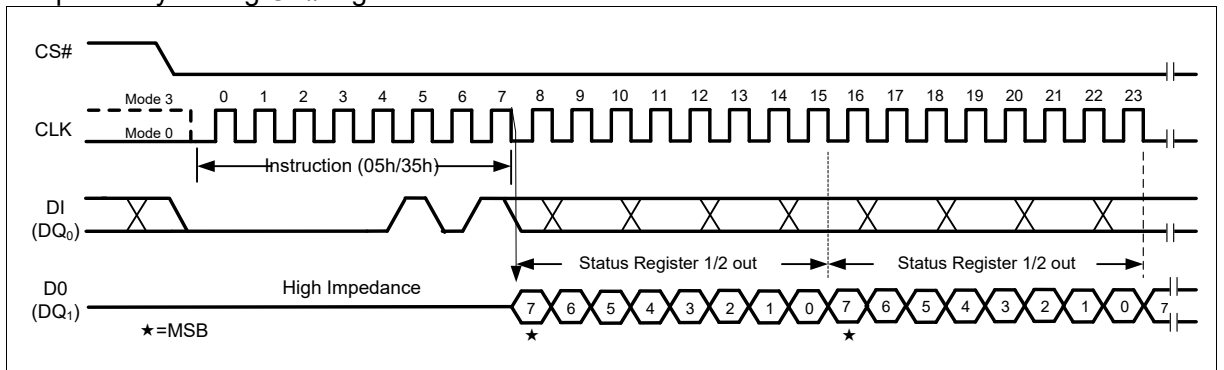


Figure 9 Read Status Register Instruction (SPI Mode)

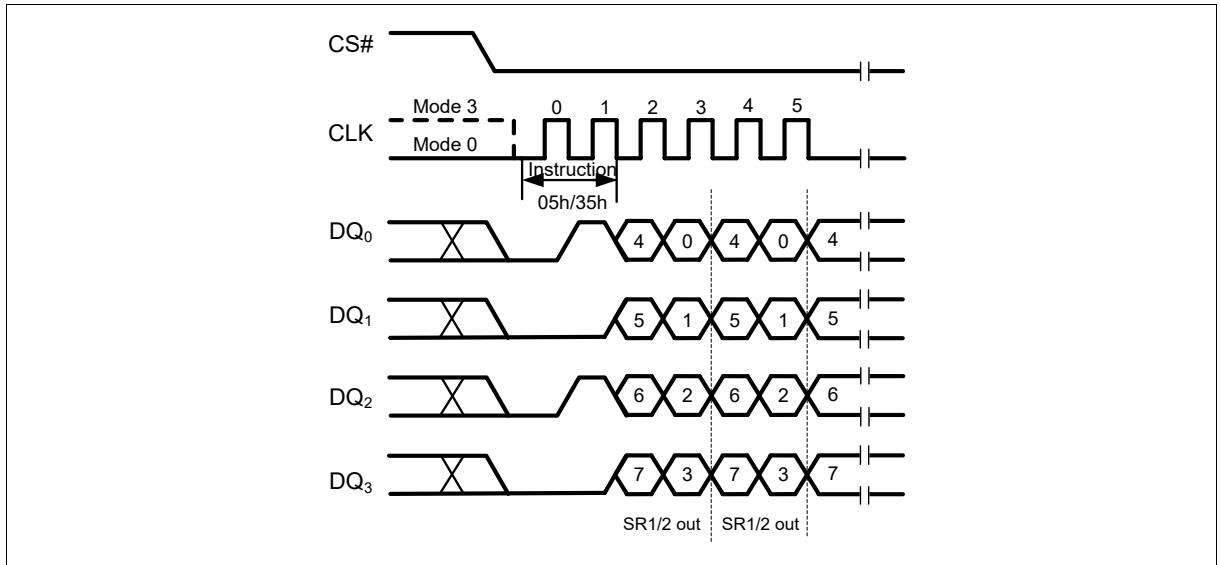


Figure 10 Read Status Register Instruction (QPI Mode)

11.10. Write Status Register-1(WRSR)(01h), Status Register-2 (31h)

The Write Status Register (WRSR) instruction allows the Status Register to be written. Only non-volatile Status Register bits SRP, SEC, TB, BP2, BP1, BP0 (bits 7 thru 2 of Status Register-1), LB (bit 8 of Status Register-2), can be written to. All other Status Register bit locations are read-only and will not be affected by the Write Status Register (WRSR) instruction. LB is non-volatile OTP bit, once it is set to 1, it cannot be cleared to 0. The Status Register bits are shown in Figure 4 and Figure 5 and described in 10 Status Register

To write non-volatile Status Register bits, a standard Write Enable (06h) instruction must previously have been executed for the device to accept the Write Status Register (WRSR) instruction (Status Register bit WEL must equal 1). Once write enabled, the instruction is entered by driving CS# low, sending the instruction code “01h”, and then writing the status register data byte as illustrated in Figure 11 Write Status Register Instruction (SPI Mode) and Figure 12.

To write volatile Status Register bits, a Write Enable for Volatile Status Register (50h) instruction must have been executed prior to the Write Status Register (WRSR) instruction (Status Register bit WEL remains 0). However, LB, cannot be changed from “1” to “0” because of the OTP protection for these bits. Upon power off or the execution of a “Reset (99h)” instruction, the volatile Status Register bit values will be lost, and the non-volatile Status Register bit values will be restored.

During non-volatile Status Register write operation (06h combined with 01h), after CS# is driven high, the self-timed Write Status Register cycle will commence for a time duration of t_w (See “12.6 AC Electrical Characteristics”). While the Write Status Register cycle is in progress, the Read Status Register instruction may still be accessed to check the status of the WIP bit. The WIP bit is a 1 during the Write Status Register cycle and a 0 when the cycle is finished and ready to accept other instructions again. After the Write Status Register cycle has finished, the Write Enable Latch (WEL) bit in the Status Register will be cleared to 0.

During volatile Status Register write operation (50h combined with 01h), after CS# is driven high, the Status Register bits will be refreshed to the new values within the time period of t_{SHSL2} (See “12.6 AC Electrical Characteristics”). WIP bit will remain 0 during the Status Register bit refresh period.

The Write Status Register (WRSR) instruction can be used in both SPI mode and QPI mode.

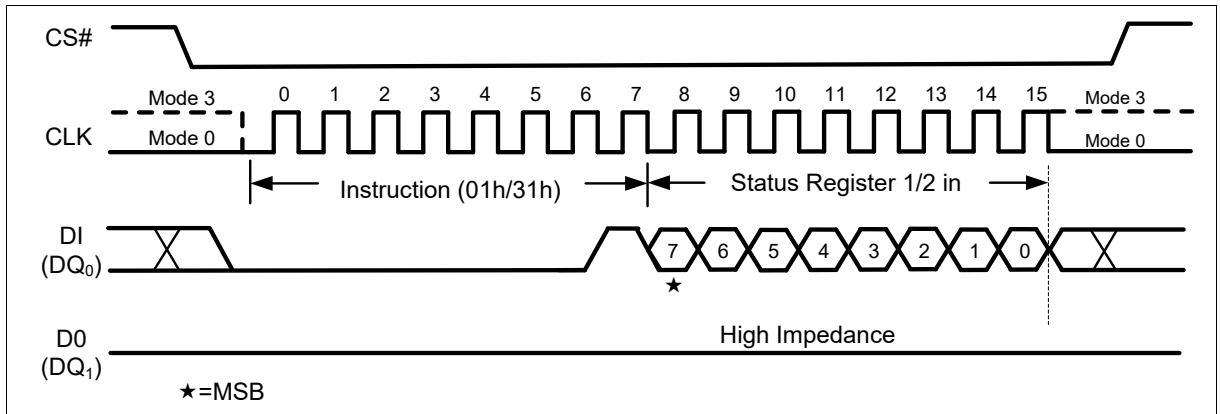


Figure 11 Write Status Register Instruction (SPI Mode)

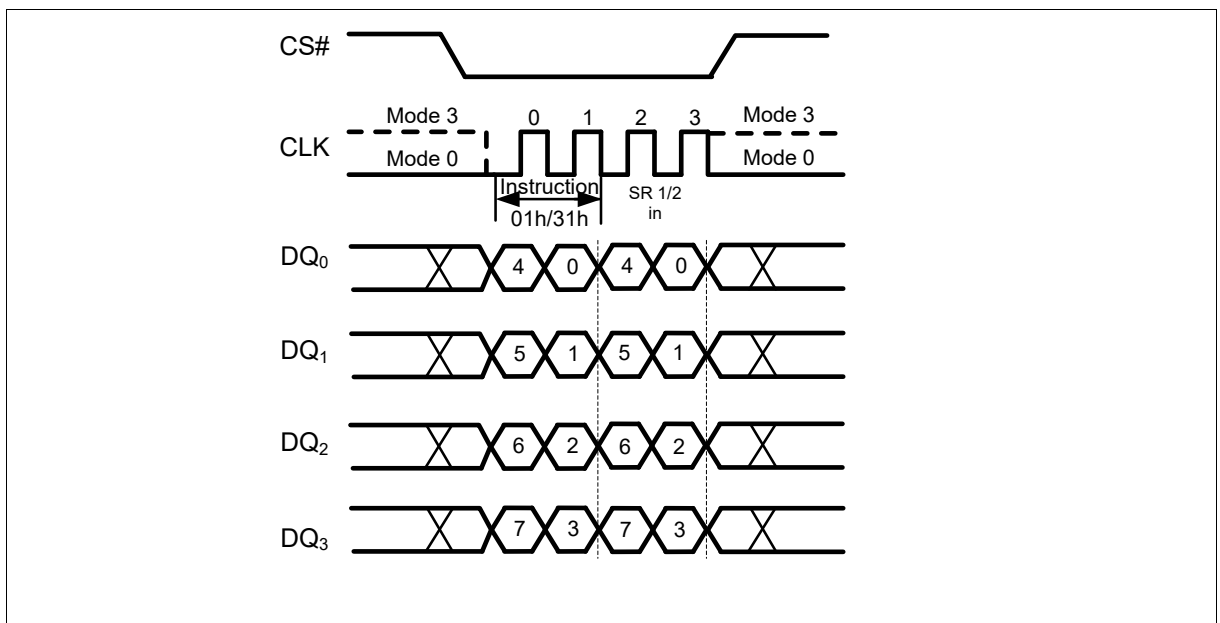


Figure 12 Write Status Register Instruction (QPI Mode)

11.11. Read Data (03h)

The Read Data instruction allows one or more data bytes to be sequentially read from the memory. The instruction is initiated by driving the CS# pin low and then shifting the instruction code “03h” followed by a 24-bit address A23-A0 into the DI pin. The code and address bits are latched on the rising edge of the CLK pin. After the address is received, the data byte of the addressed memory location will be shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) first. The address is automatically incremented to the next higher address after each byte of data is shifted out allowing for a continuous stream of data. This means that the entire memory can be accessed with a single instruction as long as the clock continues. The instruction is completed by driving CS# high.

The Read Data instruction sequence is shown in Figure 136. If a Read Data instruction is issued while an Erase, Program or Write cycle is in process (WIP =1) the instruction is ignored and will not have any effect on the current cycle. The Read Data instruction allows clock rates from D.C. to a maximum of f_R (see “12.6AC Electrical Characteristics”).

The Read Data (03h) instruction is only supported in Standard SPI mode.

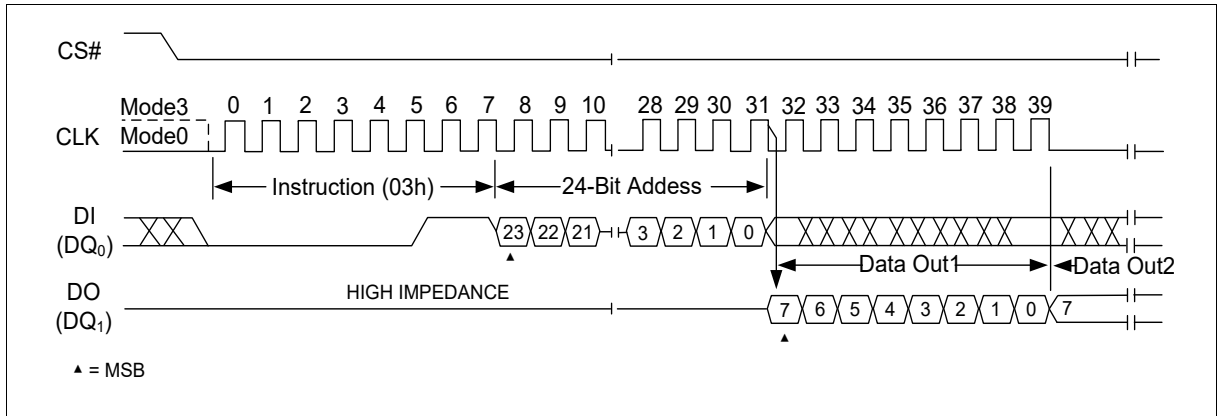


Figure 13 Read Data Instruction (SPI Mode only)

11.12. Fast Read (0Bh)

The Fast Read instruction is similar to the Read Data instruction except that it can operate at the highest possible frequency of F_R (see “12.6AC Electrical Characteristics”). This is accomplished by adding eight “dummy” clocks after the 24-bit address as shown in Figure 14. The dummy clocks allow the devices internal circuits additional time for setting up the initial address. During the dummy clocks the data value on the DI pin is a “don’t care”.

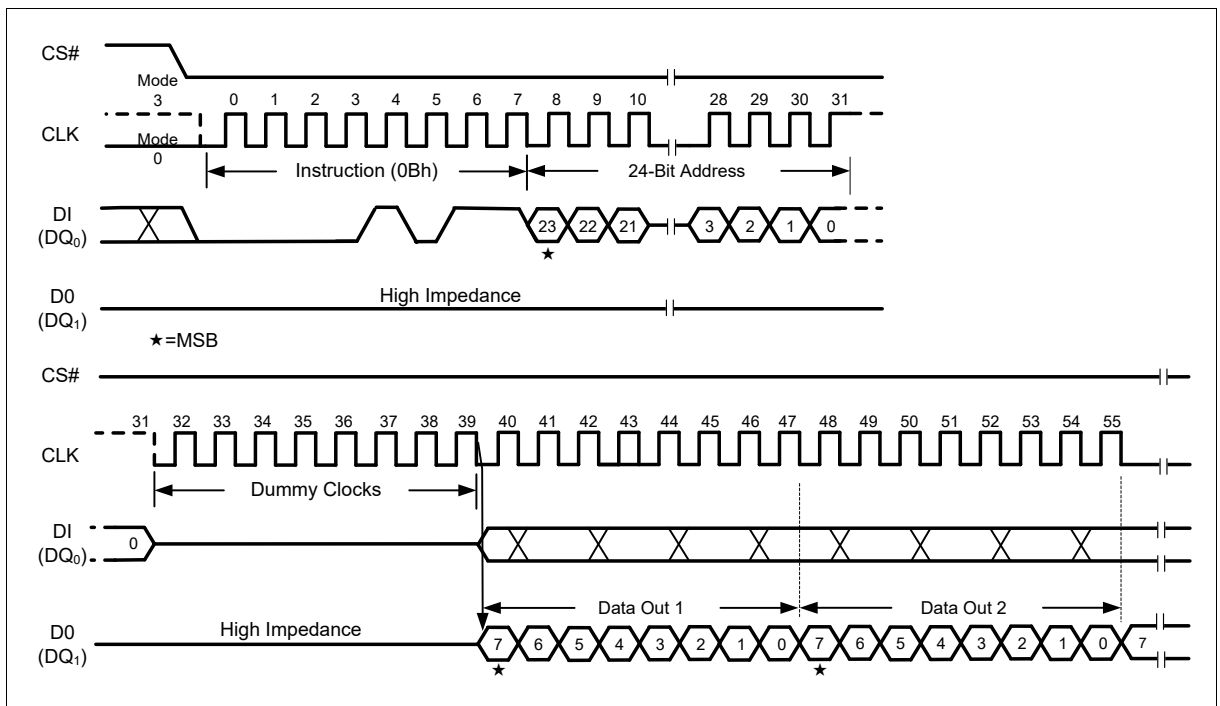


Figure 14 Fast Read Instruction (SPI Mode)

Fast Read (0Bh) in QPI Mode

The Fast Read instruction is also supported in QPI mode. When QPI mode is enabled, the number of dummy clocks is configured by the “Set Read Parameters (C0h)” instruction to accommodate wide range applications with different needs for either maximum Fast Read frequency or minimum data access latency. Depending on the Read Parameter Bits P[5:4] setting, the number of dummy clocks can be configured as either 2, 4, 6 or 8. The default number of dummy clocks upon power up or after a Reset instruction is 2.

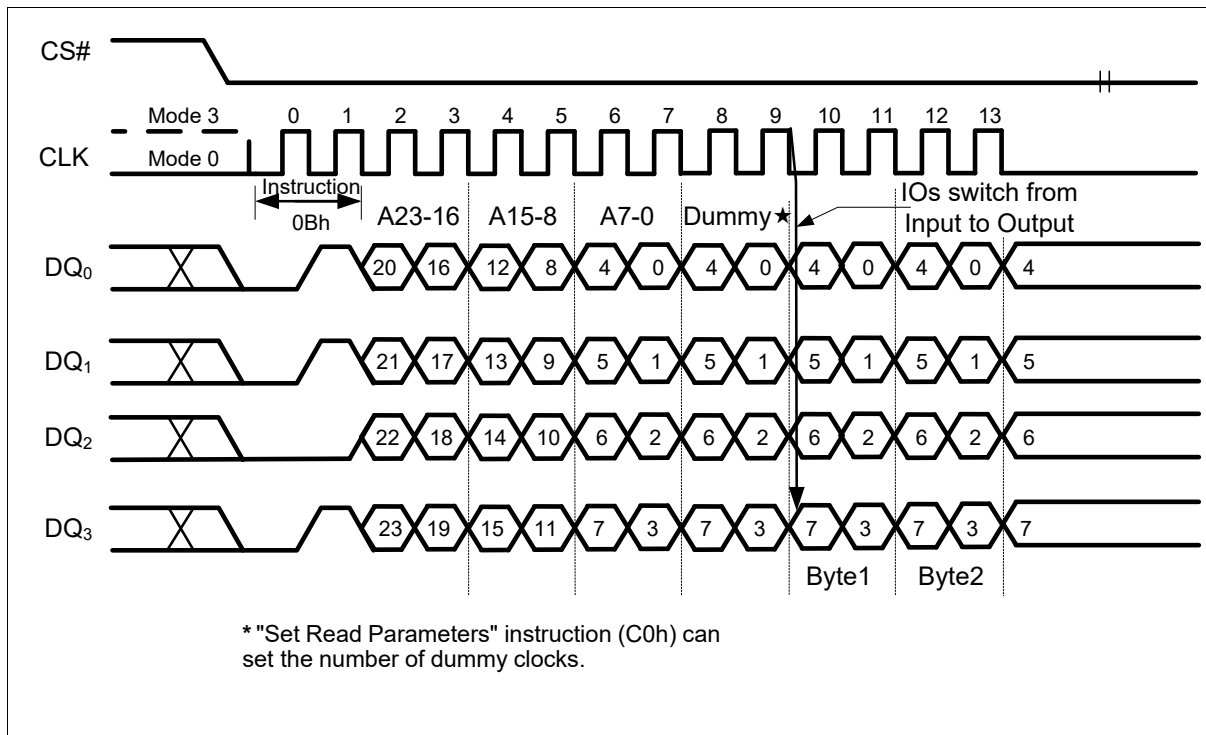


Figure 15 Fast Read Instruction (QPI Mode)

11.13. Fast Read Dual Output (3Bh)

The Fast Read Dual Output (3Bh) instruction is similar to the standard Fast Read (0Bh) instruction except that data is output on two pins; DQ₀ and DQ₁. This allows data to be transferred from the FM25W04I3 at twice the rate of standard SPI devices. The Fast Read Dual Output instruction is ideal for quickly downloading code from Flash to RAM upon power-up or for applications that cache code-segments to RAM for execution.

Similar to the Fast Read instruction, the Fast Read Dual Output instruction can operate at the highest possible frequency of F_R (see "12.6 AC Electrical Characteristics"). This is accomplished by adding eight "dummy" clocks after the 24-bit address as shown in Figure 16. The dummy clocks allow the device's internal circuits additional time for setting up the initial address. The input data during the dummy clocks is "don't care". However, the DQ₀ pin should be high-impedance prior to the falling edge of the first data out clock.

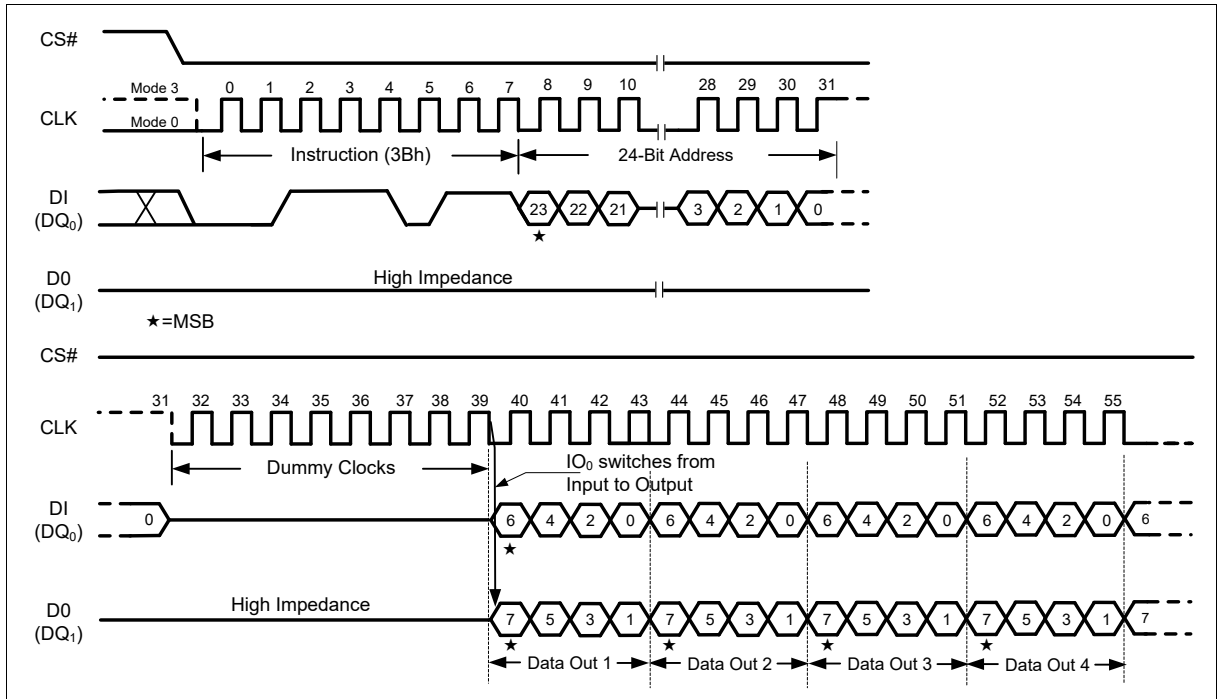


Figure 16 Fast Read Dual Output Instruction (SPI Mode only)

11.14. Fast Read Quad Output (6Bh)

The Fast Read Quad Output (6Bh) instruction is similar to the Fast Read Dual Output (3Bh) instruction except that data is output on four pins, DQ₀, DQ₁, DQ₂, and DQ₃. The Fast Read Quad Output Instruction allows data to be transferred from the FM25W04I3 at four times the rate of standard SPI devices.

The Fast Read Quad Output instruction can operate at the highest possible frequency of F_R (see “12.6AC Electrical Characteristics”). This is accomplished by adding eight “dummy” clocks after the 24-bit address as shown in Figure 17. The dummy clocks allow the device's internal circuits additional time for setting up the initial address. The input data during the dummy clocks is “don't care”. However, the DQ pins should be high-impedance prior to the falling edge of the first data out clock.

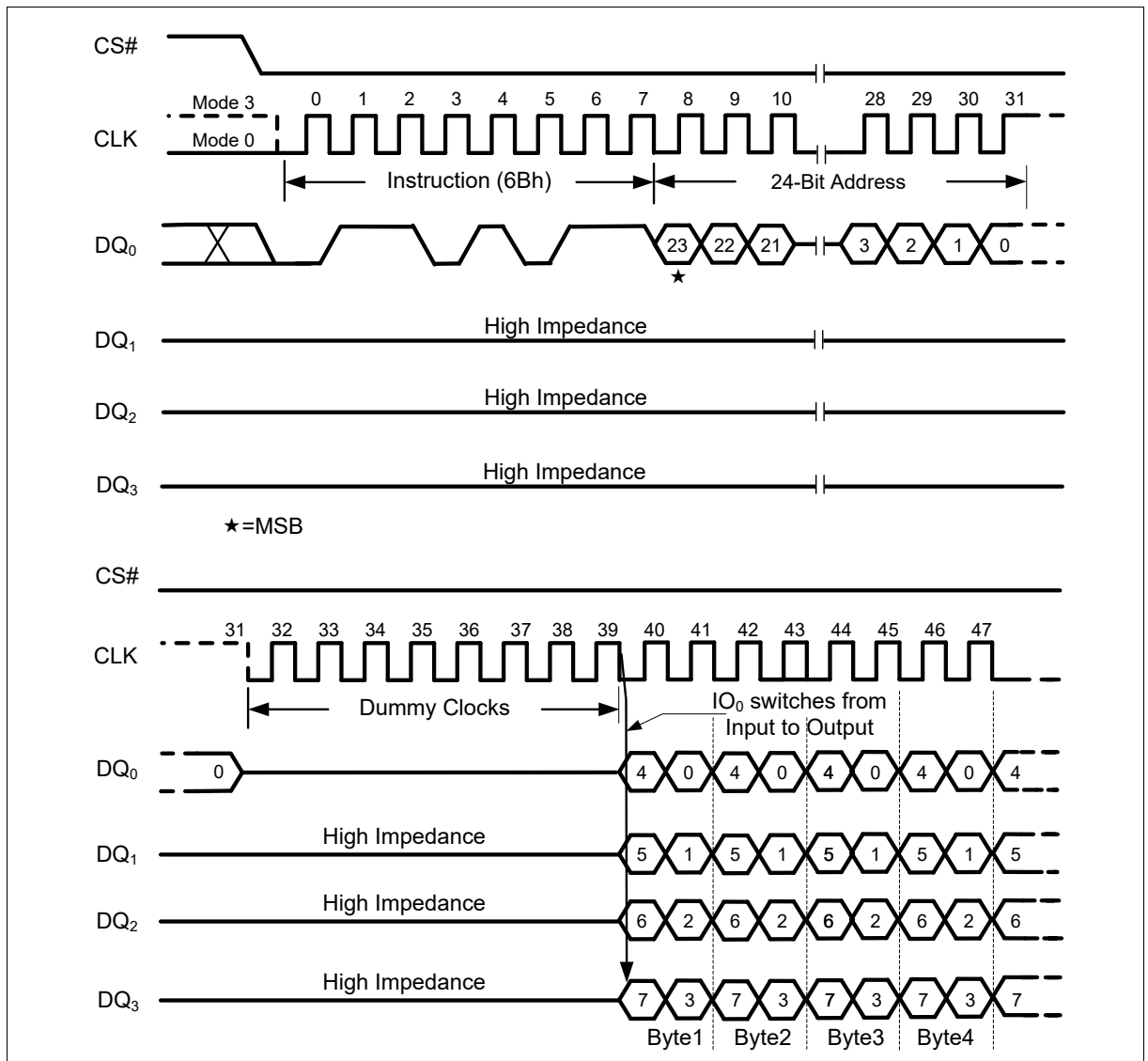


Figure 17 Fast Read Quad Output Instruction (SPI Mode only)

11.15. Fast Read Dual I/O (BBh)

The Fast Read Dual I/O (BBh) instruction allows for improved random access while maintaining two I/O pins, DQ₀ and DQ₁. It is similar to the Fast Read Dual Output (3Bh) instruction but with the capability to input the Address bits A23-A0 two bits per clock. This reduced instruction overhead may allow for code execution (XIP) directly from the Dual SPI in some applications.

Fast Read Dual I/O with “Continuous Read Mode”

The Fast Read Dual I/O instruction can further reduce instruction overhead through setting the “Continuous Read Mode” bits (M7-0) after the input Address bits A23-A0, as shown in Figure 18. The upper nibble of the (M7-4) controls the length of the next Fast Read Dual I/O instruction through the inclusion or exclusion of the first byte instruction code. The lower nibble bits of the (M3-0) are “don’t care (‘x’).” However, the DQ pins should be high-impedance prior to the falling edge of the first data out clock.

If the “Continuous Read Mode” bits M5-4 = (1,0), then the next Fast Read Dual I/O instruction (after CS# is raised and then lowered) does not require the BBh instruction code, as shown in Figure 19. This reduces the instruction sequence by eight clocks and allows the Read address to

be immediately entered after CS# is asserted low. If the “Continuous Read Mode” bits M5-4 do not equal to (10), the next instruction (after CS# is raised and then lowered) requires the first byte instruction code, thus returning to normal operation. It is recommended to input FFFFh on DQ₀ for the next (8 clocks), to ensure M4 = 1 and return the device to normal operation.

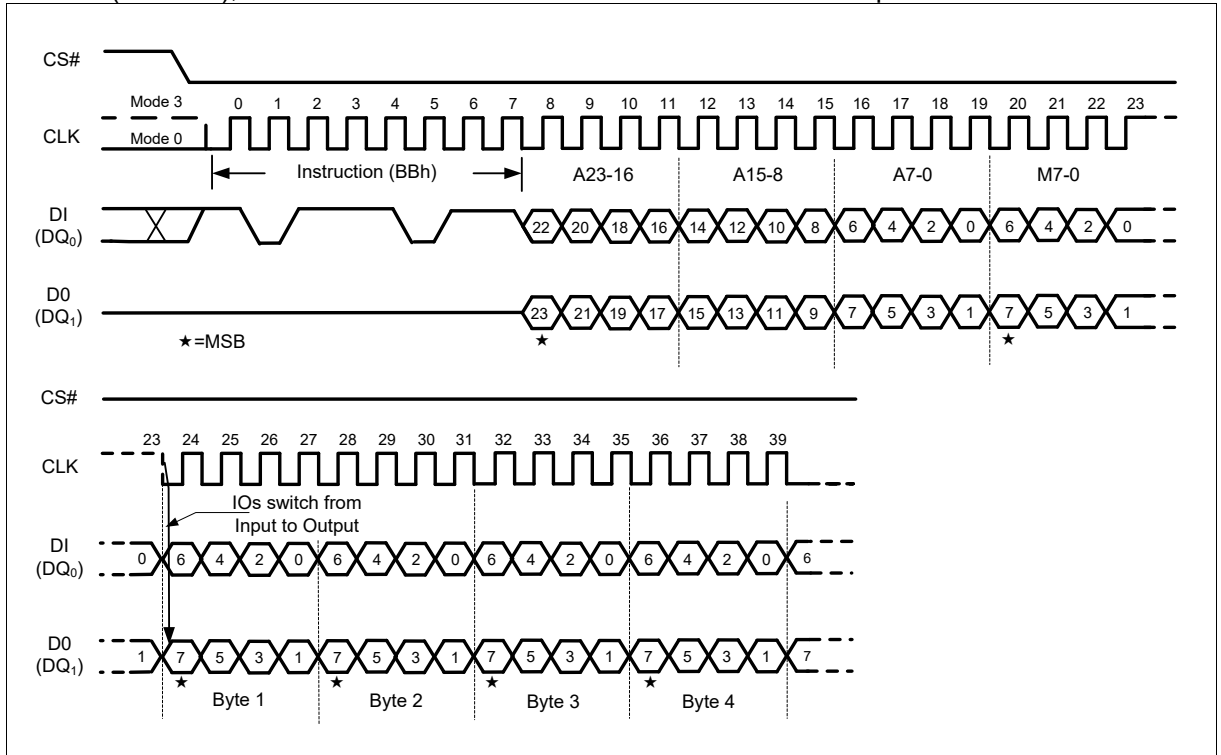


Figure 18 Fast Read Dual I/O Instruction (Initial instruction or previous M5-4 ≠ 10, SPI Mode only)

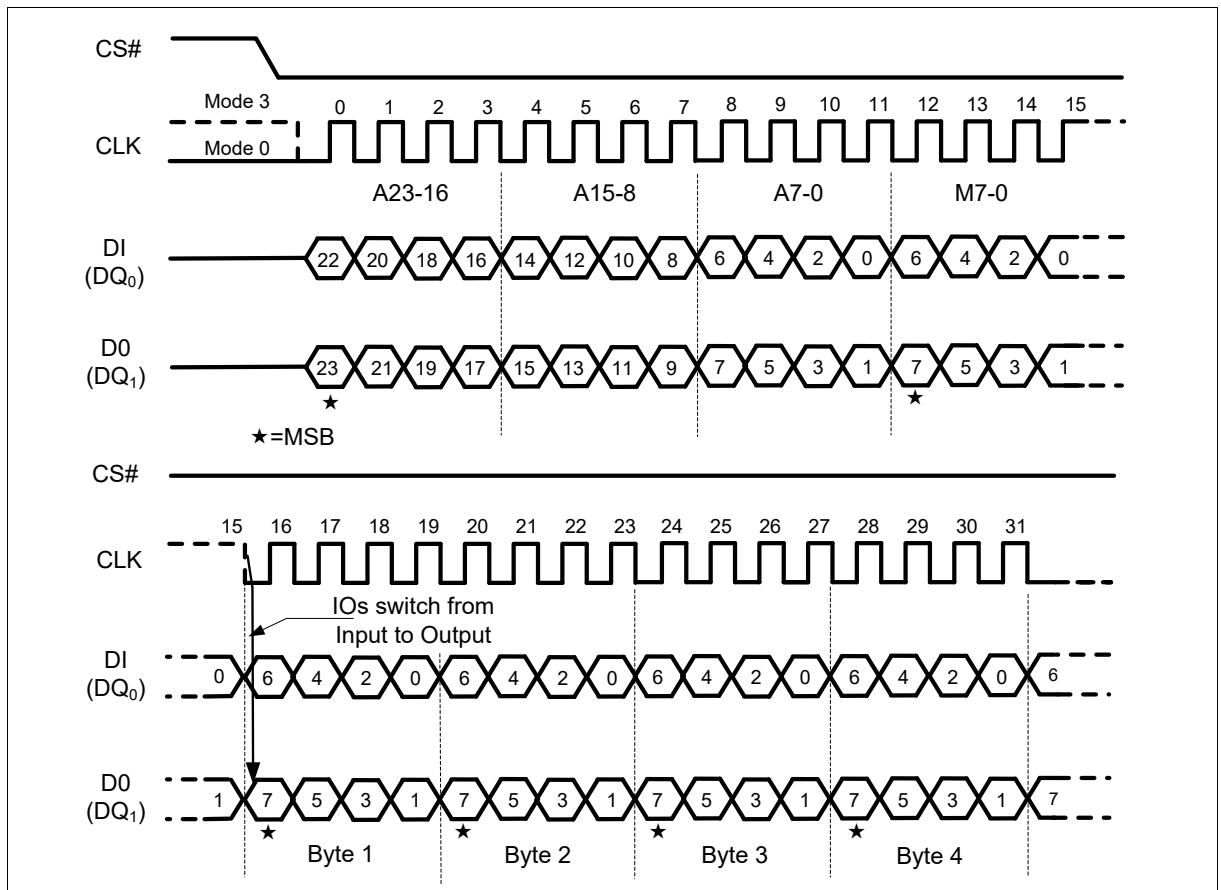


Figure 19 Fast Read Dual I/O Instruction (Previous instruction set M5-4 = 10, SPI Mode only)

11.16. Fast Read Quad I/O (EBh)

The Fast Read Quad I/O (EBh) instruction is similar to the Fast Read Dual I/O (BBh) instruction except that address and data bits are input and output through four pins DQ₀, DQ₁, DQ₂ and DQ₃ and four Dummy clocks are required in SPI mode prior to the data output. The Quad I/O dramatically reduces instruction overhead allowing faster random access for code execution (XIP) directly from the Quad SPI.

Fast Read Quad I/O with “Continuous Read Mode”

The Fast Read Quad I/O instruction can further reduce instruction overhead through setting the “Continuous Read Mode” bits (M7-0) after the input Address bits A23-A0, as shown in Figure 20. The upper nibble of the (M7-4) controls the length of the next Fast Read Quad I/O instruction through the inclusion or exclusion of the first byte instruction code. The lower nibble bits of the (M3-0) are “don’t care (“x”)”. However, the DQ pins should be high-impedance prior to the falling edge of the first data out clock.

If the “Continuous Read Mode” bits M5-4 = (1,0), then the next Fast Read Quad I/O instruction (after CS# is raised and then lowered) does not require the EBh instruction code, as shown in Figure 21. This reduces the instruction sequence by eight clocks and allows the Read address to be immediately entered after CS# is asserted low. If the “Continuous Read Mode” bits M5-4 do not equal to (1,0), the next instruction (after CS# is raised and then lowered) requires the first byte instruction code, thus returning to normal operation. It is recommended to input FFh on DQ₀ for the next instruction (8 clocks), to ensure M4= 1 and return the device to normal operation.

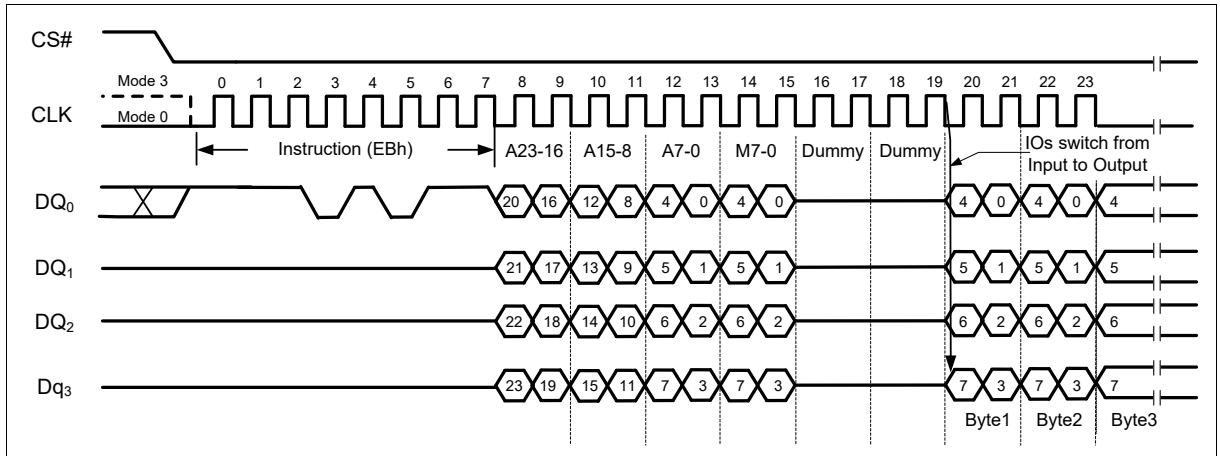


Figure 20 Fast Read Quad I/O Instruction (Initial instruction or previous M5-4≠10, SPI Mode)

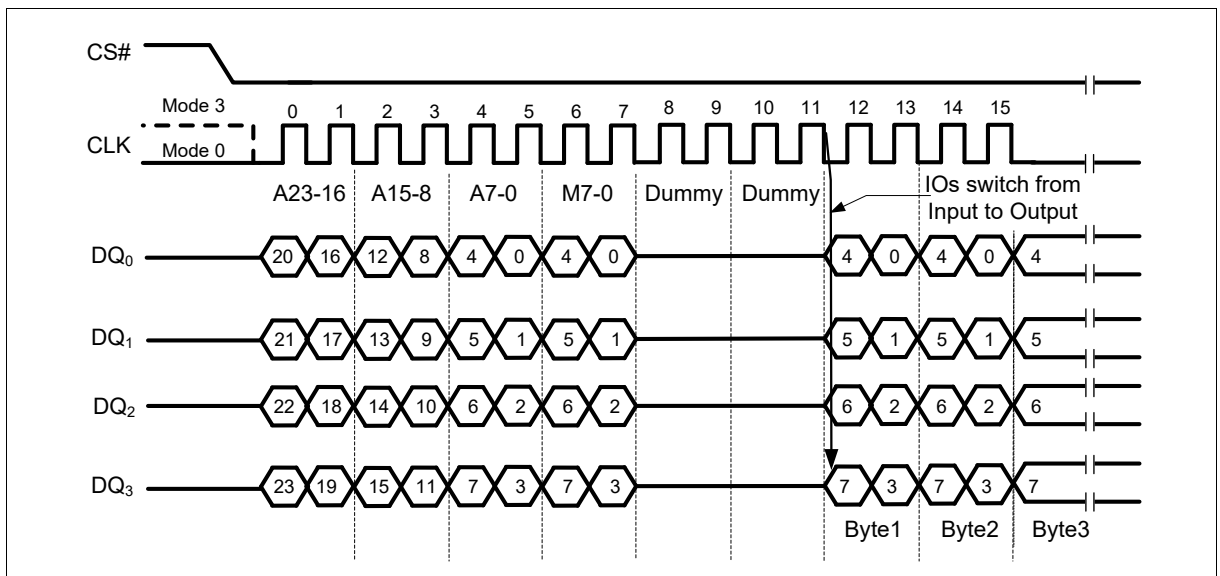


Figure 21 Fast Read Quad I/O Instruction (Previous instruction set M5-4 = 10, SPI Mode)

Fast Read Quad I/O with “8/16/32/64-Byte Wrap Around” in Standard SPI mode

The Fast Read Quad I/O instruction can also be used to access a specific portion within a page by issuing a “Set Burst with Wrap” (77h) command prior to EBh. The “Set Burst with Wrap” (77h) command can either enable or disable the “Wrap Around” feature for the following EBh commands. When “Wrap Around” is enabled, the data being accessed can be limited to either a 8, 16, 32 or 64-byte section of a 256-byte page. The output data starts at the initial address specified in the instruction, once it reaches the ending boundary of the 8/16/32/64-byte section, the output will wrap around to the beginning boundary automatically until CS# is pulled high to terminate the command.

The Burst with Wrap feature allows applications that use cache to quickly fetch a critical address and then fill the cache afterwards within a fixed length (8/16/32/64-byte) of data without issuing multiple read commands.

The “Set Burst with Wrap” instruction allows three “Wrap Bits”, W6-4 to be set. The W4 bit is used to enable or disable the “Wrap Around” operation while W6-5 are used to specify the length of the wrap around section within a page. See “11.19Set Burst with Wrap (77h)” for detail descriptions.

Fast Read Quad I/O (EBh) in QPI Mode

The Fast Read Quad I/O instruction is also supported in QPI mode, as shown in Figure 22. When QPI mode is enabled, the number of dummy clocks is configured by the “Set Read Parameters (C0h)” instruction to accommodate a wide range application with different needs for either maximum Fast Read frequency or minimum data access latency. Depending on the Read Parameter Bits P[5:4] setting, the number of dummy clocks can be configured as either 2, 4, 6 or 8. The default number of dummy clocks upon power up or after a Reset instruction is 2. In QPI mode, the “Continuous Read Mode” bits M7-0 are also considered as dummy clocks. In the default setting, the data output will follow the Continuous Read Mode bits immediately.

“Continuous Read Mode” feature is also available in QPI mode for Fast Read Quad I/O instruction. Please refer to the description on previous pages.

“Wrap Around” feature is not available in QPI mode for Fast Read Quad I/O instruction. To perform a read operation with fixed data length wrap around in QPI mode, a dedicated “Burst Read with Wrap” (0Ch) instruction must be used. Please refer to “11.38Burst Read with Wrap (0Ch)” for details.

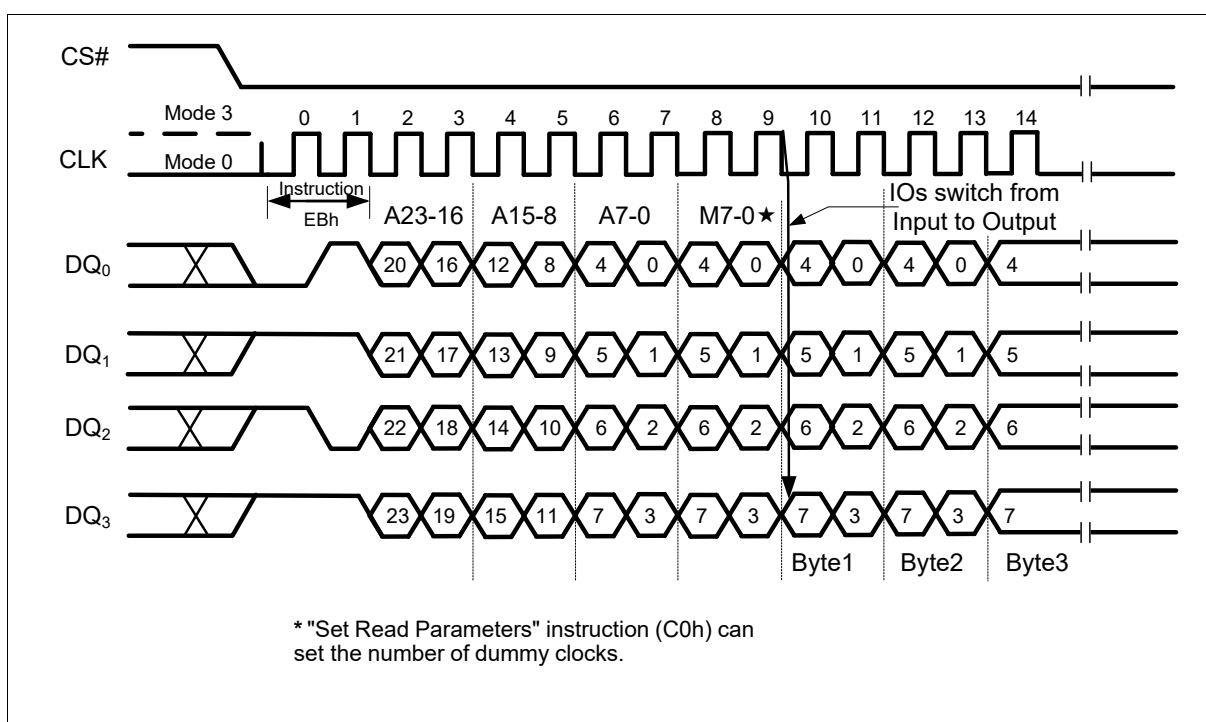


Figure 22 Fast Read Quad I/O Instruction (Initial instruction or previous M5-4#10, QPI Mode)

11.17. Word Read Quad I/O (E7h)

The Word Read Quad I/O (E7h) instruction is similar to the Fast Read Quad I/O (EBh) instruction except that the lowest Address bit (A0) must equal 0 and only two Dummy clock are required prior to the data output. The Quad I/O dramatically reduces instruction overhead allowing faster random access for code execution (XIP) directly from the Quad SPI.

Word Read Quad I/O with “Continuous Read Mode”

The Word Read Quad I/O instruction can further reduce instruction overhead through setting the “Continuous Read Mode” bits (M7-0) after the input Address bits A23-A0, as shown in Figure 23. The upper nibble of the (M7-4) controls the length of the next Fast Read Quad I/O instruction

through the inclusion or exclusion of the first byte instruction code. The lower nibble bits of the (M3-0) are “don’t care (“x”)”. However, the DQ pins should be high-impedance prior to the falling edge of the first data out clock.

If the “Continuous Read Mode” bits M5-4 = (1,0), then the next Fast Read Quad I/O instruction (after CS# is raised and then lowered) does not require the E7h instruction code, as shown in Figure 24. This reduces the instruction sequence by eight clocks and allows the Read address to be immediately entered after CS# is asserted low. If the “Continuous Read Mode” bits M5-4 do not equal to (1,0), the next instruction (after CS# is raised and then lowered) requires the first byte instruction code, thus returning to normal operation. It is recommended to input FFh on DQ₀ for the next instruction (8 clocks), to ensure M4 = 1 and return the device to normal operation.

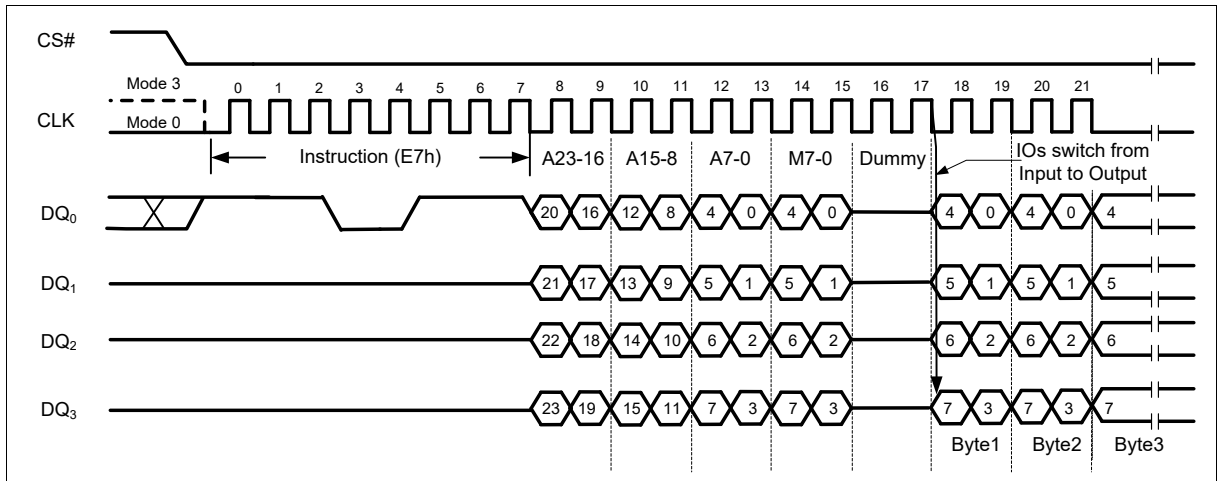


Figure 23 Word Read Quad I/O Instruction (Initial instruction or previous M5-4 ≠ 10, SPI Mode only)

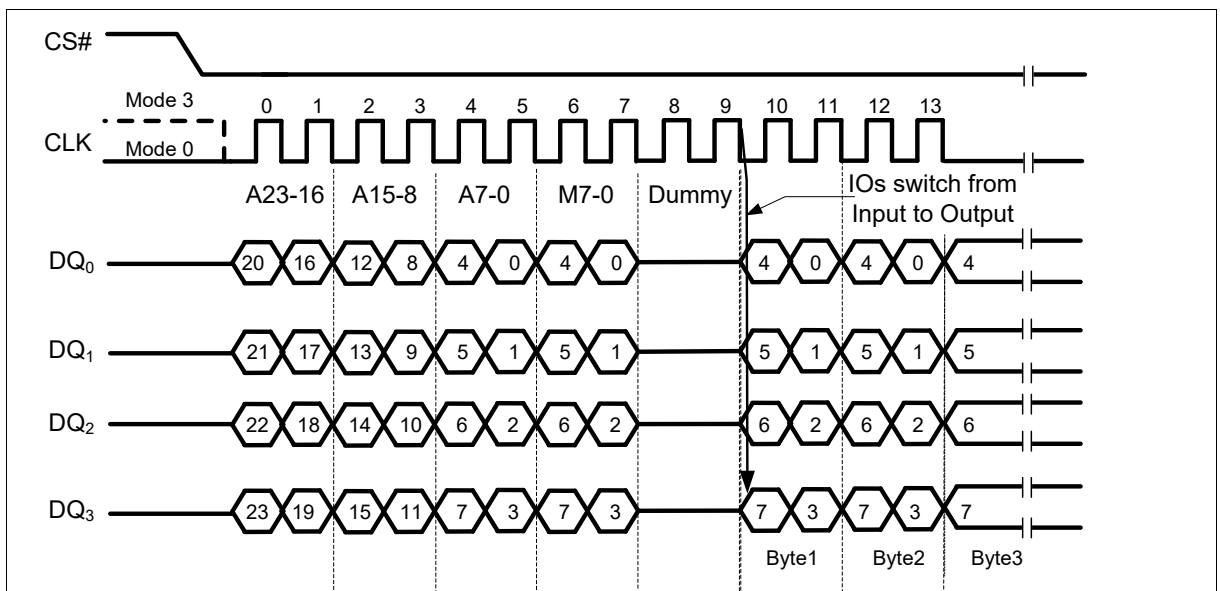


Figure 24 Word Read Quad I/O Instruction (Previous instruction set M5-4 = 10, SPI Mode only)

Word Read Quad I/O with “8/16/32/64-Byte Wrap Around” in Standard SPI mode

The Word Read Quad I/O instruction can also be used to access a specific portion within a page by issuing a “Set Burst with Wrap” (77h) command prior to E7h. The “Set Burst with Wrap” (77h) command can either enable or disable the “Wrap Around” feature for the following E7h

commands. When “Wrap Around” is enabled, the data being accessed can be limited to either a 8, 16, 32 or 64-byte section of a 256-byte page. The output data starts at the initial address specified in the instruction, once it reaches the ending boundary of the 8/16/32/64-byte section, the output will wrap around to the beginning boundary automatically until CS# is pulled high to terminate the command.

The Burst with Wrap feature allows applications that use cache to quickly fetch a critical address and then fill the cache afterwards within a fixed length (8/16/32/64-byte) of data without issuing multiple read commands.

The “Set Burst with Wrap” instruction allows three “Wrap Bits”, W6-4 to be set. The W4 bit is used to enable or disable the “Wrap Around” operation while W6-5 bits are used to specify the length of the wrap around section within a page. See “11.19 Set Burst with Wrap (77h)” for detail descriptions.

11.18. Octal Word Read Quad I/O (E3h)

The Octal Word Read Quad I/O (E3h) instruction is similar to the Fast Read Quad I/O (EBh) instruction except that the lower four Address bits (A0, A1, A2, A3) must equal 0. As a result, the dummy clocks are not required, which further reduces the instruction overhead allowing even faster random access for code execution (XIP).

Octal Word Read Quad I/O with “Continuous Read Mode”

The Octal Word Read Quad I/O instruction can further reduce instruction overhead through setting the “Continuous Read Mode” bits M7-M0 after the input Address bits A23-A0, as shown in Figure 25. The upper nibble of the (M7-4) controls the length of the next Octal Word Read Quad I/O instruction through the inclusion or exclusion of the first byte instruction code. The lower nibble bits of the (M3-0) are “don’t care (‘x’)”. However, the DQ pins should be high-impedance prior to the falling edge of the first data out clock.

If the “Continuous Read Mode” bits M5-4 = (1,0), then the next Fast Read Quad I/O instruction (after CS# is raised and then lowered) does not require the E3h instruction code, as shown in Figure 26. This reduces the instruction sequence by eight clocks and allows the Read address to be immediately entered after CS# is asserted low. If the “Continuous Read Mode” bits M5-4 do not equal to (1,0), the next instruction (after CS# is raised and then lowered) requires the first byte instruction code, thus returning to normal operation. It is recommended to input FFh on DQ₀ for the next instruction (8 clocks), to ensure M4 = 1 and return the device to normal operation.

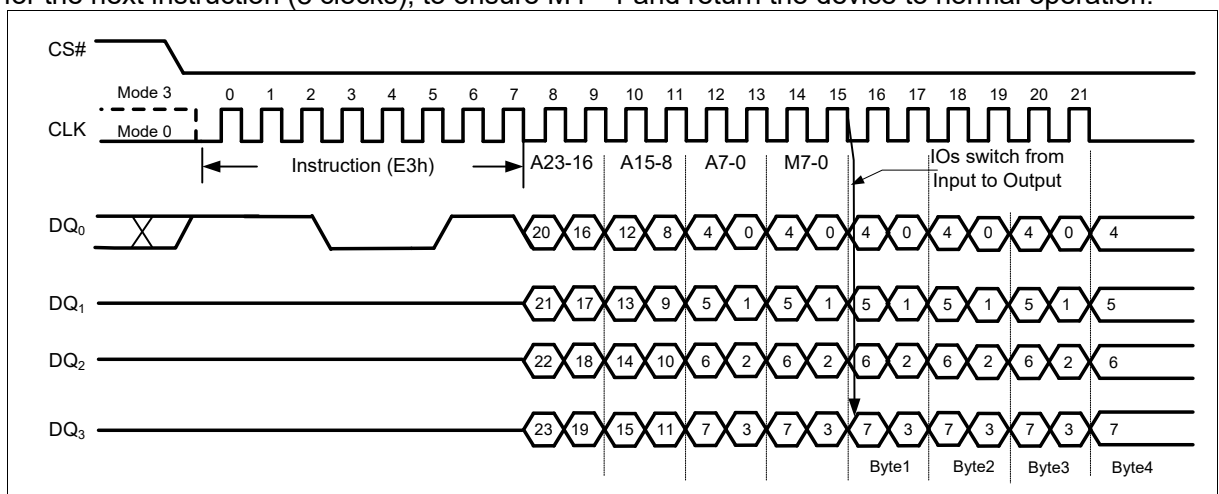


Figure 25 Octal Word Read Quad I/O Instruction (Initial instruction or previous M5-4 ≠ 10, SPI Mode only)

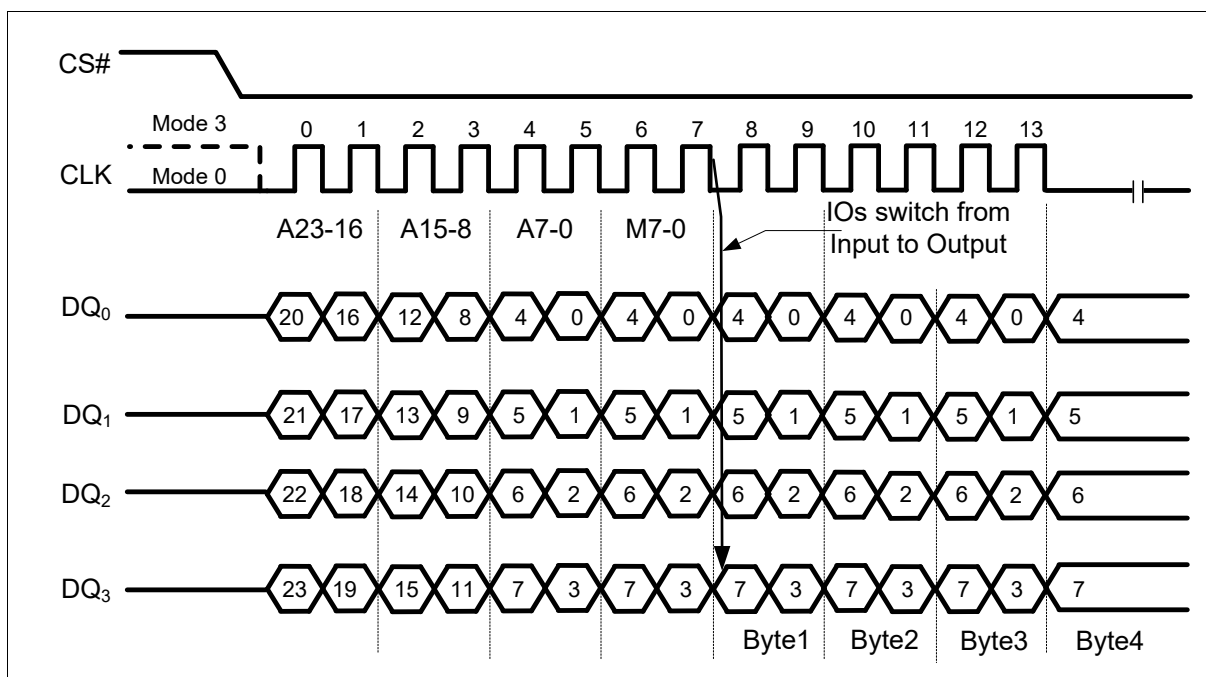


Figure 26 Octal Word Read Quad I/O Instruction (Previous instruction set M5-4 = 10, SPI Mode only)

11.19. Set Burst with Wrap (77h)

In Standard SPI mode, the Set Burst with Wrap (77h) instruction is used in conjunction with “Fast Read Quad I/O” and “Word Read Quad I/O” instructions to access a fixed length of 8/16/32/64-byte section within a 256-byte page. Certain applications can benefit from this feature and improve the overall system code execution performance.

Similar to a Quad I/O instruction, the Set Burst with Wrap instruction is initiated by driving the CS# pin low and then shifting the instruction code “77h” followed by 24 dummy bits and 8 “Wrap Bits”, W7-0. The instruction sequence is shown in Figure 27. Wrap bit W7 and the lower nibble W3-0 are not used.

W6, W5	W4 = 0		W4 =1 (default)	
	Wrap Around	Wrap Length	Wrap Around	Wrap Length
00	Yes	8-byte	No	N/A
01	Yes	16-byte	No	N/A
10	Yes	32-byte	No	N/A
11	Yes	64-byte	No	N/A

Once W6-4 is set by a Set Burst with Wrap instruction, all the following “Fast Read Quad I/O” and “Word Read Quad I/O” instructions will use the W6-4 setting to access the 8/16/32/64-byte section within any page. To exit the “Wrap Around” function and return to normal read operation, another Set Burst with Wrap instruction should be issued to set W4 = 1. The default value of W4 upon power on is 1. In the case of a system Reset while W4 = 0, it is recommended that the controller issues a Set Burst with Wrap instruction to reset W4 = 1 prior to any normal Read instructions since FM25W0413 does not have a hardware Reset Pin.

In QPI mode, the “Burst Read with Wrap (0Ch)” instruction should be used to perform the Read operation with “Wrap Around” feature. The Wrap Length set by W5-4 in Standard SPI mode is still valid in QPI mode and can also be re-configured by “Set Read Parameters (C0h)” instruction.

Refer to “11.37 Set Read Parameters (C0h)” and “11.38 Burst Read with Wrap (0Ch)” for details.

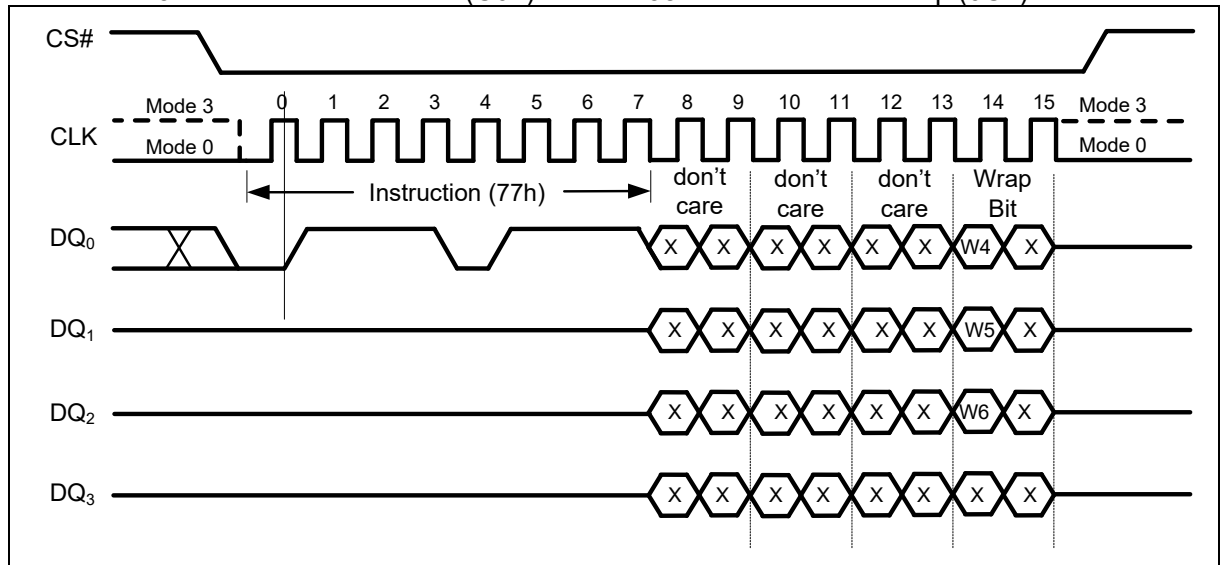


Figure 27 Set Burst with Wrap Instruction (SPI Mode only)

11.20. Page Program (02h)

The Page Program instruction allows from one byte to 256 bytes (a page) of data to be programmed at previously erased (FFh) memory locations. A Write Enable instruction must be executed before the device will accept the Page Program Instruction (Status Register bit WEL= 1). The instruction is initiated by driving the CS# pin low then shifting the instruction code “02h” followed by a 24-bit address A23-A0 and at least one data byte, into the DI pin. The CS# pin must be held low for the entire length of the instruction while data is being sent to the device. The Page Program instruction sequence is shown in Figure 28 and Figure 29.

If an entire 256 byte page is to be programmed, the last address byte (the 8 least significant address bits) should be set to 0. If the last address byte is not zero, and the number of clocks exceeds the remaining page length, the addressing will wrap to the beginning of the page. In some cases, less than 256 bytes (a partial page) can be programmed without having any effect on other bytes within the same page. One condition to perform a partial page program is that the number of clocks can not exceed the remaining page length. If more than 256 bytes are sent to the device the addressing will wrap to the beginning of the page and overwrite previously sent data.

As with the write and erase instructions, the CS# pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Page Program instruction will not be executed. After CS# is driven high, the self-timed Page Program instruction will commence for time duration of t_{PP} (See “12.6AC Electrical Characteristics”). While the Page Program cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the WIP bit. The WIP bit is a 1 during the Page Program cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Page Program cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Page Program instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB, BP2-0) bits.

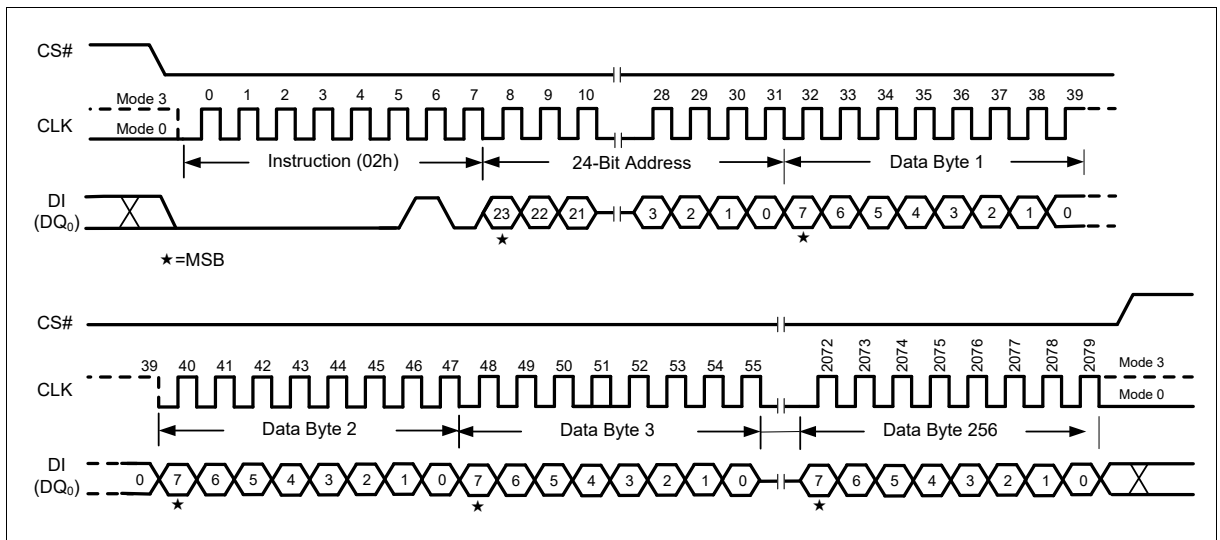


Figure 28 Page Program Instruction (SPI Mode)

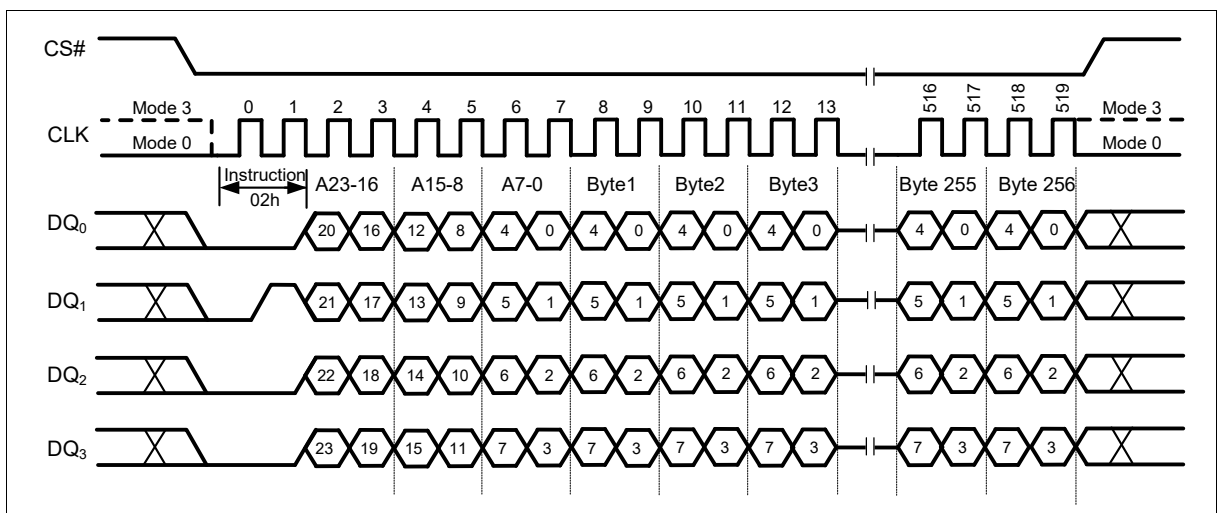


Figure 29 Page Program Instruction (QPI Mode)

11.21. Quad Input Page Program (32h)

The Quad Page Program instruction allows up to 256 bytes of data to be programmed at previously erased (FFh) memory locations using four pins: DQ₀, DQ₁, DQ₂, and DQ₃. The Quad Page Program can improve performance for PROM Programmer and applications that have slow clock speeds <5MHz. Systems with faster clock speed will not realize much benefit for the Quad Page Program instruction since the inherent page program time is much greater than the time it take to clock-in the data.

A Write Enable instruction must be executed before the device will accept the Quad Page Program instruction (Status Register-1, WEL=1). The instruction is initiated by driving the CS# pin low then shifting the instruction code “32h” followed by a 24-bit address A23-A0 and at least one data byte, into the DQ pins. The CS# pin must be held low for the entire length of the instruction while data is being sent to the device. All other functions of Quad Page Program are identical to standard Page Program. The Quad Page Program instruction sequence is shown in Figure 30.

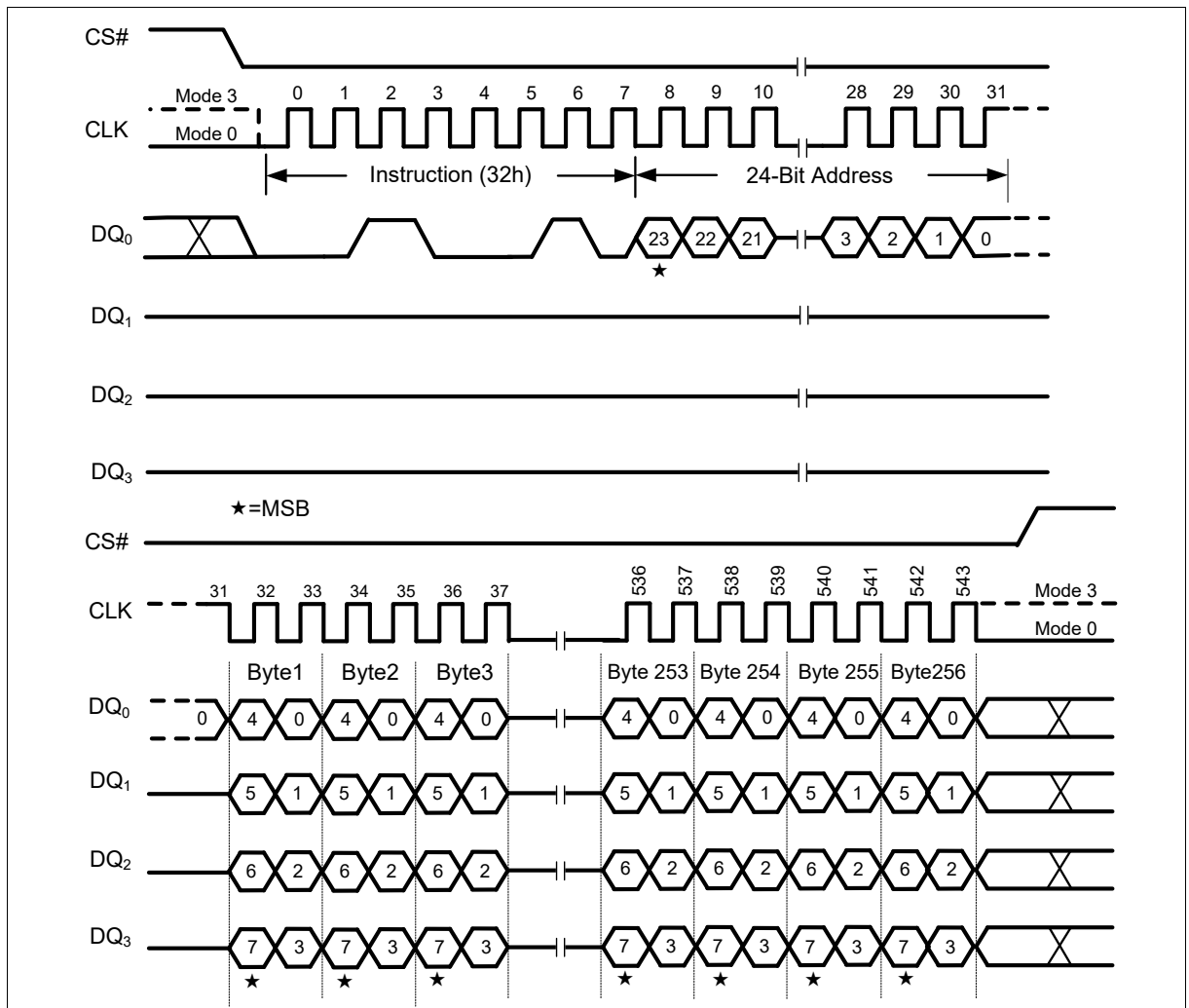


Figure 30 Quad Input Page Program Instruction (SPI Mode only)

11.22. Sector Erase (20h)

The Sector Erase instruction sets all memory within a specified sector (4K-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Sector Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the CS# pin low and shifting the instruction code “20h” followed a 24-bit sector address A23-A0 (see Figure 1). The Sector Erase instruction sequence is shown in Figure 31&Figure 32.

The CS# pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Sector Erase instruction will not be executed. After CS# is driven high, the self-timed Sector Erase instruction will commence for a time duration of t_{SE} (See “12.6AC Electrical Characteristics”). While the Sector Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the WIP bit. The WIP bit is a 1 during the Sector Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Sector Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Sector Erase instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB, BP2, BP1, and BP0) bits (see Table 3 Status Register Memory Protection table).

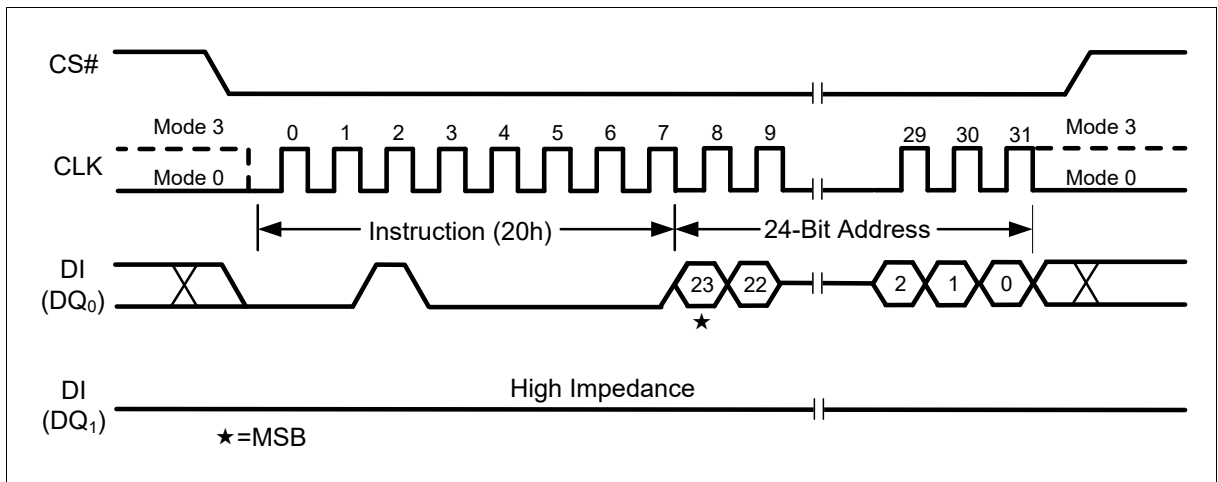


Figure 31 Sector Erase Instruction (SPI Mode)

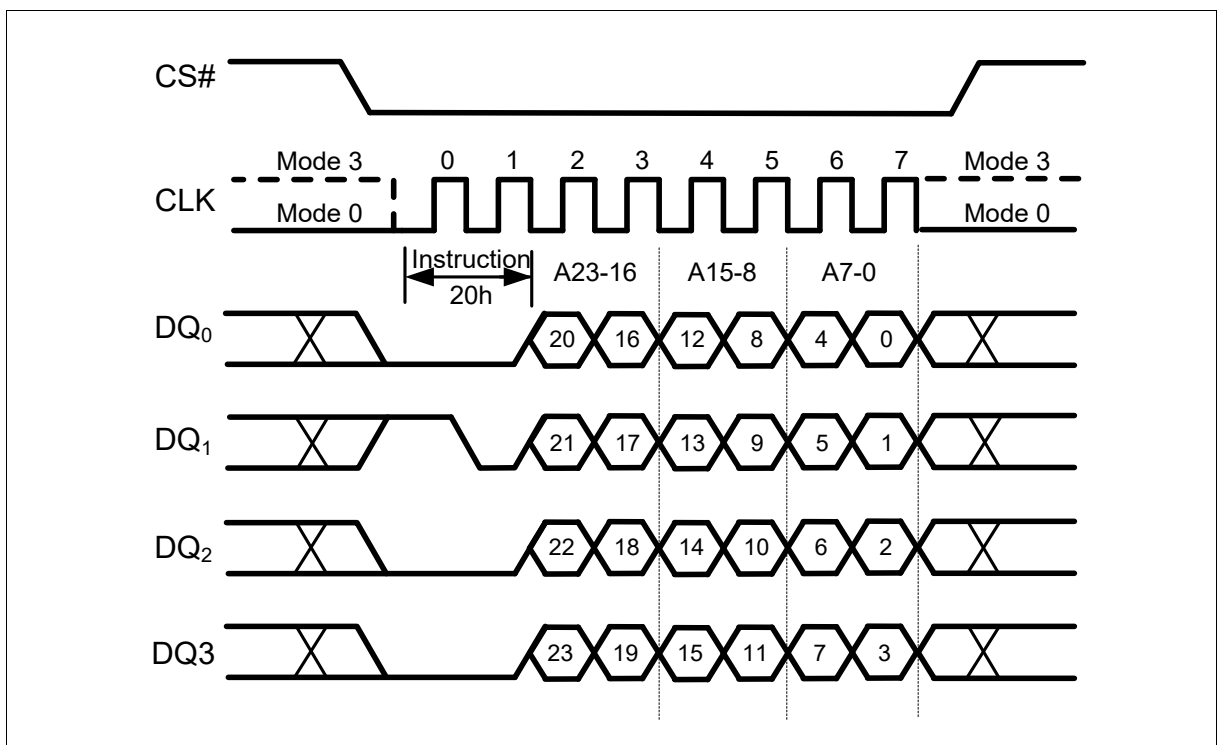


Figure 32 Sector Erase Instruction (QPI Mode)

11.23. 32KB Block Erase (BE32) (52h)

The 32KB Block Erase instruction sets all memory within a specified block (32K-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Block Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the CS# pin low and shifting the instruction code "52h" followed a 24-bit block address A23-A0. The Block Erase instruction sequence is shown in Figure 33&Figure 34.

The CS# pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Block Erase instruction will not be executed. After CS# is driven high, the self-timed Block Erase instruction will commence for time duration of t_{BE1} (See "12.6AC Electrical Characteristics"). While the Block Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the WIP bit. The WIP bit is a 1 during the Block

Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Block Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Block Erase instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB and BP2-0) bits (see Table 3 Status Register Memory Protection table).

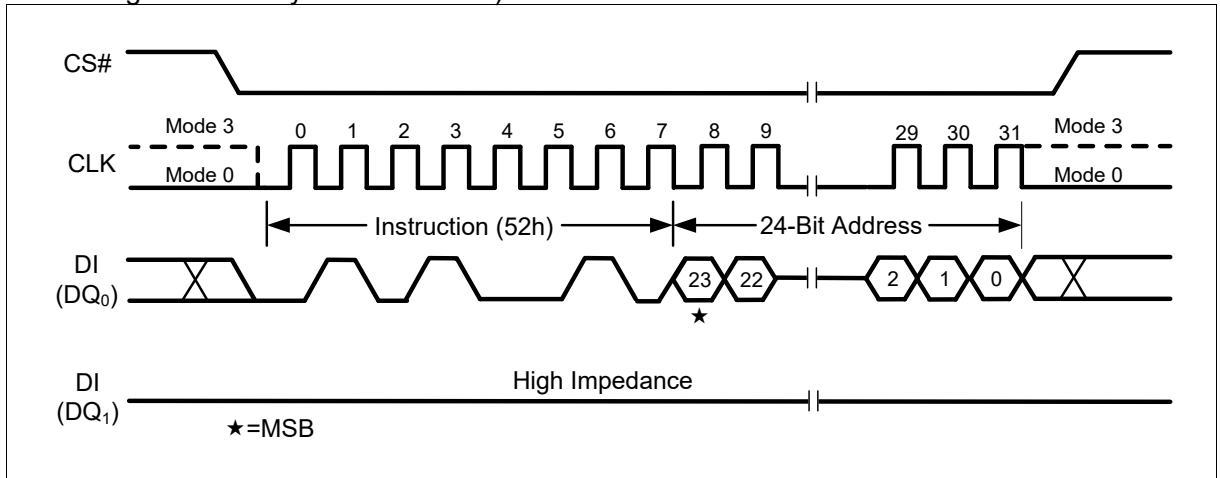


Figure 33 32KB Block Erase Instruction (SPI Mode)

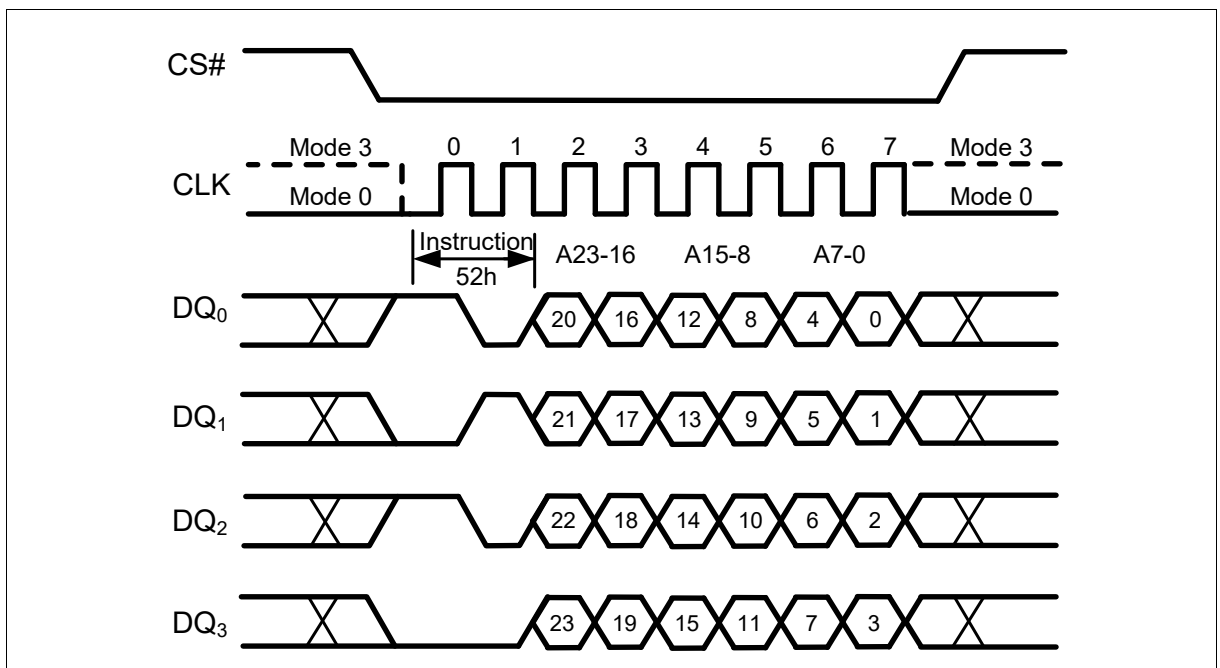


Figure 34 32KB Block Erase Instruction (QPI Mode)

11.24. 64KB Block Erase (BE) (D8h)

The 64KB Block Erase instruction sets all memory within a specified block (64K-bytes) to the erased state of all1s (FFh). A Write Enable instruction must be executed before the device will accept the Block Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the CS# pin low and shifting the instruction code “D8h” followed a 24-bit block address A23-A0. The Block Erase instruction sequence is shown in Figure 35&Figure 36.

The CS# pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Block Erase instruction will not be executed. After CS# is driven high, the self-timed

Block Erase instruction will commence for a time duration of t_{BE} (See 12.6AC Electrical Characteristics”). While the Block Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the WIP bit. The WIP bit is a 1 during the Block Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Block Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Block Erase instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB and BP2-0) bits (see Table 3 Status Register Memory Protection table).

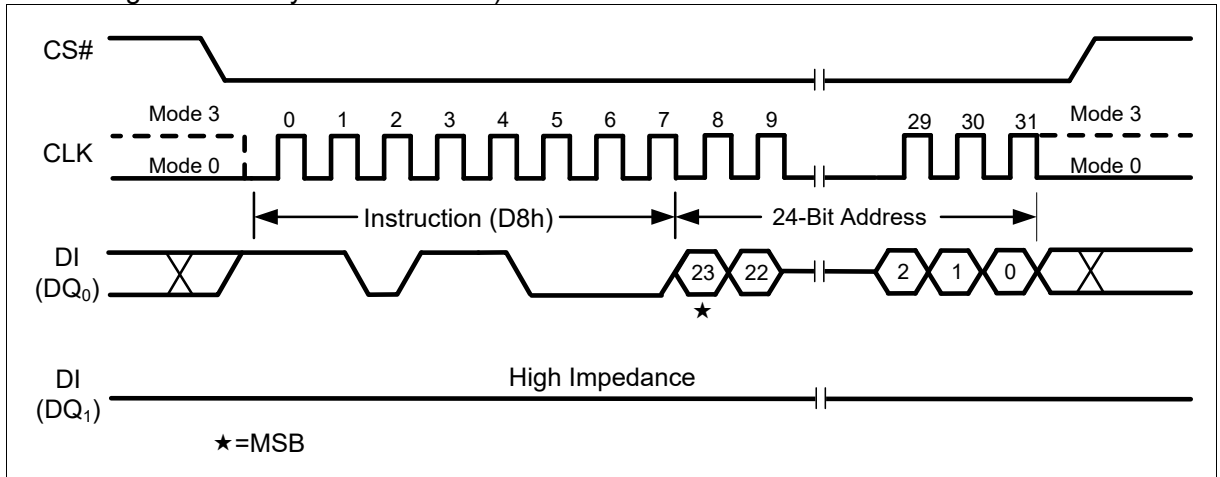


Figure 35 64KB Block Erase Instruction (SPI Mode)

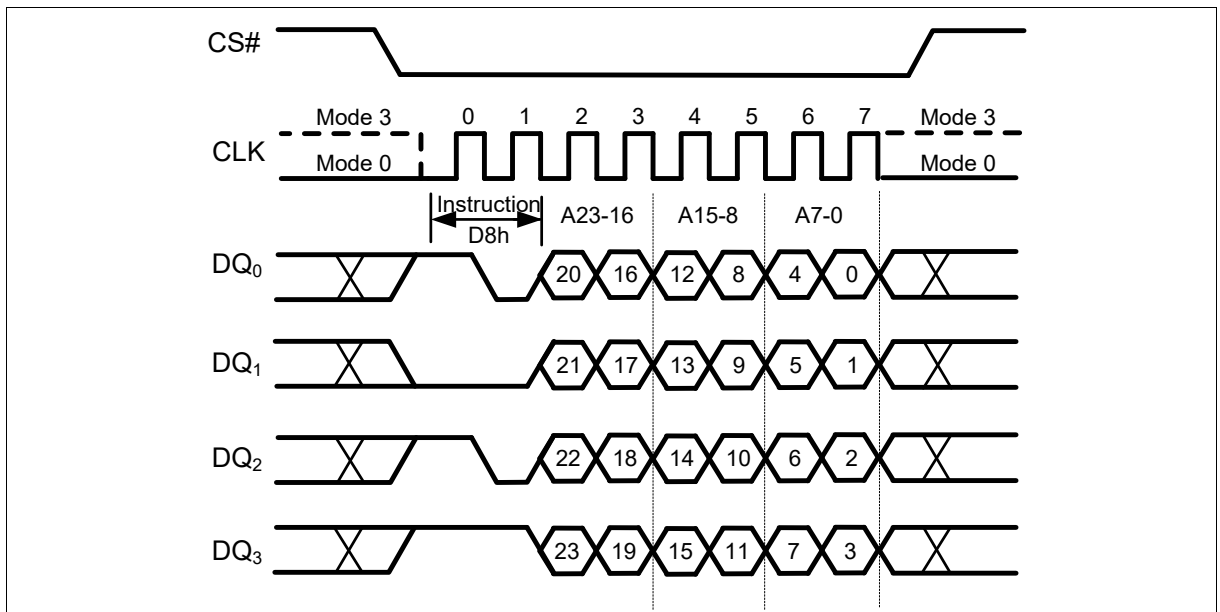


Figure 36 64KB Block Erase Instruction (QPI Mode)

11.25. Chip Erase (CE) (C7h / 60h)

The Chip Erase instruction sets all memory within the device to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Chip Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the CS# pin low and shifting the instruction code “C7h” or “60h”. The Chip Erase instruction sequence is shown in Figure 37.

The CS# pin must be driven high after the eighth bit has been latched. If this is not done the Chip Erase instruction will not be executed. After CS# is driven high, the self-timed Chip Erase instruction will commence for time duration of t_{CE} (See “12.6AC Electrical Characteristics”). While the Chip Erase cycle is in progress, the Read Status Register instruction may still be accessed to check the status of the WIP bit. The WIP bit is a 1 during the Chip Erase cycle and becomes a 0 when finished and the device is ready to accept other instructions again. After the Chip Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Chip Erase instruction will not be executed if any page is protected by the Block Protect (CMP, SEC, TB and BP2-0) bits.

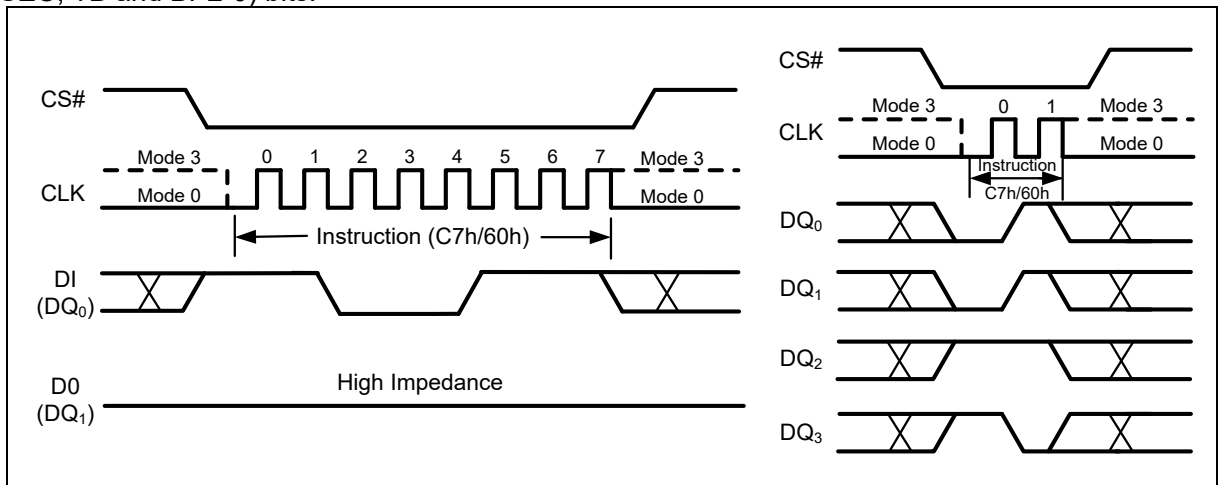


Figure 37 Chip Erase Instruction for SPI Mode (left) or QPI Mode (right)

11.26. Power-down (B9h)

Although the standby current during normal operation is relatively low, standby current can be further reduced with the Power-down instruction. The lower power consumption makes the Power-down instruction especially useful for battery powered applications (See I_{CC1} and I_{CC2} in “12.4DC Electrical Characteristics”). The instruction is initiated by driving the CS# pin low and shifting the instruction code “B9h” as shown in Figure 38&Figure 39.

The CS# pin must be driven high after the eighth bit has been latched. If this is not done the Power-down instruction will not be executed. After CS# is driven high, the power-down state will enter within the time duration of t_{DP} (See “12.6AC Electrical Characteristics”). While in the power-down state only the Release from Power-down / Device ID instruction, which restores the device to normal operation, will be recognized. All other instructions are ignored. This includes the Read Status Register instruction, which is always available during normal operation. Ignoring all but one instruction makes the Power Down state a useful condition for securing maximum write protection. The device always powers-up in the normal operation with the standby current of I_{CC1} .

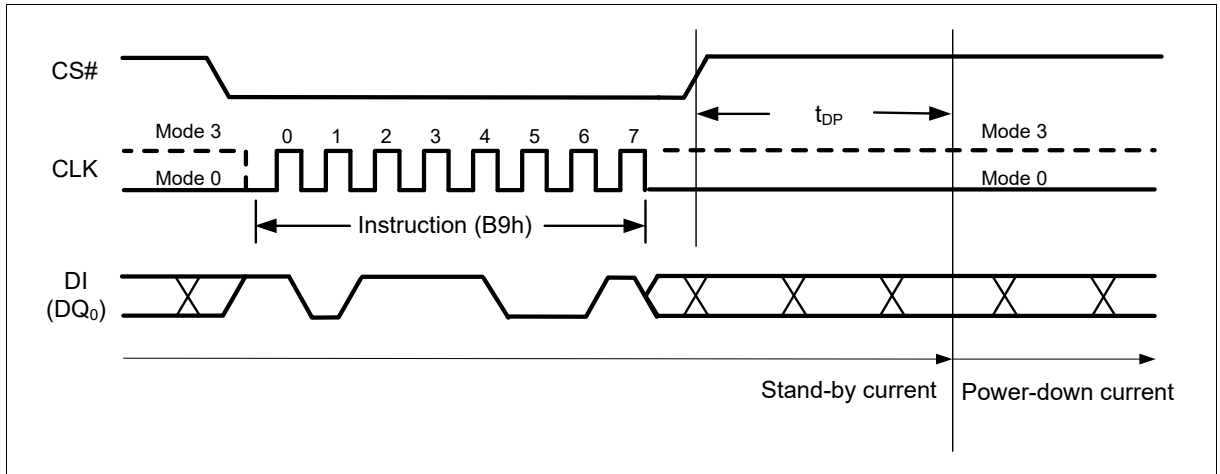


Figure 38 Deep Power-down Instruction (SPI Mode)

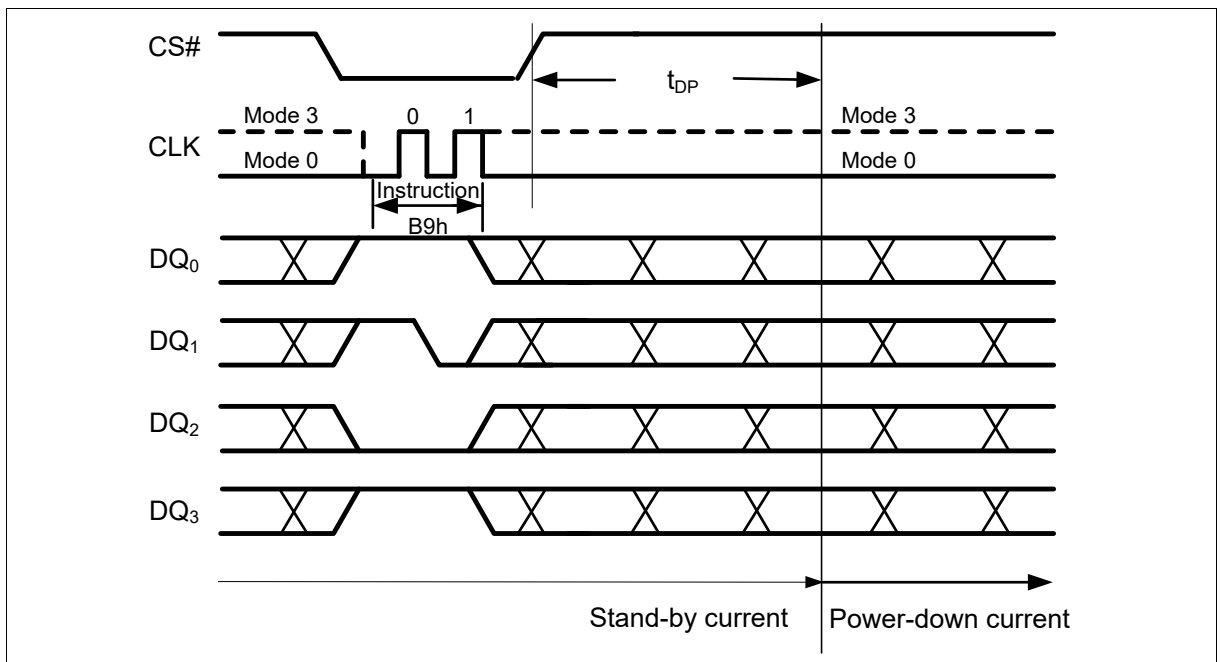


Figure 39 Deep Power-down Instruction (QPI Mode)

11.27. Release Power-down / Device ID (ABh)

The Release from Power-down / Device ID instruction is a multi-purpose instruction. It can be used to release the device from the power-down state, or obtain the device's electronic identification (ID) number.

To release the device from the power-down state, the instruction is issued by driving the CS# pin low, shifting the instruction code "ABh" and driving CS# high as shown in Figure 40 & Figure 41. Release from power-down will take the time duration of t_{RES1} (See "12.6AC Electrical Characteristics") before the device will resume normal operation and other instructions are accepted. The CS# pin must remain high during the t_{RES1} time duration.

When used only to obtain the Device ID while not in the power-down state, the instruction is initiated by driving the CS# pin low and shifting the instruction code "ABh" followed by 3-dummy bytes. The Device ID bits are then shifted out on the falling edge of CLK with most significant bit (MSB) first as shown in Figure 40 & Figure 41. The Device ID value for the FM25W04I3 is listed in

Table 4 Manufacturer and Device Identification table. The Device ID can be read continuously. The instruction is completed by driving CS# high.

When used to release the device from the power-down state and obtain the Device ID, the instruction is the same as previously described, and shown in Figure 42&Figure 43, except that after CS# is driven high it must remain high for a time duration of t_{RES2} (See “12.6AC Electrical Characteristics”). After this time duration the device will resume normal operation and other instructions will be accepted. If the Release from Power-down / Device ID instruction is issued while an Erase, Program or Write cycle is in process (when WIP equals 1) the instruction is ignored and will not have any effect on the current cycle.

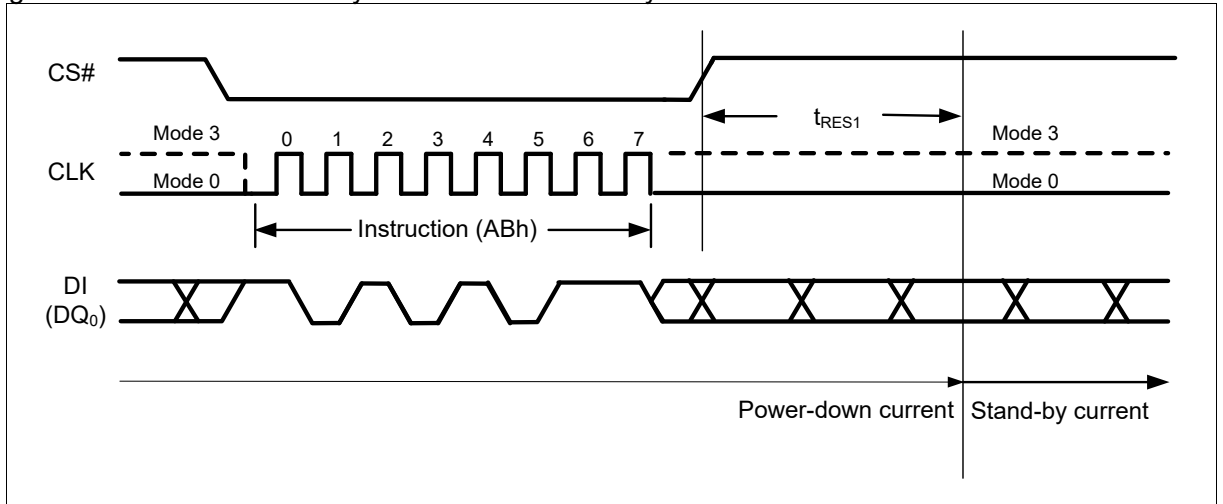


Figure 40 Release Power-down Instruction (SPI Mode)

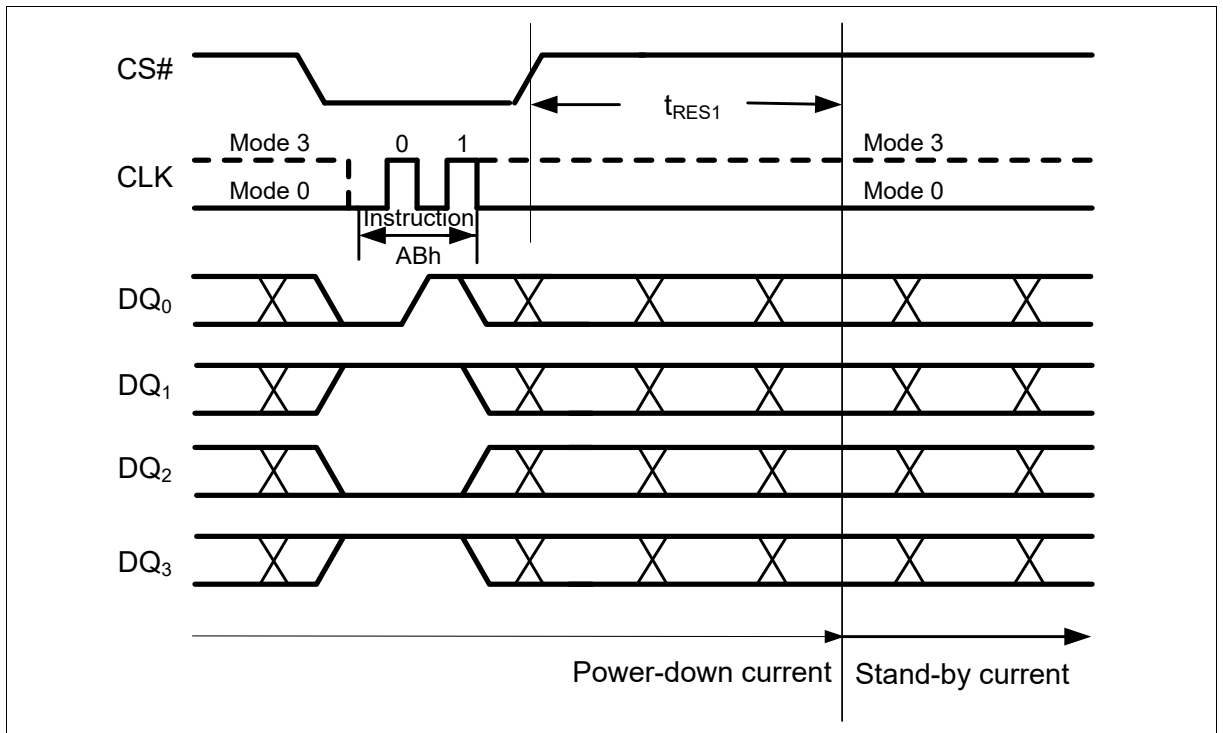


Figure 41 Release Power-down Instruction (QPI Mode)

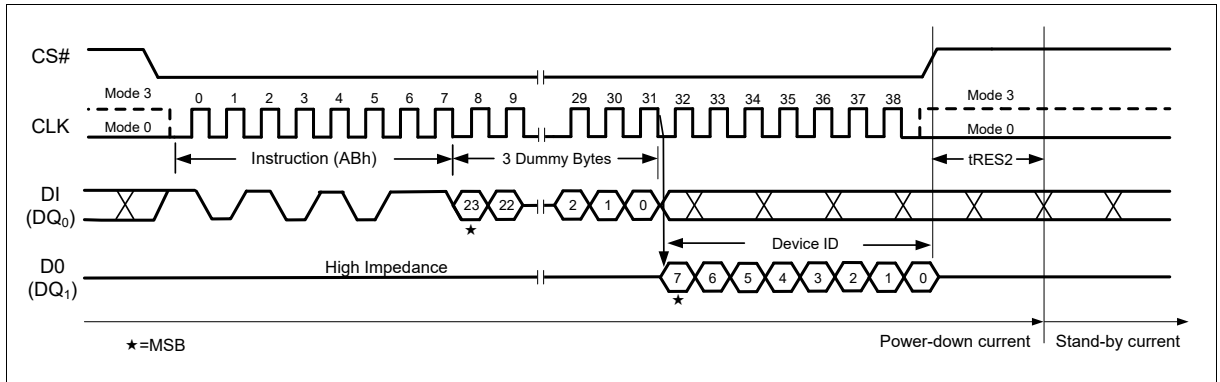


Figure 42 Release Power-down / Device ID Instruction (SPI Mode)

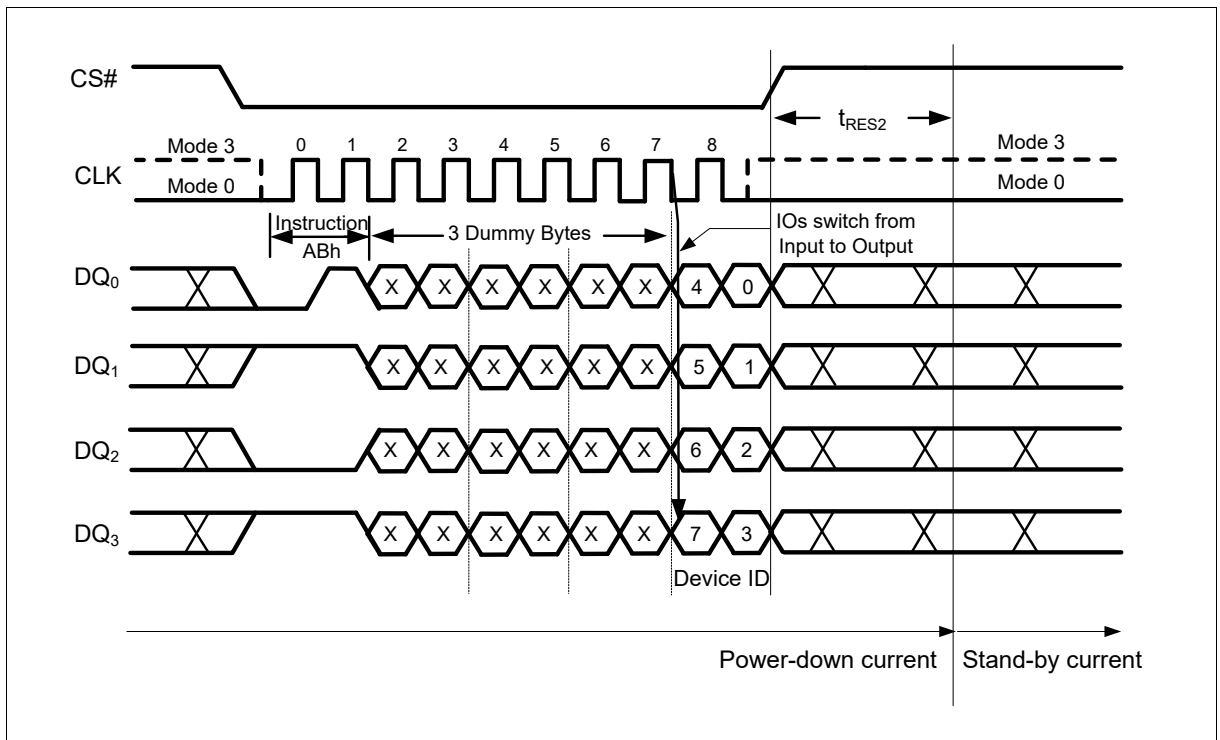


Figure 43 Release Power-down / Device ID Instruction (QPI Mode)

11.28. Read Manufacturer / Device ID (90h)

The Read Manufacturer/Device ID instruction is an alternative to the Release from Power-down / Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID.

The Read Manufacturer/Device ID instruction is very similar to the Release from Power-down / Device ID instruction. The instruction is initiated by driving the CS# pin low and shifting the instruction code "90h" followed by a 24-bit address A23-A0 of 000000h. After which, the Manufacturer ID for Shanghai Fudan Microelectronics Group Co., Ltd (A1h) and the Device ID are shifted out on the falling edge of CLK with most significant bit (MSB) first as shown in Figure 44&Figure 45. The Device ID value for the FM25W0413 is listed in Table 4 Manufacturer and Device Identification table. If the 24-bit address is initially set to 000001h the Device ID will be read first and then followed by the Manufacturer ID. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

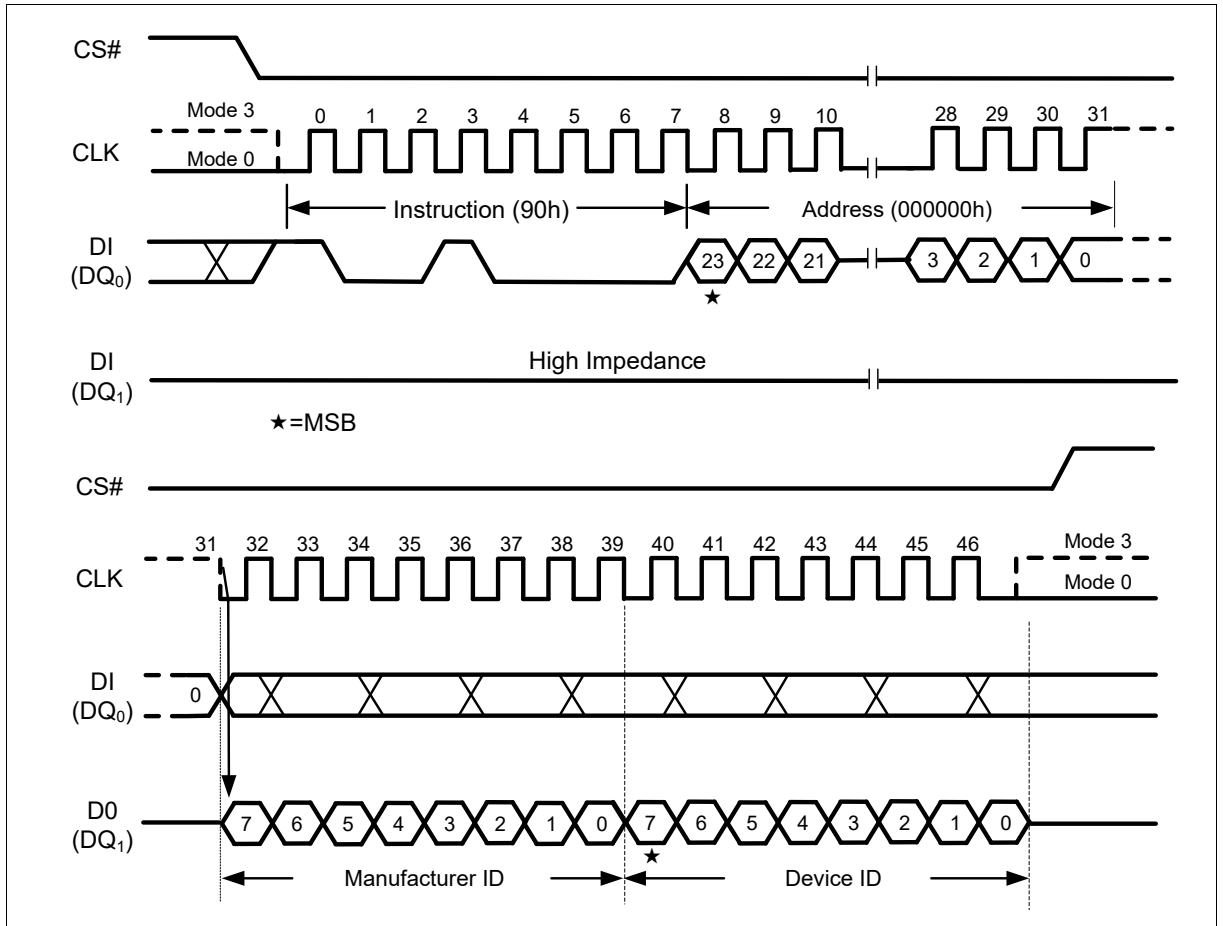


Figure 44 Read Manufacturer / Device ID Instruction (SPI Mode)

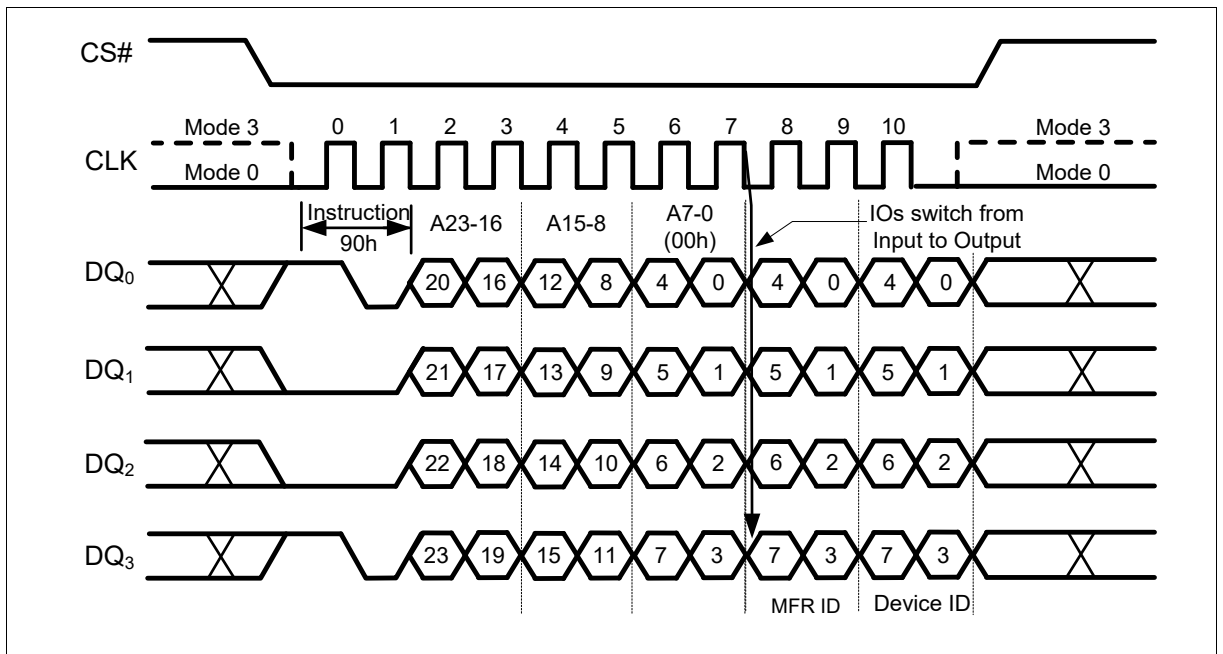


Figure 45 Read Manufacturer / Device ID Instruction (QPI Mode)

11.29. Read Manufacturer / Device ID Dual I/O (92h)

The Read Manufacturer / Device ID Dual I/O instruction is an alternative to the Read Manufacturer / Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID at 2x speed.

The Read Manufacturer / Device ID Dual I/O instruction is similar to the Fast Read Dual I/O instruction. The instruction is initiated by driving the CS# pin low and shifting the instruction code “92h” followed by a 24-bit address A23-A0 of 000000h, 8-bit Continuous Read Mode Bits, with the capability to input the Address bits two bits per clock. After which, the Manufacturer ID for Shanghai Fudan Microelectronics Group Co., Ltd (A1h) and the Device ID are shifted out 2 bits per clock on the falling edge of CLK with most significant bits (MSB) first as shown in Figure 46. The Device ID value for the FM25W04I3 is listed in Table 4 Manufacturer and Device Identification table. If the 24-bit address is initially set to 000001h the Device ID will be read first and then followed by the Manufacturer ID. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

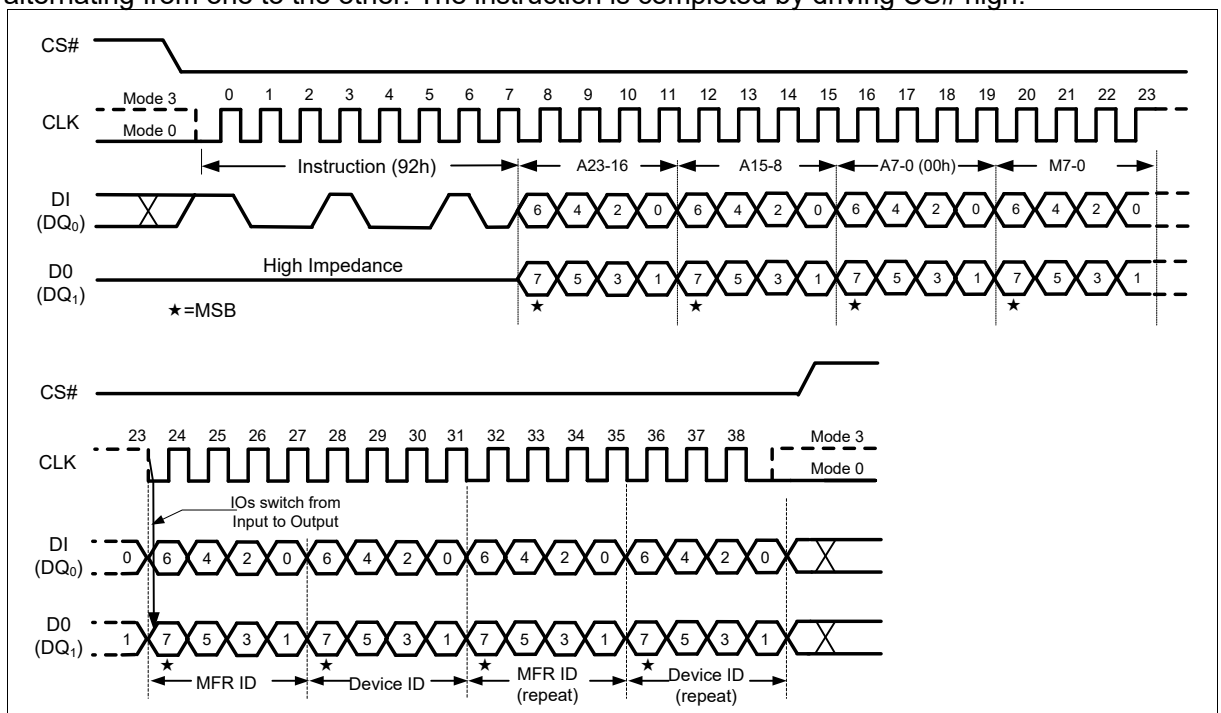


Figure 46 Read Manufacturer / Device ID Dual I/O Instruction (SPI Mode only)

Note:

The “Continuous Read Mode” bits M7-M0 must be set to Fxh to be compatible with Fast Read Dual I/O instruction.

11.30. Read Manufacturer / Device ID Quad I/O (94h)

The Read Manufacturer / Device ID Quad I/O instruction is an alternative to the Read Manufacturer / Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID at 4x speed.

The Read Manufacturer / Device ID Quad I/O instruction is similar to the Fast Read Quad I/O instruction. The instruction is initiated by driving the CS# pin low and shifting the instruction code “94h” followed by a 24-bit address A23-A0 of 000000h, 8-bit Continuous Read Mode Bits and then four clock dummy cycles, with the capability to input the Address bits four bits per clock. After which, the Manufacturer ID for Shanghai Fudan Microelectronics Group Co., Ltd (A1h) and the Device ID are shifted out four bits per clock on the falling edge of CLK with most significant bit

(MSB) first as shown in Figure 47. The Device ID value for the FM25W04I3 is listed in Manufacturer and Device Identification table. If the 24-bit address is initially set to 000001h the Device ID will be read first and then followed by the Manufacturer ID. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

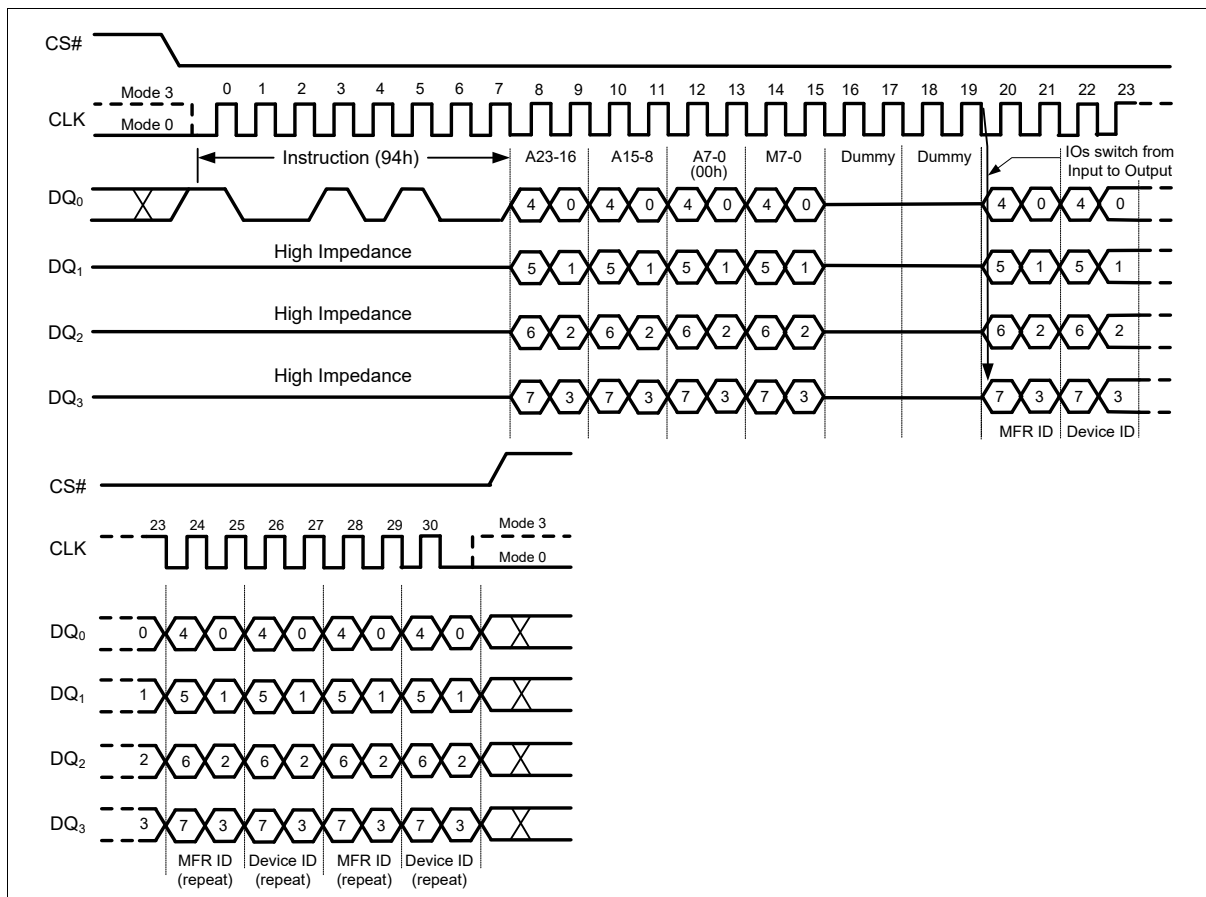


Figure 47 Read Manufacturer / Device ID Quad I/O Instruction (SPI Mode only)

Note:

The “Continuous Read Mode” bits M7-M0 must be set to Fxh to be compatible with Fast Read Quad I/O instruction.

11.31. Read Unique ID Number (4Bh)

The Read Unique ID Number instruction accesses a factory-set read-only 64-bit number that is unique to each FM25W04I3 device. The ID number can be used in conjunction with user software methods to help prevent copying or cloning of a system. The Read Unique ID instruction is initiated by driving the CS# pin low and shifting the instruction code “4Bh” followed by a four bytes of dummy clocks. After which, the 64-bit ID is shifted out on the falling edge of CLK as shown in Figure 48.

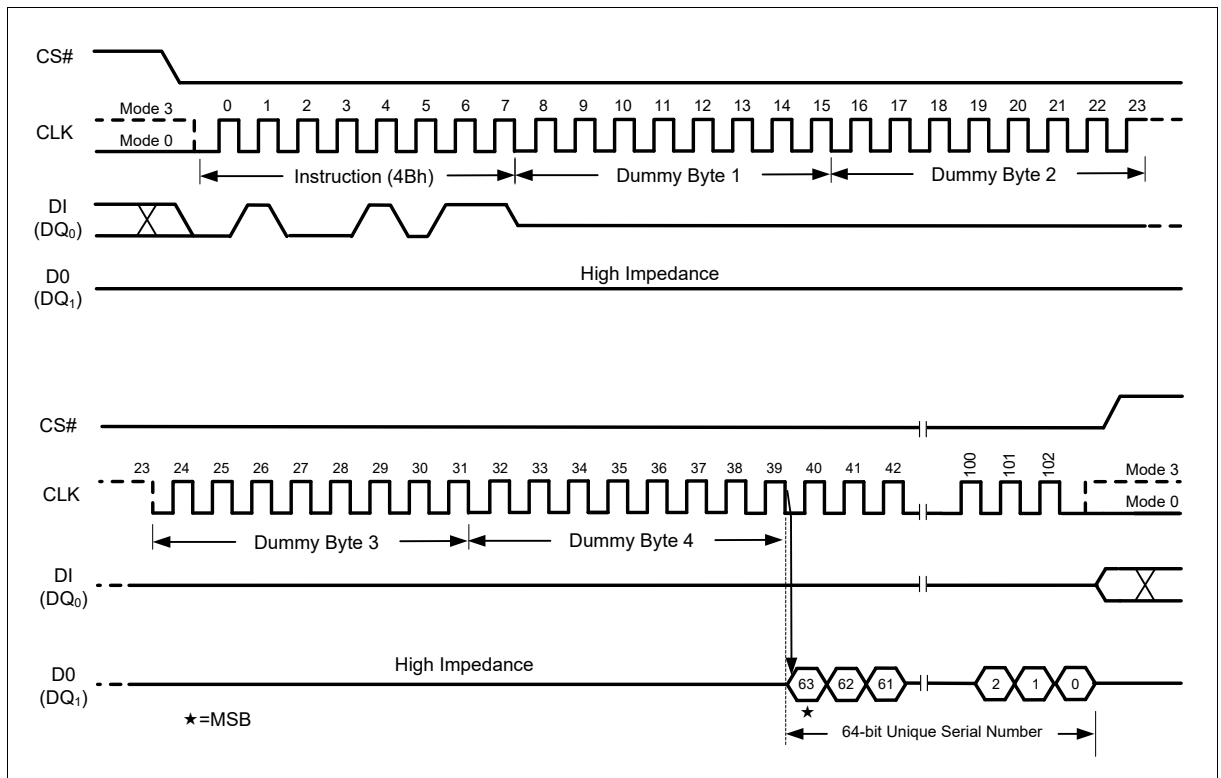


Figure 48 Read Unique ID Number Instruction (SPI Mode only)

11.32. Read JEDEC ID (9Fh)

For compatibility reasons, the FM25W04I3 provides several instructions to electronically determine the identity of the device. The Read JEDEC ID instruction is compatible with the JEDEC standard for SPI compatible serial memories. The instruction is initiated by driving the CS# pin low and shifting the instruction code “9Fh”. The JEDEC assigned Manufacturer ID byte for Shanghai Fudan Microelectronics Group Co., Ltd (A1h) and two Device ID bytes, Memory Type (ID15-ID8) and Capacity ID7-ID0 are then shifted out on the falling edge of CLK with most significant bit (MSB) first as shown in Figure 49&Figure 50. For memory type and capacity values refer to Table 4 Manufacturer and Device Identification table.

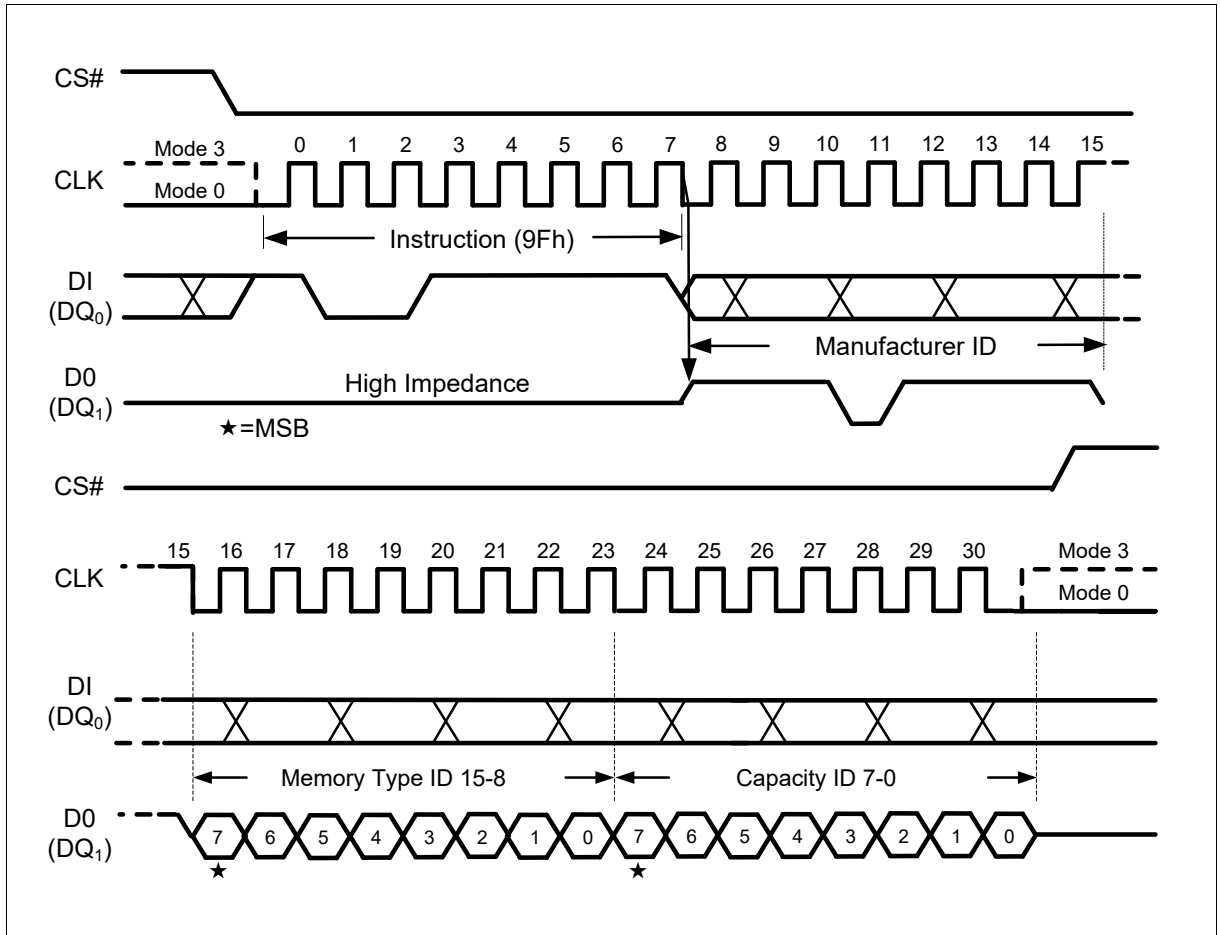


Figure 49 Read JEDEC ID Instruction (SPI Mode)

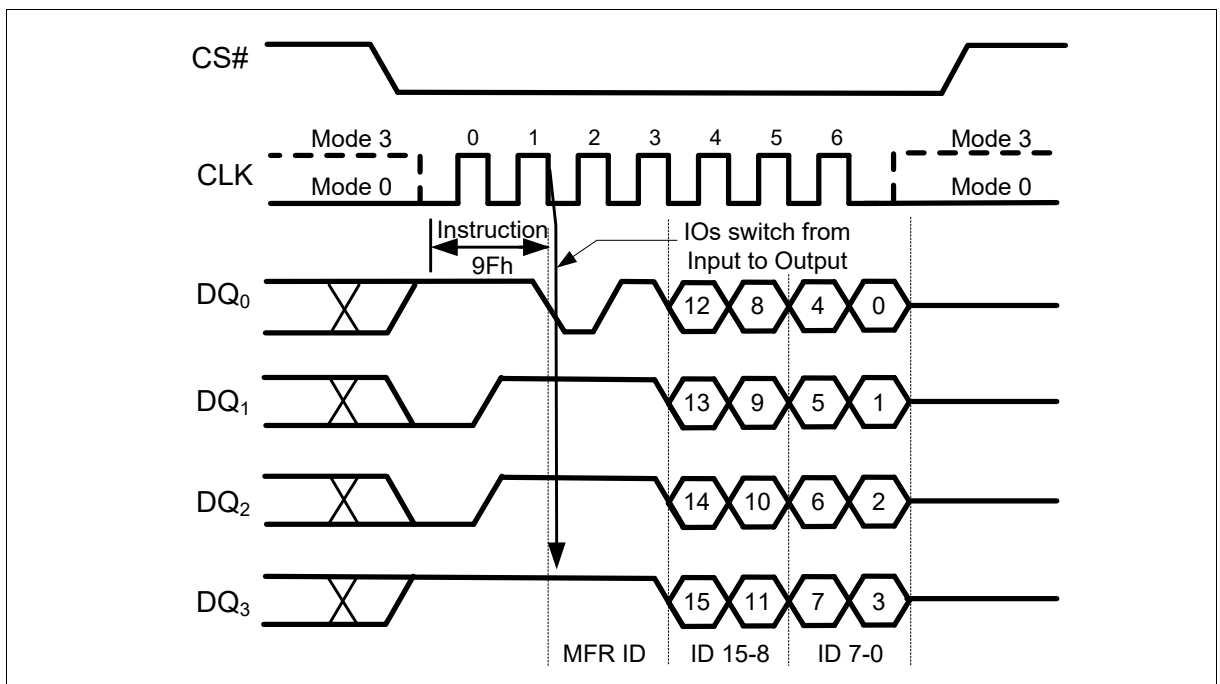


Figure 50 Read JEDEC ID Instruction (QPI Mode)

11.33. Read SFDP Register(5Ah)

The FM25W0413 features a 256-Byte Serial Flash Discoverable Parameter (SFDP) register that contains information about device configurations, available instructions and other features. The SFDP parameters are stored in one or more Parameter Identification (PID) tables. Currently only one PID table is specified. The Read SFDP Register instruction is compatible with the SFDP standard initially established in 2010 for PC and other applications, as well as the JEDEC standard 1.0 that is published in 2011.

The Read SFDP instruction is initiated by driving the /CS pin low and shifting the instruction code “5Ah” followed by a 24-bit address (A23-A0)⁽¹⁾ into the DI pin. Eight “dummy” clocks are also required before the SFDP register contents are shifted out on the falling edge of the 40th CLK with most significant bit (MSB) first as shown in Figure 51. For SFDP register values and descriptions, refer to the following SFDP Definition table.

Note: 1. A23-A8 = 0; A7-A0 are used to define the starting byte address for the 256-Byte SFDP Register.

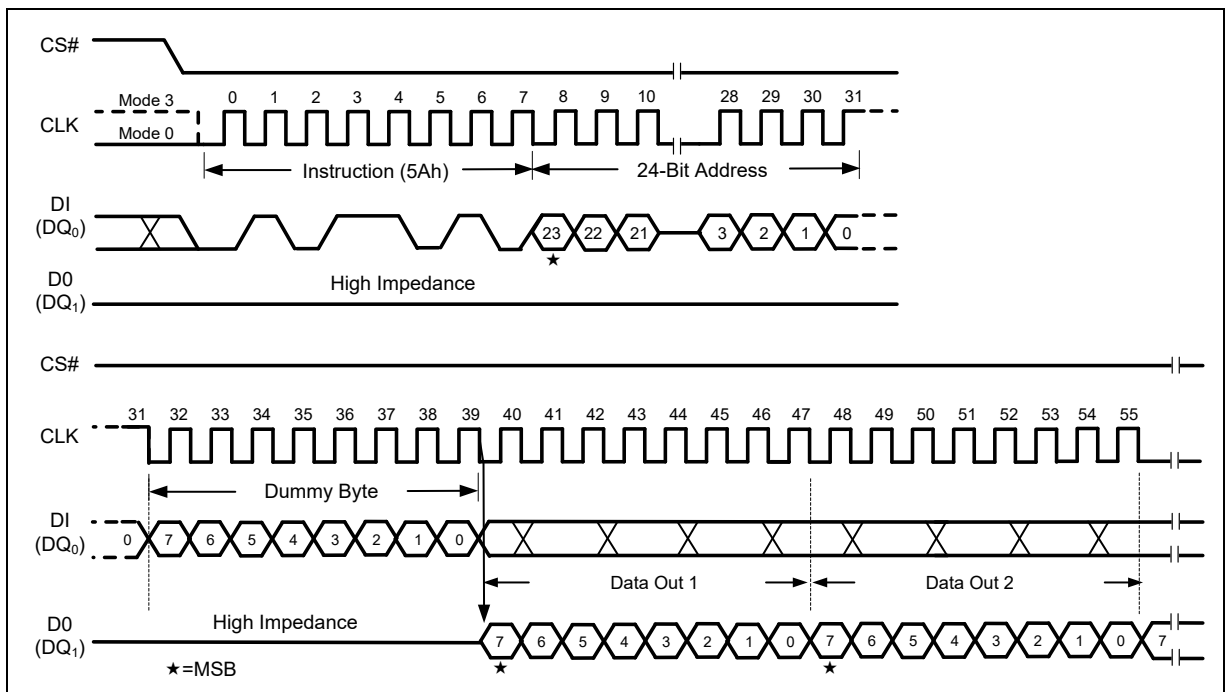


Figure 51 Read SFDP Register Instruction

Serial Flash Discoverable Parameter (JEDEC Revision 1.0) Definition Table

BYTE ADDRESS	DATA	DESCRIPTION	COMMENT
00h	53h	SFDP Signature	SFDP Signature = 50444653h
01h	46h	SFDP Signature	
02h	44h	SFDP Signature	
03h	50h	SFDP Signature	
04h	00h	SFDP Minor Revision Number	JEDEC Revision 1.0
05h	01h	SFDP Major Revision Number	
06h	00h	Number of Parameter Headers (NPH)	1 Parameter Header
07h	FFh	Reserved	
08h	00h	PID ⁽³⁾ (0): ID Number	00h = JEDEC specified
09h	00h	PID(0): Parameter Table Minor Revision Number	JEDEC Revision 1.0

BYTE ADDRESS	DATA	DESCRIPTION	COMMENT
0Ah	01h	PID(0): Parameter Table Major Revision Number	
0Bh	09h	PID(0): Parameter Table Length	9 Dwords ⁽²⁾
0Ch	80h	PID(0): Parameter Table Pointer (PTP) (A7-A0)	PID(0) Pointer = 000080h
0Dh	00h	PID(0): Parameter Table Pointer (PTP) (A15-A8)	
0Eh	00h	PID(0): Parameter Table Pointer (PTP) (A23-A16)	
0Fh	FFh	Reserved	
10h	FFh	Reserved	
... ⁽¹⁾	FFh	Reserved	
7Fh	FFh	Reserved	
80h	E5h	Bit[7:5]=111 Reserved Bit[4:3]=00 Non-volatile Status Register Bit[2]=1 Page Programmable Bit[1:0]=01 Supports 4KB Erase	
81h	20h	4K-Byte Erase Op code	
82h	F1h	Bit[7] =1 Reserved Bit[6] =1 Supports (1-1-4) Fast Read Bit[5] =1 Supports (1-4-4) Fast Read Bit[4] =1 Supports (1-2-2) Fast Read Bit[3] =0 Not support Dual Transfer Rate Bit[2:1]=00 3-Byte/24-Bit Only Addressing Bit[0] =1 Supports (1-1-2) Fast Read	
83h	FFh	Reserved	
84h	FFh	Flash Size in Bits	4 Mega Bits = 003FFFFFFh
85h	FFh	Flash Size in Bits	
86h	3Fh	Flash Size in Bits	
87h	00h	Flash Size in Bits	
88h	44h	Bit[7:5]=010 8 Mode Bits are needed Bit[4:0]=00100 16 Dummy Bits are needed	Fast Read Quad I/O Setting
89h	EBh	Quad Input Quad Output Fast Read Op code	Fast Read Quad Output Setting
8Ah	08h	Bit[7:5]=000 No Mode Bits are needed Bit[4:0]=01000 8 Dummy Bits are needed	
8Bh	6Bh	Single Input Quad Output Fast Read Op code	
8Ch	08h	Bit[7:5]=000 No Mode Bits are needed Bit[4:0]=01000 8 Dummy Bits are needed	Fast Read Dual Output Setting
8Dh	3Bh	Single Input Dual Output Fast Read Op code	Fast Read Dual I/O Setting
8Eh	80h	Bit[7:5]=100 8 Mode bits are needed Bit[4:0]=00000 No Dummy bits are needed	
8Fh	BBh	Dual Input Dual Output Fast Read Op code	
90h	FEh	Bit[7:5]=111 Reserved Bit[4]=1 support (4-4-4) Fast Read Bit[3:1]=111 Reserved Bit[0]=0 Not support (2-2-2) Fast Read	
91h	FFh	Reserved	
92h	FFh	Reserved	
93h	FFh	Reserved	
94h	FFh	Reserved	
95h	FFh	Reserved	
96h	00h	No Mode Bits or Dummy Bits for (2-2-2) Fast Read	

BYTE ADDRESS	DATA	DESCRIPTION	COMMENT
97h	00h	Not support (2-2-2) Fast Read	
98h	FFh	Reserved	
99h	FFh	Reserved	
9Ah	08h	Bit[7:5]=000 No Mode bits are needed Bit[4:0]=01000 8 Dummy bits are needed	
9Bh	EBh	QPI Fast Read Op code	
9Ch	0Ch	Sector Type 1 Size (4KB)	Sector Erase Type & Op code
9Dh	20h	Sector Type 1 Op code	
9Eh	0Fh	Sector Type 2 Size (32KB)	
9Fh	52h	Sector Type 2 Op code	
A0h	10h	Sector Type 3 Size (64KB)	Sector Erase Type & Op code
A1h	D8h	Sector Type 3 Op code	
A2h	00h	Sector Type 4 Size (256KB) – Not supported	
A3h	00h	Sector Type 4 Op code – Not supported	
... ⁽¹⁾	FFh	Reserved	
FFh	FFh	Reserved	

Notes:

1. Data stored in Byte Address 10h to 7Fh& A4h to FFh are reserved, the value is FFh.
2. 1Dword=4 Bytes
3. PID(x)= Parameter Identification Table (x)

11.34. Erase Security Sector (44h)

The FM25W04I3 offers one 1024-byte Security Sector. The Security Sector may be used by the system manufacturers to store security and other important information separately from the main memory array.

The Erase Security Sector instruction is similar to the Sector Erase instruction. A Write Enable instruction must be executed before the device will accept the Erase Security Sector Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the CS# pin low and shifting the instruction code “44h” followed by a 24-bit address A23-A0 to erase Security Sectors.

A23-16	A15-10	A9-0
00h	000000	Don't Care

The Erase Security Sector instruction sequence is shown in Figure 52. The CS# pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the instruction will not be executed. After CS# is driven high, the self-timed Erase Security Sector operation will commence for a time duration of t_{SE} (See “12.6AC Electrical Characteristics”). While the Erase Security Sector cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the WIP bit. The WIP bit is a 1 during the erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Erase Security Sector cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Security Sector Lock Bit (LB) in the Status Register-2 can be used to OTP protect the Security Sectors. Once the LB bit is set to 1, the Security Sector will be permanently locked, Erase Security Sector instruction will be ignored.

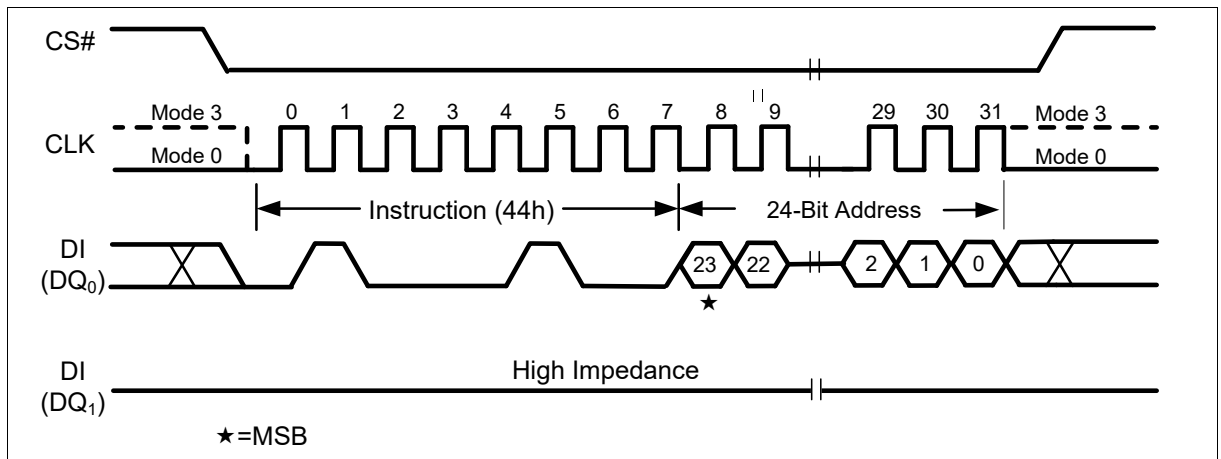


Figure 52 Erase Security Sector Instruction (SPI Mode only)

11.35. Program Security Sector (42h)

The Program Security Sector instruction is similar to the Page Program instruction. It allows from one byte to 256 bytes of Security Sector data to be programmed at previously erased (FFh) memory locations. A Write Enable instruction must be executed before the device will accept the Program Security Sector Instruction (Status Register bit WEL= 1). The instruction is initiated by driving the CS# pin low then shifting the instruction code “42h” followed by a 24-bit address A23-A0 and at least one data byte, into the DI pin. The CS# pin must be held low for the entire length of the instruction while data is being sent to the device.

A23-16	A15-10	A9-8	A7-0
00h	0 0 0 0	0 0 0 1 1 0 1 1	Byte Address

The Program Security Sector instruction sequence is shown in Figure 53. The Security Sector Lock Bit (LB) in the Status Register-2 can be used to OTP protect the Security Sectors. Once a lock bit is set to 1, the Security Sector will be permanently locked and Program Security Sector instruction will be ignored.

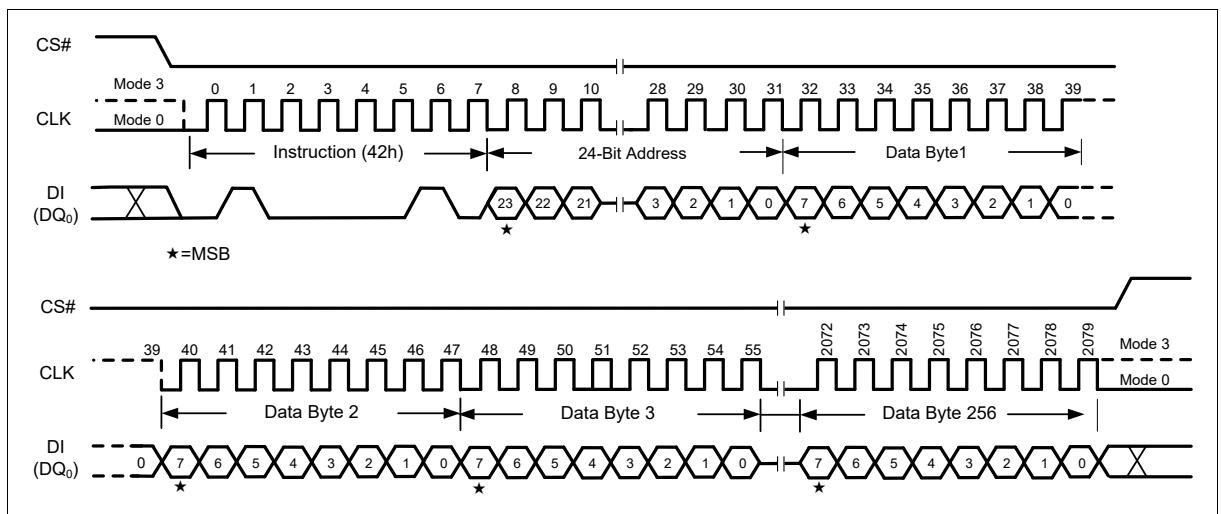


Figure 53 Program Security Sectors Instruction (SPI Mode only)

11.36. Read Security Sector (48h)

The Read Security Sector instruction is similar to the Fast Read instruction and allows one or more data bytes to be sequentially read from the Security Sector. The instruction is initiated by driving the CS# pin low and then shifting the instruction code “48h” followed by a 24-bit address A23-A0 and eight “dummy” clocks into the DI pin. The code and address bits are latched on the rising edge of the CLK pin. After the address is received, the data byte of the addressed memory location will be shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) first. The byte address is automatically incremented to the next byte address after each byte of data is shifted out. Once the byte address reaches 3FFh (the last byte of the register), it will be reset to 00h(the first byte of the register) and continue to increment. The instruction is completed by driving CS# high. The Read Security Sector instruction sequence is shown in Figure 54. If a Read Security Sector instruction is issued while an Erase, Program or Write cycle is in process (WIP =1) the instruction is ignored and will not have any effect on the current cycle. The Read Security Sector instruction allows clock rates from D.C. to a maximum of FR (see “12.6AC Electrical Characteristics”).

A23-16	A15-10	A9-8	A7-0
00h	0 0 0 0	0 0 0 1 1 0 1 1	Byte Address

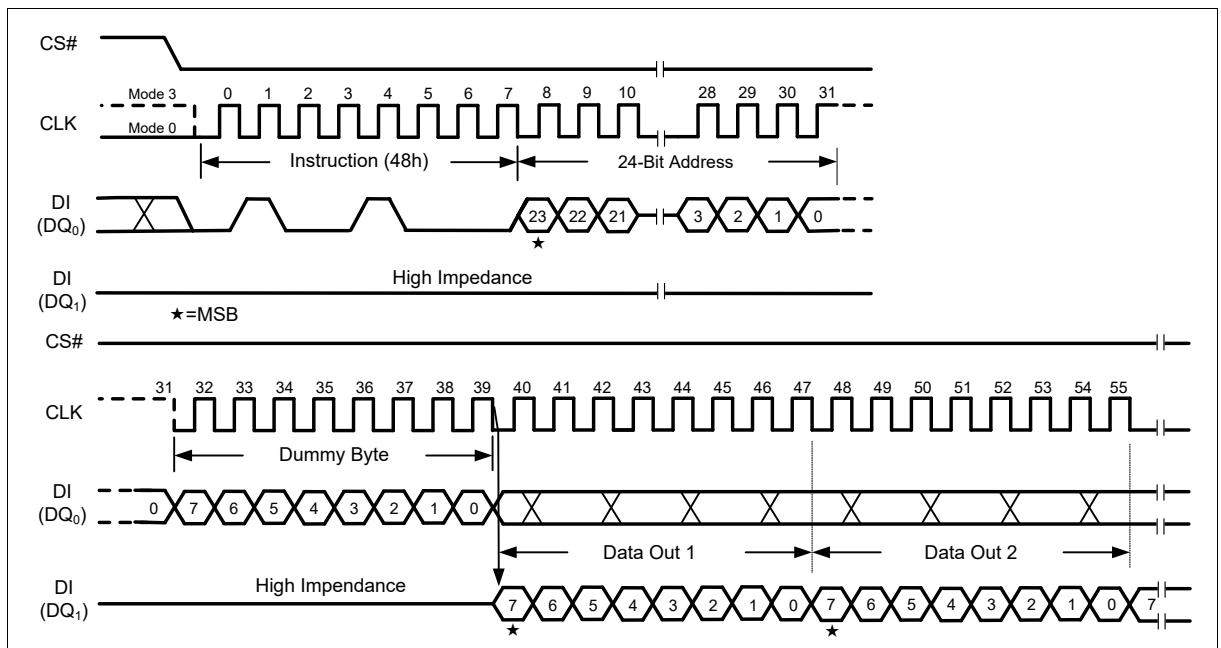


Figure 54 Read Security Sectors Instruction (SPI Mode only)

11.37. Set Read Parameters (C0h)

In QPI mode, to accommodate a wide range of applications with different needs for either maximum read frequency or minimum data access latency, “Set Read Parameters (C0h)” instruction can be used to configure the number of dummy clocks for “Fast Read (0Bh)”, “Fast Read Quad I/O (EBh)” & “Burst Read with Wrap (0Ch)” instructions, and to configure the number of bytes of “Wrap Length” for the “Burst Read with Wrap (0Ch)” instruction.

In Standard SPI mode, the “Set Read Parameters (C0h)” instruction is not accepted. The dummy clocks for various Fast Read instructions in Standard/Dual/Quad SPI mode are fixed, please refer to Table 8 QPI Instructions Set the Instruction set for details. The “Wrap Length” is set by W5-4 bit in the “Set Burst with Wrap (77h)” instruction. This setting will remain unchanged when the device is switched from Standard SPI mode to QPI mode.

The default “Wrap Length” after a power up or a Reset instruction is 8 bytes, the default number of dummy clocks is 2.

P5 – P4	DUMMY CLOCKS	MAXIMUM READ FREQ.
00	2	50MHz
01	4	80MHz
10	6	100MHz
11	8	100MHz

P1 – P0	WRAP LENGTH
00	8-byte
01	16-byte
10	32-byte
11	64-byte

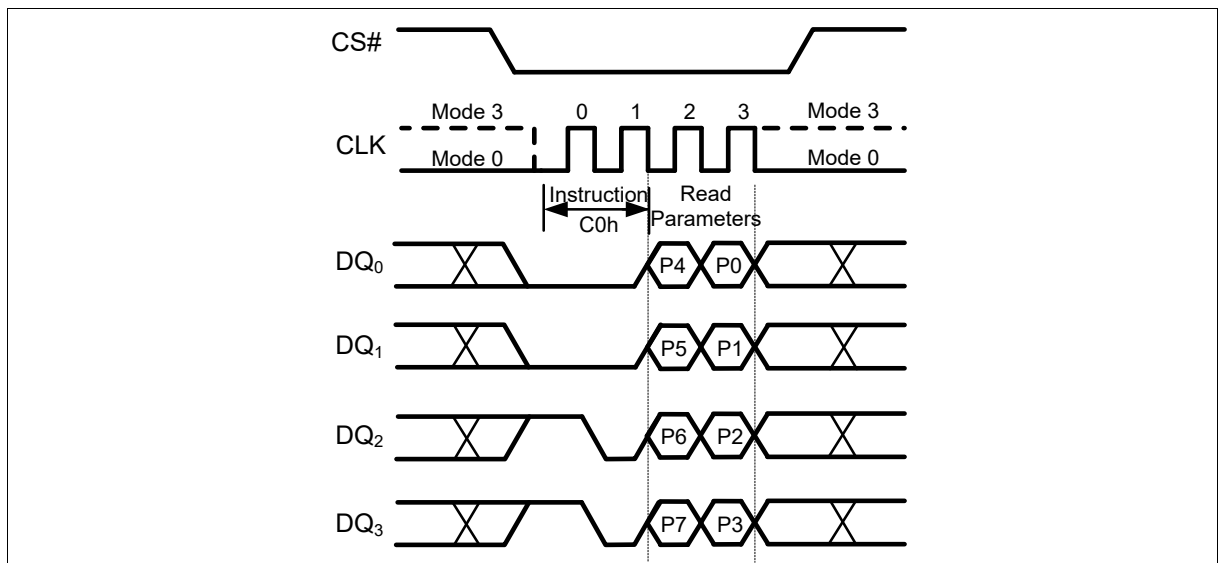


Figure 55 Set Read Parameters Instruction (QPI Mode only)

11.38. Burst Read with Wrap (0Ch)

The “Burst Read with Wrap (0Ch)” instruction provides an alternative way to perform the read operation with “Wrap Around” in QPI mode. The instruction is similar to the “Fast Read (0Bh)” instruction in QPI mode, except the addressing of the read operation will “Wrap Around” to the beginning boundary of the “Wrap Length” once the ending boundary is reached.

The “Wrap Length” and the number of dummy clocks can be configured by the “Set Read ParametersC0h)” instruction.

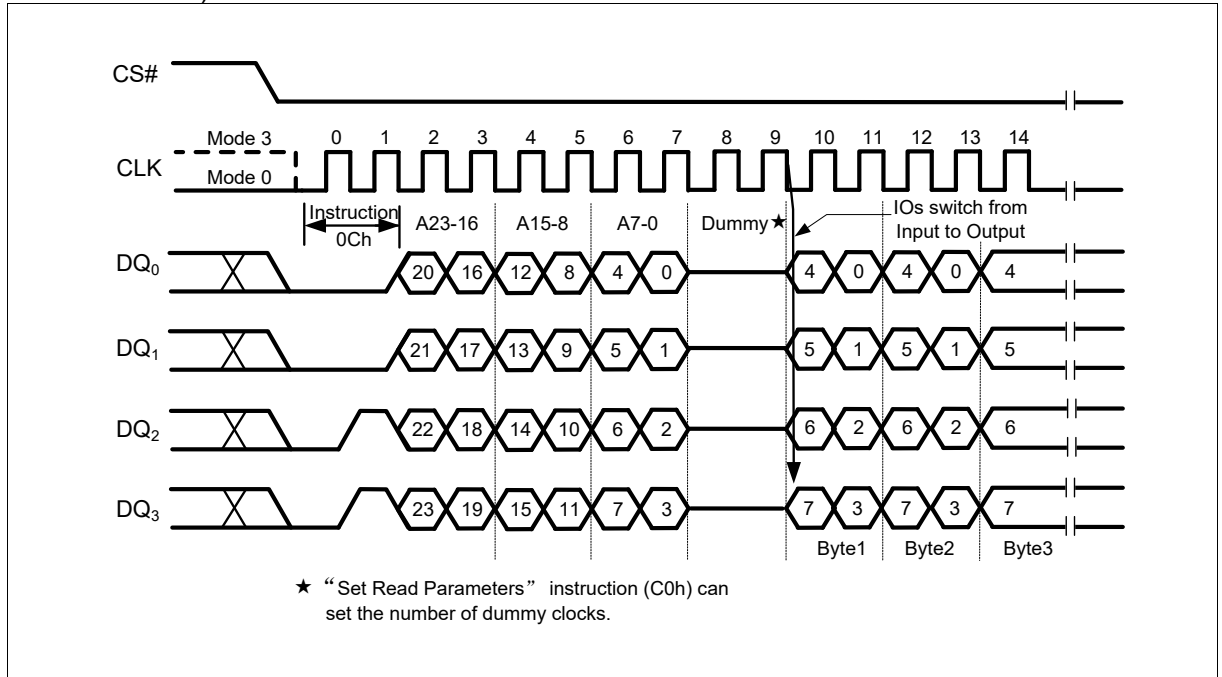


Figure 56 Burst Read with Wrap Instruction (QPI Mode only)

11.39. Enable QPI (38h)

The FM25W0413 support both Standard/Dual/Quad Serial Peripheral Interface (SPI) and Quad Peripheral Interface (QPI). However, SPI mode and QPI mode can not be used at the same time. “Enable QPI (38h)” instruction is the only way to switch the device from SPI mode to QPI mode.

Upon power-up, the default state of the device upon is Standard/Dual/Quad SPI mode. See Table 8 QPI Instructions ^{Set (15)} for all supported SPI commands. In order to switch the device to QPI mode, an “Enable QPI (38h)” instruction must be issued.

See Table 8 QPI Instructions Set Instruction Set for all the commands supported in QPI mode.

When the device is switched from SPI mode to QPI mode, the existing Write Enable and the Wrap Length setting will remain unchanged.

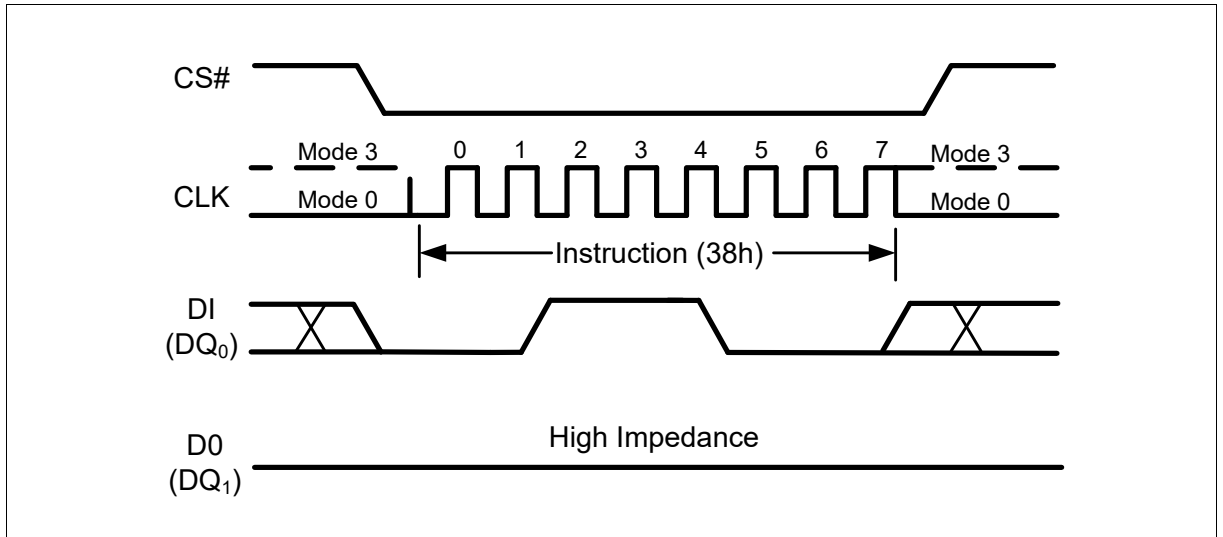


Figure 57 Enable QPI Instruction (SPI Mode only)

11.40. Disable QPI (FFh)

In order to exit the QPI mode and return to the Standard/Dual/Quad SPI mode, a “Disable QPI (FFh)” instruction must be issued.

When the device is switched from QPI mode to SPI mode, the existing Write Enable Latch (WEL) and the Wrap Length setting will remain unchanged.

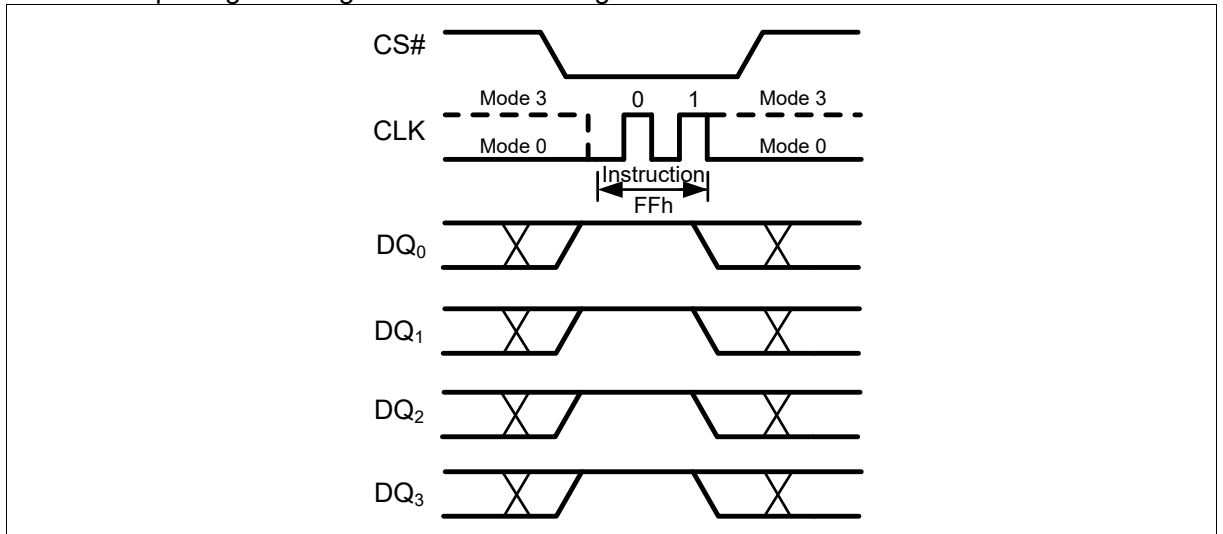


Figure 58 Disable QPI Instruction (QPI Mode only)

11.41. Enable Reset (66h) and Reset (99h)

Because of the small package and the limitation on the number of pins, the FM25W0413 provide a software Reset instruction instead of a dedicated RESET pin. Once the Reset instruction is accepted, any on-going internal operations will be terminated and the device will return to its default power-on state and lose all the current volatile settings, such as Volatile Status Register bits, Write Enable Latch (WEL) status, Read parameter setting P7-P0, Continuous Read Mode bit setting M7-M0 and Wrap Bit setting W6-W4.

“Enable Reset (66h)” and “Reset (99h)” instructions can be issued in either SPI mode or QPI mode. To avoid accidental reset, both instructions must be issued in sequence. Any other commands other than “Reset (99h)” after the “Enable Reset (66h)” command will disable the “Reset Enable” state. A new sequence of “Enable Reset (66h)” and “Reset (99h)” is needed to reset the device. Once the Reset command is accepted by the device, the device will take approximately $t_{RST}=30\mu s$ to reset. During this period, no command will be accepted.

Data corruption may happen if there is an on-going internal Erase or Program operation when Reset command sequence is accepted by the device. It is recommended to check the WIP bit in Status Register before issuing the Reset command sequence.

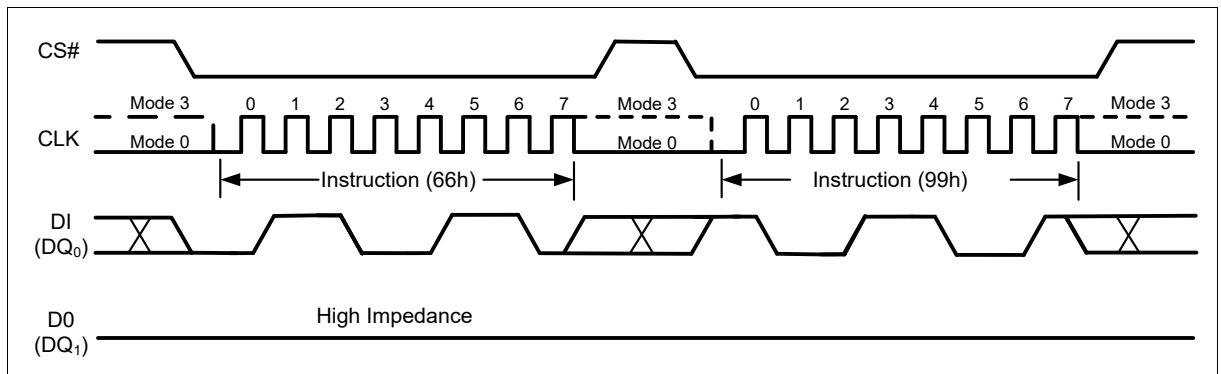


Figure 59 Enable Reset and Reset Instruction Sequence (SPI Mode)

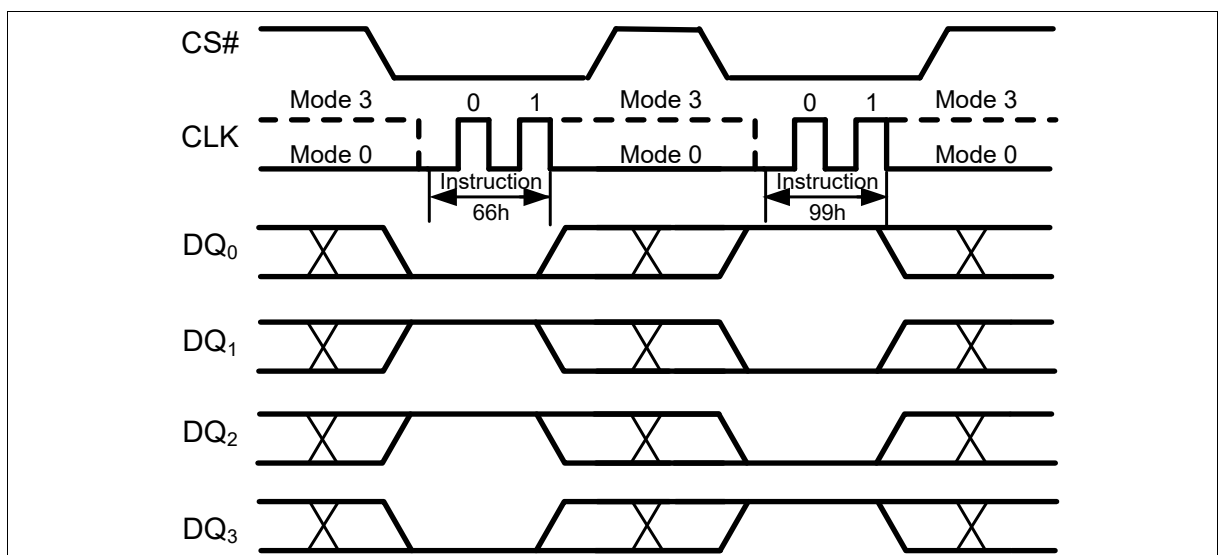


Figure 60 Enable Reset and Reset Instruction Sequence (QPI Mode)

12. Electrical Characteristics

12.1. Absolute Maximum Ratings

Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C
Voltage on I/O Pin with Respect to Ground	-0.5V to $V_{CC}+0.4V$
V_{CC}	-0.5V to 4.0V

*NOTICE: Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

12.2. Pin Capacitance

PARAMETER	SYMBOL	CONDITIONS	Max	Units
Input Capacitance	$C_{IN}^{(1)}$	$V_{IN} = 0V, f = 5 \text{ MHz}$	6	pF
Output Capacitance	$C_{OUT}^{(1)}$	$V_{OUT} = 0V, f = 5 \text{ MHz}$	8	pF

Note: 1. this parameter is characterized and not 100% tested.

12.3. Power-up Timing

Applicable over recommended operating range from: $T_A = -40^\circ\text{C}$ to 85°C , $V_{CC} = 1.65V$ to $3.6V$, (unless otherwise noted).

SYMBOL	PARAMETER	SPEC		UNIT
		MIN	MAX	
t_{VSL}	VCC (min) to CS# Low	10		μs
t_{PUW}	Time Delay Before Write Instruction	1	10	ms
V_{WI}	Write Inhibit Threshold Voltage	1	1.4	V

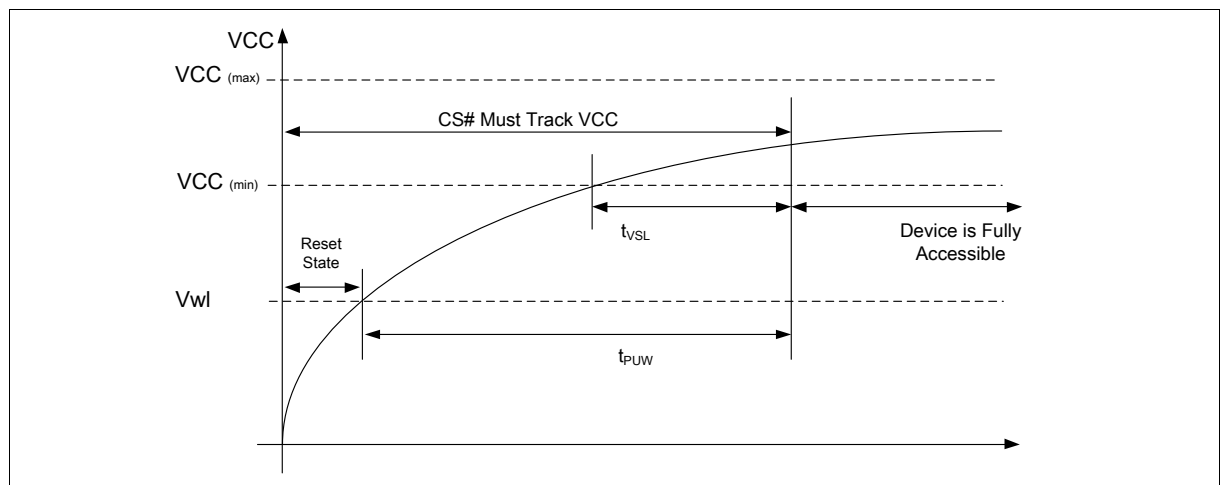


Figure 61 Power-up Timing & Power Up/Down and Voltage Drop

12.4. DC Electrical Characteristics

Table 9 DC Characteristics

Applicable over recommended operating range from: $T_A = -40^{\circ}\text{C}$ to 85°C , $V_{CC} = 1.65\text{V}$ to 3.6V , (unless otherwise noted).

SYMBOL	PARAMETER	CONDITIONS	SPEC			UNIT
			MIN	TYP	MAX	
V_{CC}	Supply Voltage		1.65		3.6	V
I_{LI}	Input Leakage Current				± 2	μA
I_{LO}	Output Leakage Current				± 2	μA
I_{CC1}	Standby Current	$CS\# = V_{CC}$, $V_{IN} = V_{SS}$ or V_{CC}		3	10	μA
I_{CC2}	Deep Power-down Current	$CS\# = V_{CC}$, $V_{IN} = V_{SS}$ or V_{CC}		1	5	μA
$I_{CC3}^{(1)}$	Read Current	$CLK = 0.1V_{CC}/0.9V_{CC}$ at 33MHz, DQ open			15	mA
		$CLK = 0.1V_{CC}/0.9V_{CC}$, at 100MHz, DQ open			25	mA
I_{CC4}	Operating Current (WRSR)	$CS\# = V_{CC}$		10	20	mA
I_{CC5}	Operating Current (PP)	$CS\# = V_{CC}$		10	20	mA
I_{CC6}	Operating Current (SE)	$CS\# = V_{CC}$		10	20	mA
I_{CC7}	Operating Current (BE)	$CS\# = V_{CC}$		10	20	mA
V_{IL}	Input Low Voltage		-0.5		$0.2V_{CC}$	V
V_{IH}	Input High Voltage		$0.8V_{CC}$		$V_{CC} + 0.4$	V
V_{OL}	Output Low Voltage	$I_{OL} = 100\ \mu\text{A}$			0.4	V
V_{OH}	Output High Voltage	$I_{OH} = -100\ \mu\text{A}$	$V_{CC} - 0.2$			V

Notes:

1. Checker Board Pattern.

12.5. AC Measurement Conditions

Table 10 AC Measurement Conditions

SYMBOL	PARAMETER	SPEC		UNIT
		MIN	MAX	
CL	Load capacitance(including jig capacitance)		20	pF
TR, TF	Input Rise and Fall Times		5	ns
V_{IN}	Input Pulse Voltages	$0.2V_{CC}$ to $0.8V_{CC}$		V
IN	Input Timing Reference Voltages	$0.3V_{CC}$ to $0.7V_{CC}$		V
OUT	Output Timing Reference Voltages	$0.5V_{CC}$		V

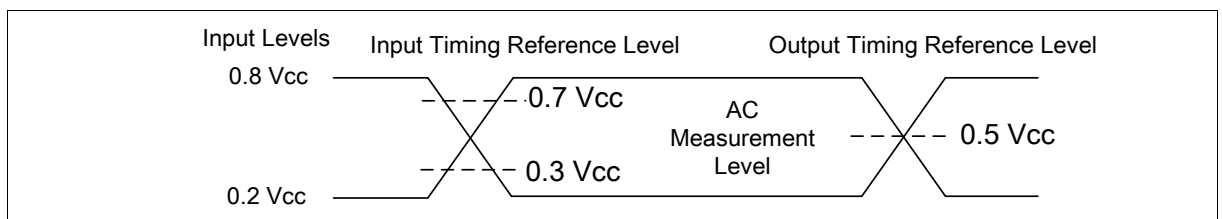


Figure 62 AC Measurement I/O Waveform

12.6. AC Electrical Characteristics

Table 11 AC Characteristics

Applicable over recommended operating range from: $T_A = -40^{\circ}\text{C}$ to 85°C , $V_{CC} = 1.65\text{V}$ to 3.6V , (unless otherwise noted).

SYMBOL	PARAMETER	SPEC			UNIT
		MIN	TYP	MAX	
F_R	Serial Clock Frequency for: FAST_READ, PP, SE, BE, DP, RES, WREN, WRDI, WRSR(1.65~2.7V/2.7~3.6V)			75/100	MHz
f_R	Serial Clock Frequency for READ, RDSR, RDID (1.65~2.7V/2.7~3.6V)			33/50	MHz
$t_{CH1}^{(1)}$	Serial Clock High Time	4.5			ns
$t_{CL1}^{(1)}$	Serial Clock Low Time	4.5			ns
$t_{CLCH}^{(2)}$	Serial Clock Rise Time (Slew Rate)	0.1			V/ns
$t_{CHCL}^{(2)}$	Serial Clock Fall Time (Slew Rate)	0.1			V/ns
$t_{SLCH}^{(2)}$	CS# Active Setup Time	5			ns
$t_{CHSH}^{(2)}$	CS# Active Hold Time	5			ns
$t_{SHCH}^{(2)}$	CS# Not Active Setup Time	5			ns
$t_{CHSL}^{(2)}$	CS# Not Active Hold Time	5			ns
$t_{SHSL}^{(2)}$	CS# High Time	7			ns
$t_{SHQZ}^{(2)}$	Output Disable Time			7	ns
$t_{CLQX}^{(2)}$	Output Hold Time	0			ns
$t_{DVCH}^{(2)}$	Data In Setup Time	1.5			ns
$t_{CHDX}^{(2)}$	Data In Hold Time	4			ns
$t_{CLQV}^{(2)}$	Output Valid from CLK(1.65~2.7V/2.7~3.6V)			10/8	ns
$t_{WHSL}^{(2)}$	Write Protect Setup Time before CS# Low	20			ns
$t_{SHWL}^{(2)}$	Write Protect Hold Time after CS# High	100			ns
$t_{DP}^{(2)}$	CS# High to Deep Power-down Mode			3	μs
$t_{RES1}^{(2)}$	CS# High to Standby Mode without Electronic Signature Read			3	μs
$t_{RES2}^{(2)}$	CS# High to Standby Mode with Electronic Signature Read			1.8	μs
$t_{RST}^{(2)}$	CS# High to next Instruction after Reset			1	ms
t_W	Write Status Register Cycle Time		10	15	ms
t_{BP}	Byte Program Time		30	50	μs
t_{PP}	Page Program Time(1.65~2.7V)		1	5	ms
	Page Program Time(2.7~3.6V)		0.5	3	ms
t_{SE}	Sector Erase Time		80	300	ms
t_{BE}	Block Erase Time (32KB)		250	1500	ms
t_{BE}	Block Erase Time (64KB)		400	2000	ms
t_{CE}	Chip Erase Time		3	15	s

Notes:

- $t_{CH} + t_{CL} \geq 1 / F_R$ or $1 / f_R$;
- This parameter is characterized and is not 100% tested.

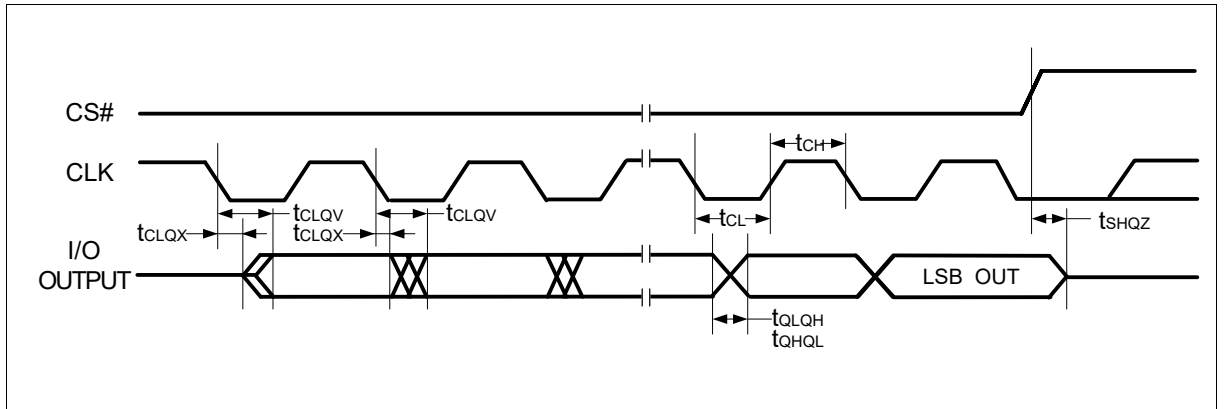


Figure 63 Serial Output Timing

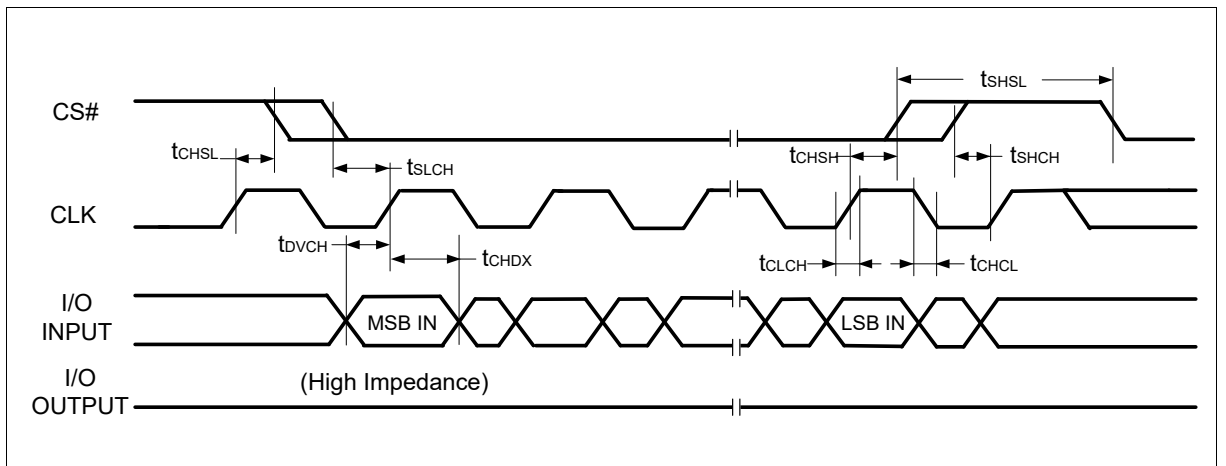


Figure 64 Serial Input Timing

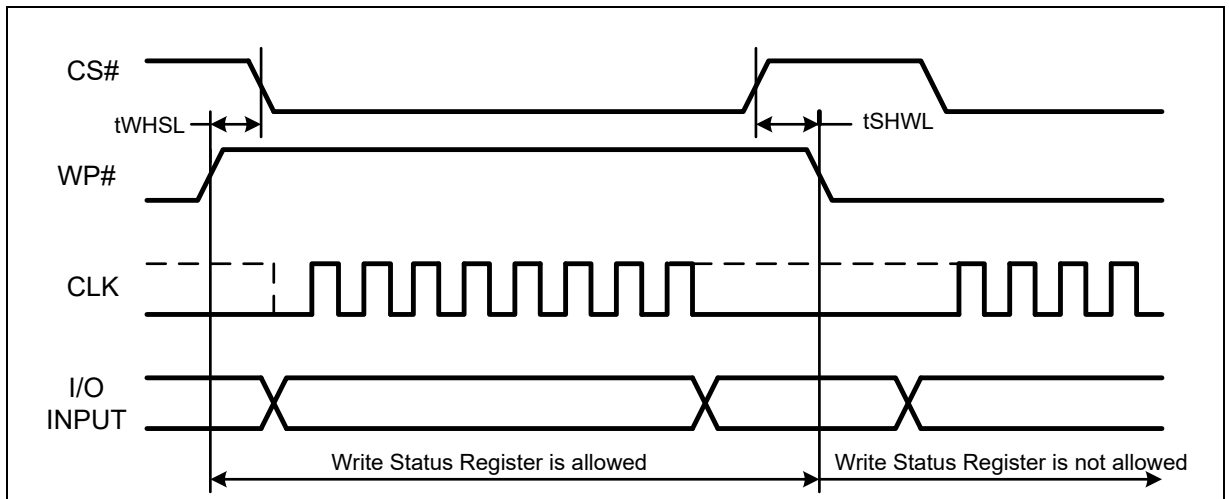


Figure 65 WP# Timing

13. Ordering Information

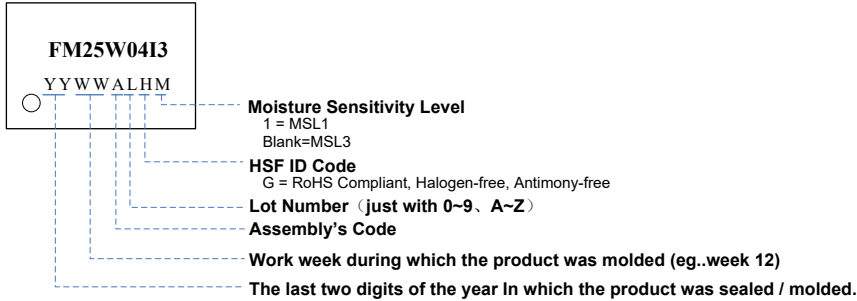
	FM	25W	0413-XXX	-C	-H	M
Company Prefix FM = Fudan Microelectronics Group Co.,Ltd						
Product Family 25W = 1.65~3.6V Serial Flash with 4KB Uniform-Sector, Dual/Quad SPI & QPI						
Product Density 0413 = 4M-bit						
Package Type SO = 8-pin SOP (150mil) SN = 8-pin USON (3*2mm, thickness 0.45mm) CTC= Thin 8-ball WLCSP ⁽¹⁾ SNA= 8-pin USON (1.5*1.5mm,thickness 0.45mm)						
Product Carrier U = Tube T = Tape and Reel (8mm) TC = Tape and Reel (12mm) ⁽²⁾						
HSF ID Code G = RoHS Compliant, Halogen-free, Antimony-free						
MSL Code 1 = MSL1 3 = MSL3						

Note:

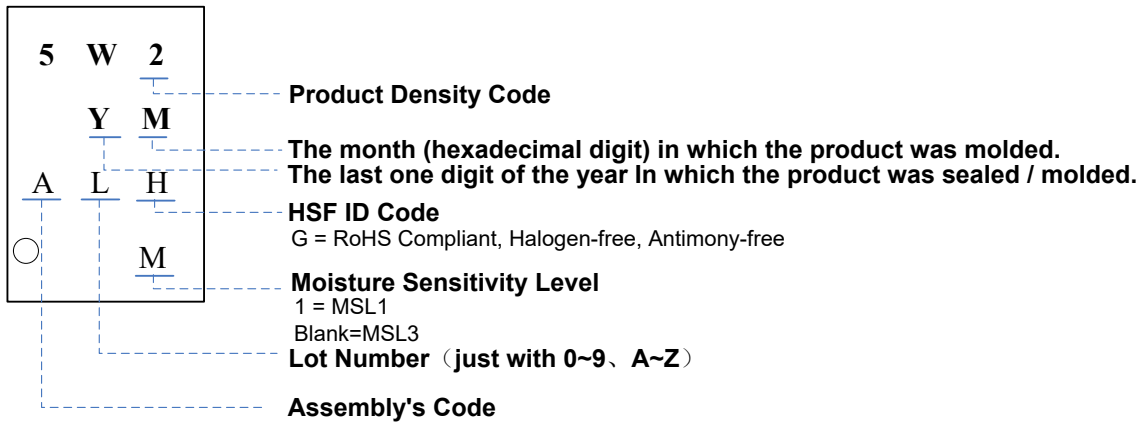
1. For the details of WLCSP package please contact local sales office.
2. 12mm tape reel only for USON8 (3*2*0.45) .

14. Part Marking Scheme

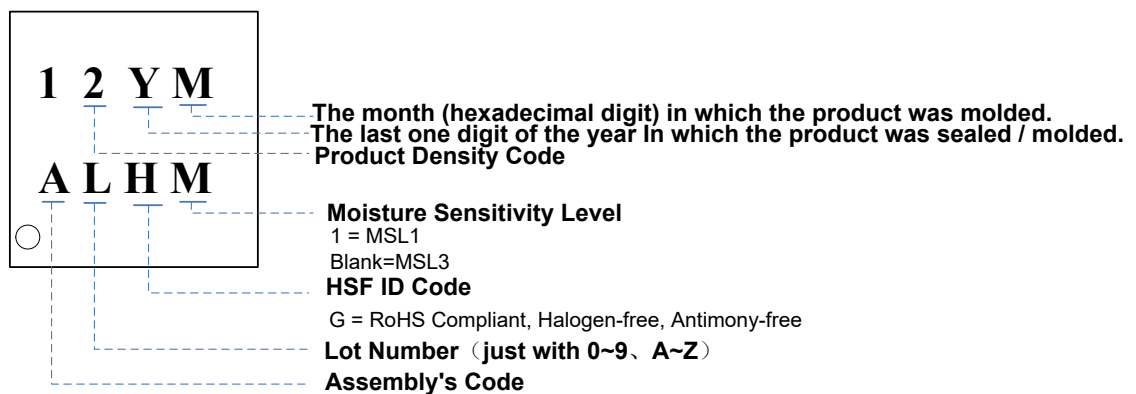
14.1. SOP8 (150mil)



14.2. USON8 (3*2mm, 0.45mm thickness)

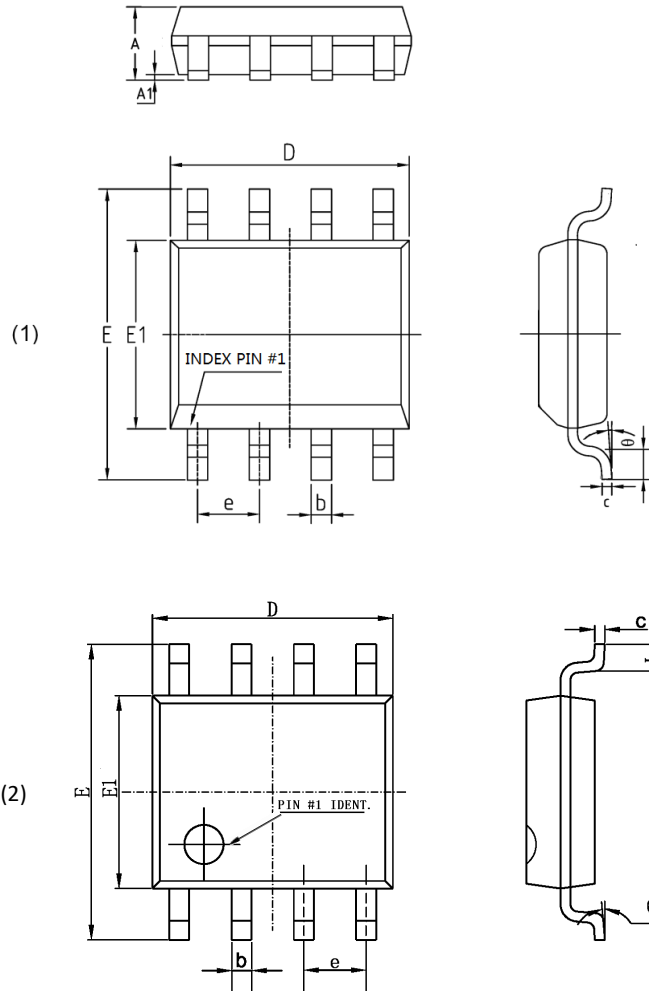


14.3. USON8 (1.5*1.5mm, 0.45mm thickness)



15. Packaging Information

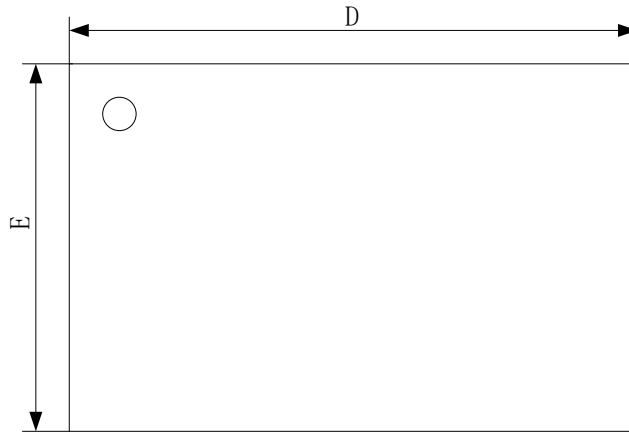
SOP 8 (150mil)



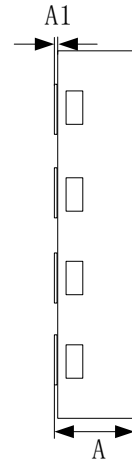
Symbol	MIN	MAX
A	1.350	1.750
A1	0.050	0.250
b	0.330	0.510
c	0.150	0.250
D	4.700	5.150
E1	3.700	4.100
E	5.800	6.200
e	1.270(BSC)	
L	0.400	0.900
θ	0°	8°

NOTE:
1. Dimensions are in Millimeters.

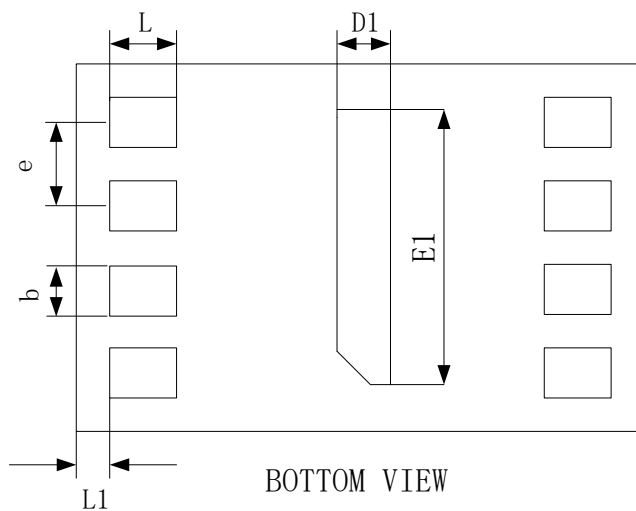
USON8 (3*2mm,0.45mm thickness)



TOP VIEW



SIDE VIEW



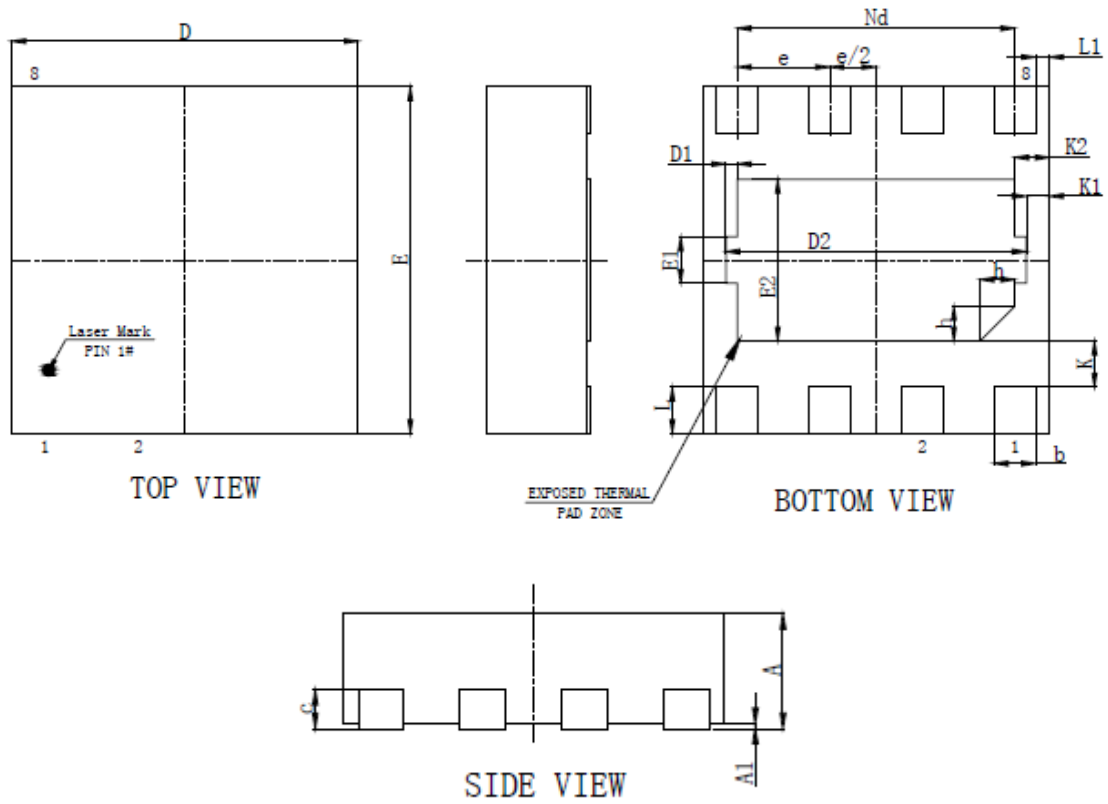
BOTTOM VIEW

Symbol	MIN	MAX
A	0.400	0.500
A1	0.000	0.050
D	2.900	3.100
E	1.900	2.100
D1	0.100	0.300
E1	1.500	1.700
b	0.200	0.300
e	0.500(BSC)	
L	0.300	0.400
L1	0.050	0.150

NOTE:

1. Dimensions are in Millimeters.

USON8 (1.5*1.5mm,0.45mm thickness)



Symbol	MIN	MAX
A	0.400	0.500
A1	0.000	0.050
b	0.130	0.230
D	1.450	1.550
D2	1.200	1.400
E	1.450	1.550
E2	0.600	0.800
e	0.400(BSC)	
L	0.150	0.250

NOTE:

1. Dimensions are in Millimeters.



16. Revision History

VERSION	DATE	PAGE	Revise Description
1.0	Sep. 2023	68	Initial Document Release.



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